VHF-FM PERSONAL RADIO STATION MODEL STORNOPHONE 500 TYPE CQP511 TYPE CQP512 TYPE CQP514 146 - 174 MHz

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Technical Data and Typical Performance Characteristics

Unless otherwise stated, specifications are based on the measuring methods prescribed in EIA publication RS-316.

Frequency Range

CQP510L: 146-160 MHz. CQP510H: 156-174 MHz.

Minimum Channel Spacing

CQP511: 50 kHz.

CQP512: 25kHz/20kHz.

CQP514: 12.5 kHz.

Maximum Frequency Swing

CQP511: ±15 kHz.

CQP512: $\pm 5kHz/\pm 4kHz$.

CQP514: ±2.5 kHz.

General

Antenna Impedance

50 Ω.

Maximum Channel Bandwidth

1.4 MHz.

Number of RF Channels

Maximum 3.

Dimensions, Cabinet

196 mm x 72 mm x 33 mm.

Weight

750 grams.

Transmitter

RF Output

500 mW.

Modulation

Phase-modulation.

Modulation Response

CQP511, CQP512:

6 dB/octave preemphasis characteristic from 300 to 3000 Hz, +1dB relative to 1000 Hz.

CQP514:

 $6~\mathrm{dB/octave}$ preemphasis characteristic from

300 to 2500 Hz, +1dB -3dB relative to 1000 Hz.

Frequency Stability

Meets government specifications.

Crystal Frequency Calculation

Crystal frequency = $\frac{\text{signal frequency}}{12}$

Spurious and Harmonic Radiation

Less than 2 x 10-7 watts.

Crystal

Storno type 98-8, spec. S-98-8.

Receiver Section

Sensitivity

 $0.8 \,\mu\text{V}$ e.m.f. for 12 dB SINAD.

Squelch

Electronic, adjustable.

Adjacent Channel Selectivity

80 dB.

Spurious and Harmonic Radiation

Less than 2 x 10-9 watts.

Intermodulation Attenuation

65 dB.

Spurious Response Attenuation

85 dB.

Crystal Frequency Calculation

CQP510L:

Crystal frequency = signal frequency +10.7 MHz.

CQP510H:

Crystal frequency = signal frequency -10.7 MHz.

AF Power Output

200 mW.

Crystal

Storno type 98-9 spec. S-98-9.

Battery

Туре

Rechargeable NiCd (Storno BU501).

Number of Cells

10.

Nominal Voltage

12.4 V.

Capacity

225 mAh.

Current Consumption

Standby: 10 mA.

Receive, AF output 200 mW: 40 mA.

Transmit: 120 mA.

Storno reserves the right to change the listed

specifications without notice.

SUPPLEMENT FOR 1W TRANSMITTERS CQP510

Technical Data and Guaranteed Performance Characteristics

Unless otherwise stated, specifications are based on the measuring methods precribed in EIA publication RS-316.

Storno reserves the right to change the listed specifications without notice.

General

Frequency Range

CQP510L: 146-160 MHz CQP510H: 156-174 MHz.

Minimum Channel Spacing

CQP511: 50 kHz CQP512: 25 kHz CQP513: 20 kHz CQP514: 12.5 kHz.

Maximum Frequency Swing

CQP511: ±15 kHz CQP512: ± 5 kHz CQP512: ± 4 kHz CQP514 ± 2.5 kHz. Antenna Impedance

50 Ω.

Maximum Channel Bandwidth

1.4 MHz.

Number of RF Channels

Maximum 3.

Dimensions, Cabinet

196 mm x 72 mm x 33 mm.

Weight 750 grams.

Transmitter

RF Output

1.0 W

Modulation

Phase-modulation.

Modulation Response

CQP511, CQP512, CQP513:

 $6~\mathrm{dB/octave}$ preemphasis characteristic from 300 to 3000 Hz, +1 dB relative to 1000 Hz.

CQP514

6 dB/octave preemphasis characteristic from 300 to 2500 Hz, +1 dB -3 dB relative to 1000 Hz.

Frequency Stability

Meets government specifications.

Crystal Frequency Calculation

Crystal frequency = $\frac{\text{signal frequency}}{12}$

Spurious and Harmonic Radiation

Less than 2×10^{-7} watts.

Crystal

Storno type 98-8, spec. S-98-8.

Receiver

Sensitivity

 $0.8 \,\mu\text{V}$ e.m.f. for 12 dB SINAD.

Squelch

Electronic, adjustable.

Ajacent Channel Selectivity

80 dB.

Spurious and Harmonic Radiation

Less than 2 x 10⁻⁹ watts.

Intermodulation Attenuation

65 dB.

Spurious Response Attenuation

85 dB.

Туре

Rechargeable NiCd (Storno BU501).

Number of Cells

10.

Nominal Voltage

12.4 V.

Crystal Frequency Calculation

CQP510L:

Crystal frequency = signal freq. +10.7 MHz

CQP510H:

Crystal frequency = signal freq.-10.7
MHz

AF Power Output

200 mW.

Crystal

Storno type 98-9, spec. S-98-9.

Battery

Capacity

225 mAh.

Current Consumption

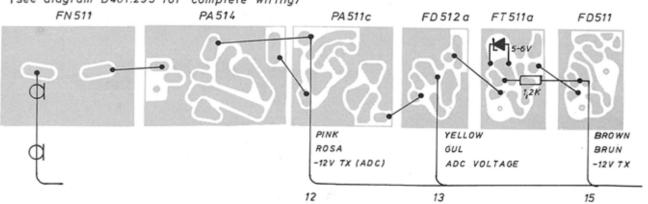
Standby: 10 mA.

Receive, AF output 200 mW: 40 mA.

Transmit: 200 mA

225 mA for R models.

MODIFICATION OF CABLING FOR 1W TRANSMITTER (see diagram D401.295 for complete wiring)

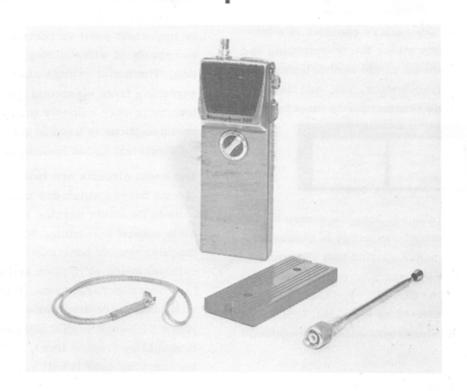


R 1.2 kΩ

E 5.6 V Zener diode

CABLING CQP510(R)-1W

CHAPTER I. GENERAL DESCRIPTION AND OPERATING INSTRUCTIONS A. Stornophone 500



Introduction

The STORNOPHONE 500 portable radiotelephone comprises a series of combined transmitters and receivers for FM radio communication on fixed crystal-controlled channels. The STORNO-PHONE 500 is available in versions for local or remote control with different channel spacings inside the frequency bands 68-88 MHz, 146-174 MHz, and 420-470 MHz. This manual contains descriptions of the locally controlled versions CQP511, CQP512, CQP513, and CQP514, for use in the VHF band from 146 to 174 MHz, and of those categories of accessories which are supplied by STORNO. If your radiotelephone is a special version you will find the relevant modification description and circuit diagrams inserted at the end of this manual or contained in a separate manual.

We at STORNO are constantly processing the experience we gain during the production and operation of our radiotelephones. Minor modifications will therefore be made continually, and all information given in this manual must therefore be subject to such reservations as are a logical consequence of this policy. However, any corrections and modifications will whenever practicable be printed on a special supplement and amendment sheet which will be inserted as the last page of this manual.

Versions

Туре	Channel Spacing	
CQP511	50 kHz	
CQP512	25 kHz	
CQP513	20 kHz	
CQP514	12.5 kHz	

Type Designations

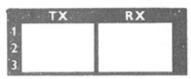
A type plate at the bottom of the back of the cabinet states the type designation of the radio-telephone.

Chapter I. General Description and Operating Instructions

This plate also carries the serial number, which should always be quoted in all communications to STORNO concerning this particular radiotelephone.

Storno

At the bottom of the battery cassette is a frequency chart which states the transmitting and receiving frequencies of the radiotelephone in question. Tone frequencies, too, are listed on the chart if a tone transmitter is incorporated.



Where no differentiation between radiotelephones with different channels spacings is necessary, the manual uses a designation that is common to such versions. For example, radiotelephones CQP511, CQP512, CQP513, and CQP514 are designated collectively as CQP510. Similarly, antennas AN511 and AN512 will be designated AN510.

Complete Radiotelephone

A complete STORNOPHONE 500 radiotelephone consists of these components:

A cabinet containing the transmitter/receiver, control knobs,
and speaker-microphone CQP510
A short sling with snap hook 49.096
A nickel-cadmium battery BU501
An antenna with matching network . AN510

Accessories for special applications are separately available: Lapel microphone, earphone, carrying case, tone transmitters, tone receivers, and various units for charging nickelcadmium batteries. This equipment is described in detail in Chapter III, ACCESSORIES.

Construction

The radiotelephone cabinet is of pressure-diecast light alloy metal. This reduces weight to a minimum with no sacrifice of ruggedness an important point as portable equipment must be capable of withstanding fairly robust handling. The metal cabinet also provides effective screening from electrical interference. This feature is very valuable in cases where the radiotelephone is used in localities with powerful electrical fields (industrial areas etc.).

The radio circuits are built on small printed circuit boards which are mounted in small metal cans to facilitate service and provide best possible mutual screening. Miniturization and the modular type of construction employed mean rational space utilization and an exceedingly high order of ruggedness. However, it is obvious that there are limits to how robust handling a STORNOPHONE 500 can take. In practice it should be treated like a camera. If placed in its carrying case it will have appreciably higher resistance to impacts and robust treatment.

The cabinet is designed so that it can be carried in the usual type of uniform breast pocket. However, the radiotelephone may also be carried in a special leather case either at the belt or in a shoulder sling.

The radio cabinet is splashproof and dustproof, and the relatively modest amount of heat generated by the transistors is dissipated through the metal surface of the cabinet. Also with its battery removed the radiotelephone is splashproof, permitting battery replacement anywhere - also in rainy weather - and without the use of tools.

B. Accessories

Standard Accessories

Storno offers a wide range of accessories for CQP510 radiotelephones, including antennas, microphones, earphones, tone equipment, cases and carrying slings, battery chargers etc.

This section contains a brief description of these accessories and their applications. A more detailed description is given in Chapter III, ACCESSORIES.

Chapter I. General Description and Operating Instructions

Antennas

AN511 Quarter-wave telescoping antenna with matching network for the 146-174 MHz frequency band.

AN512 Quarter-wave whip antenna with matching network for the 146-174 MHz frequency band.

AN516 Body antenna (for fastening to button etc.) for the 146-174 MHz frequency band.

AN517 Belt antenna for the 146-174 MHz frequency band.

AN518 Ribbon antenna for the 146-174 MHz frequency band.

AN519 Short whip antenna (λ /16) with matching network for 146 - 174 MHz frequency band.

Microphones and Headphones

MC501 Lapel microphone with connector and cord for connection to the multi-wire connector on the top terminal surface of the radiotelephone.

HP501 Earphone with cable and connector for connection to the multi-wire connector of the radiotelephone.

Tone Equipment

TT501 Single-tone transmitter for selective 15.002 calling. For installation in the radiotelephone cabinet.

C. Operation

TT504 Double-tone transmitter for selective calling. For installation in the radiotelephone cabinet.

Carrying Cases

49.100 Black leather carrying case with sling straps for attachment to belt, and with a case for the telescoping antenna.

Pocket Clip

49.094 Screw-on pocket clip. For mounting on the radiotelephone cabinet to protect it from falling out of the pocket.

Battery

BU501 Nickel-cadmium battery, 10 cells, 12.5V, 225 mAh.

Charging Units

CU501 Charging unit for max. 10 battery outlets.

CU502 Charging unit for max. 10 battery outlets and with automatic timer to permit the batteries connected to it to be charged for a previously selected number of hours.

CU503 Charging unit for max. 2 battery out-

15.001 Battery outlets for CU501 and CU503.

15.002 Battery outlets for CU502.

Operating Instructions

Operation of the portable radiotelephone is simple. Nevertheless, the user is advised to devote a few minutes to a study of the correct operating procedure.

Before beginning to use the radiotelephone it is necessary to make sure that the antenna is plugged into the antenna connector. If a telescoping antenna is employed, it should be pulled out to full length.

Because the receiver is very sensitive it will under favourable conditions be possible to receive signals with the telescoping antenna fully collapsed, but the telescoping antenna should always be pulled out to full length while transmitting.

Receive

- Set the channel selector to the desired channel.
- Adjust the volume control for convenient sound level. If there is any traffic on the channel you will hear it now.
- Adjust the squelch control while there is no traffic on the channel. When you turn the knob anti-clockwise you will hear a hissing sound; thereafter turn the knob clockwise until the noise only just disappears.

Chapter I. General Description and Operating Instructions

Transmit

- Set the channel selector to the desired channel. Listen in to make sure that someone is not speaking; do not start transmitting until the channel is clear.
- Press the transmit button on the radiotelephone cabinet. Speak towards the microphone.
 Correct speaking distance will be approx.
 10 cm (4 in.) at normal voice intensity. Be
 sure to release the transmit button when you
 want to listen.
- If a tone transmitter is installed in your radiotelephone, a calling tone will be transmitted when both the tone button and the transmit button on the radiotelephone cabinet are operated.

Do not operate the transmit button without an antenna connected to the radiotelephone. Do not forget to switch off after use. To switch off, set channel selector to the 0 position.

Checking the Battery Voltage

The battery voltage can be checked by pressing only the tone button on the cabinet. The condition of the battery will be shown by the indicator lamp at the bottom of the cabinet. If the lamp glows dimly or not at all, it is an indication that the battery is almost discharged, and a fully charged battery should be inserted instead.

Proper Care of Batteries

A nickel-cadmium battery can be charged at least 500 times without appreciably reducing its capacity. Ambient temperature, on the other hand, very markedly affects the capacity, which decreases with decreasing temperature. However, the battery may be used at temperature as low as -25°C but its capacity will then be only half of what it is at room temperature.

To remove the battery cassette from the cabinet, press the slide button on the rear of the cabinet upwards, whereupon the cassette can be tipped out. The cassette can be inserted in one way only.

Recommended charging current is the current that will discharge the battery in 10 hours - approx. 23 mA for this type of battery. However, approx. 14 hours will be required for charging a fully discharged battery, due to the fact that the efficiency when charging is approximately 70 per cent. Overcharging the battery should obviously be avoided, but the battery will not normally suffer permanent damage by being charged for up to twice the prescribed charging time. Thus, a fully charged battery will not be permanently damaged by being charged for an additional 14 hours even though repeated overcharging will reduce its capacity and shorten its usable life.

The discharge time obviously depends on the particular nature of the service for which the radiotelephone is employed, but the percentagewise distribution tabulated below should serve as a guide for the great majority of applications:

10 % transmit at 130 mA

80 % standby at 8 mA

10 % squelch open, average 16 mA.

Consequently, average power consumption per working hour will be approx. 21 milliampere-hours, corresponding to a total working time of $\frac{225}{21}$ hours = 10.7 hours with a fully charged battery.

During receive periods, the battery voltage will keep fairly constant until the battery is almost discharged, when the voltage drops quite suddenly. However, when the battery is exposed to heavy loads - as will be the case during transmit periods - the voltage will decrease somewhat during the last hours of the discharge period.

The Ni-Cd batteries are charged in a type CU50x charging unit, which is manufactured in different versions. These are described in detail in Chapter III, ACCESSORIES. It should also be kept in mind that a certain amount of self-discharge occurs in the batteries.

Communication

Due to the absence of a ground plane the antenna of the STORNOPHONE 500 radiotelephone is not so efficient as a comparable mobile an-

Chapter I. General Description and Operating Instructions

tenna. However, this slight disadvantage can be offset by choice of a suitable site. Note also that it is important that the antenna is held vertical.

Range in practice depends materially on the nature of the surrounding terrain and on whether communication is to be with another pocket station, a mobile station, or a base station. Also, extended range will be obtained with the STORNOPHONE 500 radiotelephone placed on, say the roof of a car, which will improve the effectiveness of the antenna.

In practice, the best sites have been found to be hilltops and high locations in general: near windows in buildings; in street crossings; and in cars, where the antenna can be put out of the window. However, reduced range must be expected from basements, ferro-concrete buildings, iron-frame bridges, dense woods, narrow streets, etc.

Service

The organization of a preventive maintenance routine is of material importance in securing that the radiotelephone will be capable of peak performance under all conditions.

Chapter IV contains a detailed description of maintenance and service of the radiotelephone. The complete adjustment procedure is described in Chapter IV.

CHAPTER II. CIRCUIT ANALYSIS A. Controls and Their Functions

The controls of the radiotelephone are placed on the sides of the cabinet and on the front panel. The antenna connector and multi-wire connector are placed on the top terminal surface of the cabinet. The battery indicator, which shows the condition of the battery, is placed in the bottom.

The functions described here are common to both transmitter and receiver. Functions relating only to the transmitter, receiver, or tone transmitter are covered by the respective descriptions of these.

Channel Selection - On/Off

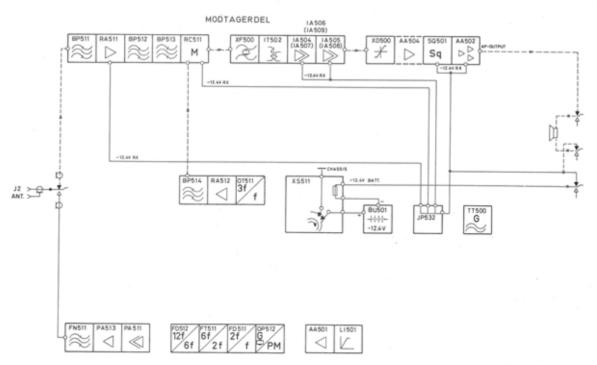
The radiotelephone has a combined on/offswitch and channel selector which applies battery voltage to the radiotelephone and switches between frequency channels 1, 2, and 3.

In the 0 position (extreme left position) one switch section disconnects the battery plus terminal, and the radiotelephone therefore receives no battery voltage.

In the 1, 2, or 3 position one switch section connects the battery plus terminal to chassis, and the radiotelephone therefore receives battery voltage and is in the standby condition. The other switch section connects transmitter and receiver crystals for the channel selected. This switch section is devised so that non-used receiver crystals are disconnected whereas the corresponding transmitter crystals are short-circuited. The circuit diagram shows the radiotelephone in the standby condition with channel 1 selected. The red dot-and-dash lines indicate signal paths; solid lines represent DC-current paths.

Transmit-button Function

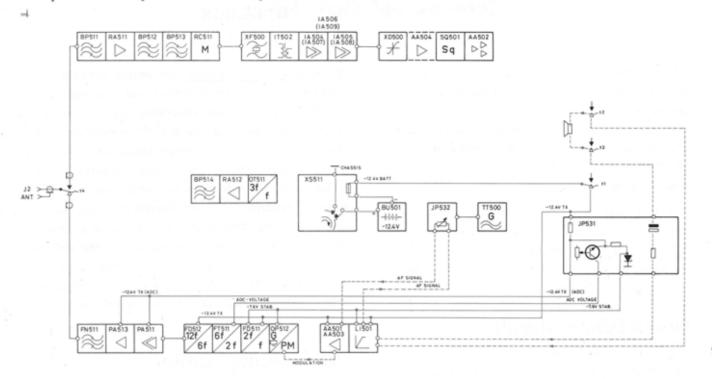
Before operating the transmit button, the channel selector should be set at either 1, 2, or 3. On the transmit button being operated, the battery voltage is switched from the receiver section to the transmitter section, which receives, in addition to 12.4V, 7.6V stabilized



SENDERDEL

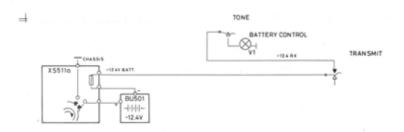
Chapter II. Circuit Analysis

voltage and ADC-controlled voltage from junction panel JP531. Besides, the antenna is connected to the transmitter RF output and the speaker-microphone to the AF input.

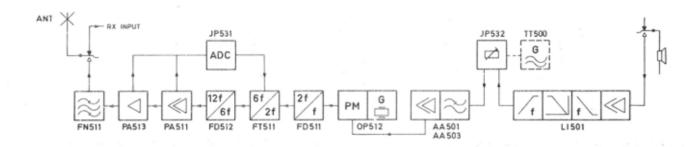


Battery-indicator Function

Battery indication depends on whether the equipment is in the standby condition. On the tone button being operated, the indicator lamp receives battery voltage and shows the condition of the battery.



B. Transmitter Section



General

The transmitter is built on a number of circuit boards which are mounted in screen cans and therefore constitute separate modules. This type of construction ensures a high order of stability and facilitates service.

The transmitter is phase modulated on the fundamental frequency. Its output frequency is in the 146-174 MHz frequency band.

The output frequency is found by multiplying the crystal-oscillator frequency by 12.

The radiotelephone can be provided with 3 frequency channels, and switching between channels is performed by switching the proper crystals. An automatic drive control system (ADC) protects the transmitter output transistor and secures constant carrier output regardless of changes in battery voltage and temperature.

Modules

The transmitter consists of the following modules:

LI501 AF limiter

AA501 AF amplifier for 50, 25, and 20 kHz

channel spacing

AA503 AF amplifier for 12.5 kHz channel

spacing

OP512 Oscillator and phase modulator

FD511 Frequency doubler

FT511 Frequency tripler

FD512 Frequency doubler

PA511 RF power amplifier

PA513 RF power amplifier

FN511 Antenna filter

Coverage of the full frequency range requires minor modifications to coils and capacitors in the tuned circuits of some of the modules. Such modules have a letter added to their type designations, either H (high sub-band) or L (low sub-band). This division corresponds, in terms of output frequency, to 156 - 174 MHz (H) and 146 - 160 MHz (L).

Moreover, some of the transmitter circuits are contained in the following modules which are common to the transmitter and receiver sections:

JP531 Junction panel

JP532 Junction panel

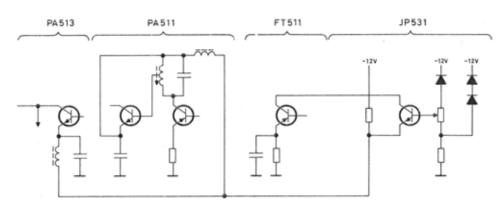
XS511 Crystal shift unit

These modules are described in detail in Section D of this chapter. Tone equipment is described in Chapter III, ACCESSORIES.

ADC Function

The ADC function (automatic drive control) serves the purpose of protecting the power transistors in modules PA511 and PA513 against overloads caused by mismatching such as may occur if the transmit button is operated without the telescoping antenna

Chapter II. Circuit Analysis



mounted and pulled out. Besides, the ADC circuit minimizes carrier output variations in the case of battery-voltage and temperature changes.

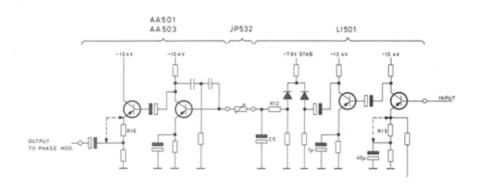
A 2.7 Ω resistor is inserted in the circuits of the transistors in RF power amplifiers PA511 and PA513. Physically, the resistor is located in junction panel JP531 (R4). The voltage drop across the resistor is used to control transistor Q1 in JP531. Q1 is in a DC series connection with the transistor of frequency tripler FT511. The operating voltage of the latter unit and hence also its output will therefore be reduced by any increase in the collector currents of RF power amplifier stages PA511 and PA513. Consequently, any increase in the currents of the RF power amplifier stages will be

counteracted by a reduction of the amount of drive applied from frequency tripler FT511. Silicon diodes E3 and E4 in junction panel JP531 operate as voltage stabilizer diodes seeing that the voltage drop (approx. 0.5V) across a diode is virtually independent of the current and hence also of the battery voltage. These diodes and E1 also provide temperature compensation of regulator transistor Q1.

Potentiometer R3 in junction panel JP531 permits adjustment of the regulator transistor base current. This feature permits adjusting the ADC circuit to a condition of balance where the power output is constant at 500 mW.

The following pages contain a circuit analysis and technical specifications of individual modules.

Speech Limiter and Filter Amplifier LI501 and AA501 or AA503



Description

Speech limiter LI501 and filter amplifier AA501 or AA503 constitute the AF section of the transmitter. The speech limiter amplifies and clips the microphone signal applied to it. It is composed of two grounded-emitter amplifier stages. The first stage has unsymmetrical input, the microphone signal being applied to the base of the transistor. An un-bypassed resistor R13 in the emitter circuit reduces the gain. Short-circuiting R13 will increase the gain by 6 dB.

The emitter of the second amplifier transistor is only partly bypassed, providing a reduction in negative feedback at high frequencies.

Thereafter follows a clipper composed of two diodes which are biased in their forward direction. The amount of bias is adjusted for symmetrical clipping. The clipper is followed by an integrating circuit (R12, C5).

The AF circuit of the speech limiter is fed to the limiter potentiometer (in the junction panel) which controls the level of limiting and, from there, to filter amplifier AA501 or AA503. Filter amplifier AA501 is used in radiotelephones with 50 kHz, 25 kHz, and 20 kHz channel spacing whilst filter amplifier AA503 is used in radiotelephones with 12.5 kHz channel spacing.

The filter module amplifies the input signal and cuts off all frequencies above 3000 Hz (AA501) or 2500 Hz (AA503). The filter module contains

two stages. The first one of these, a groundedemitter stage, has an RC filter to suppress the high frequencies inserted between its collector and base. The second stage is an emitter follower, which secures a low value of generator impedance for the following phase modulator. The emitter circuit of the second stage is composed of two resistors. In the AA501 module, one of them (R16) can be strapped, thereby altering the maximum frequency swing from ±5 kHz to ±15 kHz.

Technical Specifications

LI501

Supply Voltage and Current Drain

Nominal: 12.4V 5mA.

Diode clipper: Zener regulated, 7.6V 0.1mA.

Sensitivity

Input sensitivity for $\Delta f = 2/3 \Delta f$ max. is determined by the setting of the limiter potentiometer, as no gain control is provided.

Output Voltage

For 1 mV input signal at 1000 Hz: Approx. 45mV Harmonic distortion: Approx. 4%.

Frequency Response

When used with filter amplifier AA501: Flat 300 - 3000 Hz + 1/-3 dB.

When used with filter amplifier AA503: Flat 300-2500 Hz +1/-3 dB.

AA501/AA503

Supply Voltage Nominal: 12,4 V.

Current Drain

5 mA.

Frequency Response (AA501)

When used with speech limiter LI501, with reference to 1000 Hz:

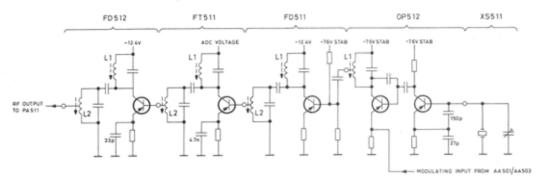
300 - 3000 Hz: Flat +1/-3 dB 3000 - 6000 Hz: -18 dB/octave 6000 - 20.000 Hz: -20 dB/octave. Frequency Response of Filter Amplifier AA503

When used with speech limiter LI501, with reference to 1000 Hz:

300 - 2500 Hz, flat +1/-3 dB. 2500 - 5000 Hz, -18 dB/octave.

5000 - 10000 Hz, -20 dB/octave.

Oscillator, Modulator and Frequency Multiplier OP512, FD511, FT511 and FD512



Description

The transmitter oscillator and multiplier chain is composed of the following modules:

OP512 Crystal oscillator and phase modulator

FD511 Frequency doubler

FT511 Frequency tripler

FD512 Frequency doubler.

Crystal Oscillator and Phase Modulator OP512

The crystal oscillator operates in a Pierce-Colpitts circuit, the output signal being taken off across a resistor in the collector circuit. Two capacitors, between base and emitter and between emitter and chassis potential, constitute part of the crystal load capacitance in addition to serving as voltage divider for the feedback circuit.

Trimmer capacitors in shunt across the crystals permit fine adjustment of the oscillator frequencies. Both the crystals and trimmer capacitors are mounted in a crystal shift unit which is common to the transmitter and receiver. The oscillator output signal is fed to the phase modulator through a capacitor. Modulation is produced by applying AF voltage to the emitter circuit, thereby varying the mutual conductance of the transistor.

Frequency Doubler FD511

The frequency doubler transistor operates in Class A with its emitter grounded. The base bias network connects to a stabilized 7.6V supply. The advantage of this arrangement is that the input impedance is virtually independent of battery voltage and that the output level is stable. The transistor works into two circuits which in conjunction with a coupling capacitor constitute a top-coupled band-pass filter.

Frequency Tripler FT511

The frequency tripler transistor operates in Class B-C without fixed base bias, which is possible due to the relatively high input signal level. This results in good DC stability and high efficiency. The transistor works into a bandpass filter composed of two circuits with capacitive top coupling and an inductive tap on the output circuit. Operating voltage for the frequency tripler is controlled by the ADC circuit described elsewhere in this manual.

Frequency Doubler FD512

The frequency doubler is similar to the FT511 multipliers in circuitry and operation. An exception is that the emitter resistor is bypassed only for the desired frequency range, thereby preventing radiation on any subharmonic frequencies.

Technical Specifications

Crystal Oscillator/Phase Modulator OP512

Frequency Range 12.16 - 14.5 MHz.

Crystal Frequency Calculation

 $f_{x} = \frac{\text{signal frequency}}{12}$

Frequency Pulling ±20 x 10⁻⁶.

Frequency Stability
Better than ±1.8 kHz.

Crystal Power Rating
Max. 1 mW.

Supply Voltage 12.4 V.

7.6 V stabilized.

Modulating Frequency 300 - 3000 Hz.

Modulation Sensitivity (1000 Hz)

Input voltage for $\Delta f = \pm 0.84$ rad. corresponding to $\Delta f \pm 10$ kHz at the output frequency: 100 mV.

Harmonic Distortion

Measured at 1000 Hz and $\Delta f = \pm 10$ Hz: 8%.

RF Output Level Approx. 35 mV.

Frequency Doubler FD511

Frequency Range

Input frequency: 12.16 - 14.50 MHz Output frequency: 24.33 - 29.00 MHz

RF Input Level

Approx. 35 mV.

RF Output Level

1.5 V.

Current Drain (at 12.4 V)

Without input signal: 1.6 mA With input signal: 1.8 mA.

Frequency Tripler FT511

Frequency Range

Input frequency (L): 24.33 - 26.66 MHz

Output frequency (L): 73.00 - 80.00 MHz

Input frequency (H): 26.00 - 29.00 MHz

Output frequency (H): 78.00 - 87.00 MHz.

RF Input Level

1.5 V.

RF Output Level

0.9 V.

Current Drain (at 12.4 V)

Approx. 2 mA.

Frequency Doubler FD512

Frequency Range

Input frequency (L): 73 - 80 MHz

Output frequency (L): 146 - 160 MHz

Input frequency (H): 78 - 87 MHz

Output frequency (H): 156 - 174 MHz.

Input Level

0.9 V.

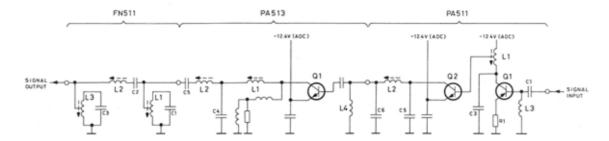
RF Output Level

1.7 V.

Current Drain (at 12.4 V)

Approx. 2 mA.

RF Power Amplifier and Antenna Filter PA511, PA513 and FN511



Description

The power amplifier chain of the transmitter is composed of the following modules:

PA511 1st power amplifier

PA513 2nd power amplifier

FN511 Antenna filter.

RF Power Amplifier PA511

RF power amplifier PA511 operates on the signal frequency. It is composed of a straight amplifier Q1, and a driver stage, Q2.

The signal is applied to Q1 via C1, which in conjunction with choke coil L3 suppresses radiation at subharmonic frequencies. The collector impedance is a single-tuned circuit. The emitter R1 makes it possible to measure the current through Q1. Driver transistor Q2 is an NPN type with its operating voltage applied to the emitter. The base is coupled directly to a tap on L1, through which it receives its DC potential. The anode is tuned by a pi-section (L2-C5-C6), which provides good matching and efficiency.

RF Power Amplifier PA513

RF power amplifier PA513 operates in Class C without emitter resistor in order to accomplish maximum power gain. The PA513 requires a nominal input level of approx. 50 mW. This corresponds to a nominal output level of approx. 500 mW, taking losses in the antenna filter and antenna switch into account.

The collector circuit is a pi-section (the output capacitance of Q1 and L1 and C4) which is followed by a series-tuned circuit (L2 and C5), and these two circuits constitute a tunable output transformer. By adjustment of L1 and L2, matching between the transistor and its load is obtained, together with adequate suppression of harmonic radiation.

The input coil (L4) provides a DC path for the preceding stage (PA511).

Antenna Filter FN511

Antenna filter FN511 is a band-pass filter which provides strong suppression of spurious and harmonic radiation from the transmitter section. It is a pi-filter consisting of three circuits (L1-C1, L2-C2, and L3-C3) in which L1, L2 as well as L3 are adjustable. The module has two inside screens to reduce coupling between coils.

Technical Specifications

RF Power Amplifier PA511

Frequency Range

PA511L: 146 - 160 MHz

PA511H: 156 - 174 MHz.

RF Input Voltage

Nominal approx. 1.7 V.

RF Output Power

Approx. 130 mW.

RF Power Amplifier PA513

Frequency Range

146 - 174 MHz.

RF Input Level

Approx. 130 mW.

RF Output Level

600 mW into 50 Ω .

Load Impedance

50 Ω.

Current Drain with Normal Drive Applied

70 mA.

Antenna Filter FN511

Pass Band

146 - 174 MHz.

3 dB Attenuation Points

124 and 190 MHz.

Insertion Loss

Max. 0.4 dB (measured between PA513 and $50~\Omega$ load in range 146 - 174 MHz).

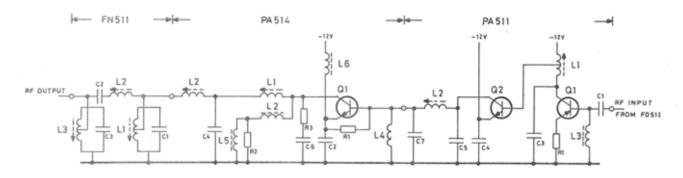
Attenuation

More than 20 dB at 87 MHz More than 30 dB at 292 MHz (measured between 50 Ω generator and 50-ohm load).

Maximum RF Power

2 watts.

RF Power Amplifier and Antenna Filter PA511, PA535, and FN511



RF Power Amplifier PA511

RF power amplifier PA511 operates on the signal frequency. PA511 is composed of a linear amplifier, Q1, and a driver stage, Q2.

The signal is applied to Q1 via C1, which in conjunction with choke coil L3 suppresses radiation at subharmonic frequencies. The collector impedance is a single-tuned circuit.

Emitter resistor R1 provides a simple method of measuring current through Q1. Normal operating current is approx. 6 mA.

Driver transistor Q2 is an NPN type having its operating voltage applied to the emitter. The base is coupled directly to a tap on L1, through which it also receives its DC potential.

The collector is tuned by network L2, C5 and C6, which provides good matching and efficiency. Normal operating current is approx. 20 mA.

RF Power Amplifier PA514

RF power amplifier PA514 operates in Class C without an emitter resistor in order to achieve maximum power gain.

The PA514 requires an input signal power of approx. 150 mV in order to deliver 1.0 W output power, taking losses in the antenna filter and antenna switch into account.

Q1 works into a pi-network consisting of its own collector capacity, coil L1 and capacitor C4, which, together with coil L2, constitutes a tunable, impedance matching output transformer, also providing for adequate suppression of harmonic radiation.

Input coil L4 and capacitor C1 serve as a matching network at the input to the stage. L4 also provides a DC path for the preceding stage (PA511).

Antenna Filter FN511

Antenna Filter FN511 is a band-pass filter which provides strong suppression of spurious and harmonic radiation from the transmitter section.

It is a filter consisting of three circuits (L1-C1, L2-C2, and L3-C3), where all three coils are adjustable.

Two shields placed inside the module reduce coupling between coils.

Technical Specifications

RF Power Amplifier PA511

Frequency Range

PA511L: 146 - 160 MHz

PA511H: 156 - 174 MHz.

RF Input Voltage

Nominal approx. 1.2 V.

RF Output Power

Approx. 150 mW.

Current Drain with Normal Drive:

20 mA.

RF Power Amplifier PA514

Frequency Range 146 - 174 MHz.

RF Input Level
Approx. 150 mW.

RF Output Level 1.0 W into 50 Ω

Load Impedance 50 Ω

Current Drain with Normal Drive Applied 175 mA.

Antenna Filter FN511

Pass Band 146 - 174 MHz. 3 dB Attenuation Points 124 and 190 MHz.

Insertion Loss

Max. 0.4 dB (measured between PA513 and 50 Ω load in range 146 - 174 MHz).

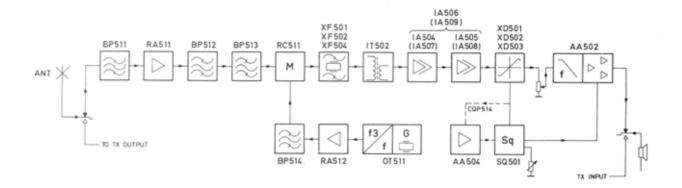
Attenuation

More than 20 dB at 87 MHz More than 30 dB at 292 MHz (measured between 50 Ω generator and 50-ohm load).

Maximum RF Power

2 watts.

C. Receiver Section



General

The receiver is built on a number of circuit boards which are mounted in screen cans and therefore constitute separate modules. This type of construction ensures a high order of stability and facilitates service.

The receiver is a single-conversion superheterodyne.

The frequency specifications of the receiver are as follows:

Signal-frequency Range

High sub-band	156-174 MHz
Low sub-band	146-160 MHz
Intermediate frequency	10.7 MHz

Crystal frequency Range

High sub-band	52.2-56.9 MHz
Low sub-band	48-54.4 MHz

An IF crystal filter provides the degree of selectivity required for channel spacing. A maximum of three crystal-controlled channels can be provided. Channel selection is performed by switching the crystals. An electronic squelch circuit is also provided.

Modules

DDS11

The receiver is composed of the following modules:

BP511	Band-pass filter
RA511	Signal-frequency amplifier
BP512	Band-pass filter

BP513	Band-pass	filter

RC511	3.07.2
RUSTI	Miver

OT511 Oscillator and frequency tripler

RA512 Amplifier

BP514 Band-pass filter

XF501 Crystal filter for 50 kHz channel spacing

XF502 Crystal filter for 25/20 kHz channel

Crystal filter for 12.5 kHz channel XF504 spacing

IT502 Impedance transformer

IF amplifier for 50, 25, and 20 kHz IA506 channel spacing, comprising IF modules IA504 and IA505

IA509 IF amplifier for 12.5 kHz channel spacing, comprising IF modules IA507 and IA508

Crystal discriminator for 50 kHz chan-XD501 nel spacing

Crystal discriminator for 25/20 chan-XD502 nel spacing

XD503 Crystal discriminator for 12.5 kHz channel spacing.

AA504 Noise amplifier for 12.5 kHz channel spacing

SQ501 Squelch circuit

AA502 AF amplifier.

Coverage of the full frequency range requires minor modifications to coils and capacitors in the tuned circuits of some of the modules. Such modules have a letter added to their type designations, either H (high sub-band) or L (low subband). This division corresponds, in terms of

Chapter II. Circuit Analysis

output frequency, to 156 - 174 MHz (H) and 146 - 160 MHz (L).

Moreover, part of the receiver circuit is contained in the following modules which are common to the transmitter and receiver sections:

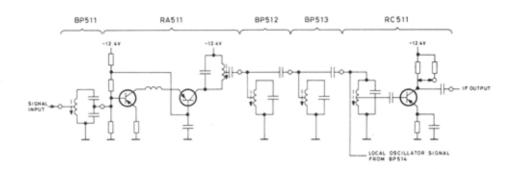
JP531 Junction panel

JP532 Junction panel

XS511 Crystal shift unit.

These modules are described in detail in Section D of this chapter. Tone equipment is described in Chapter III, ACCESSORIES.

Front End BP511, RA511, BP512, BP513 and RC511



The receiver front end is composed of the following modules:

BP511 Input filter

RA511 Signal-frequency amplifier

BP512 Band-pass filter

BP513 Band-pass filter

RC511 Mixer.

Band-pass Filter BP511

Band-pass filter BP511 is employed as antenna input circuit for the receiver section but also operates as impedance matching network between the antenna and RF amplifier module RA511. Impedance matching is accomplished by means of a tap on coil L1 on the antenna side and a capacitive tap (C1 - C2) on the receiver side.

Signal-frequency Amplifier RA511

RF amplifier RA511 amplifies the signals received from the antenna before they are fed to the mixer (RC511) through two band-pass filters (BP512 and BP513). The amplifier is a cascode circuit, which possesses the advantages of high gain and minimum feedback from output to input.

Coil L1, which connects the collector of Q1 to the emitter of Q2, acts as a wideband circuit tuned by the series connection of the collectorto-chassis capacitance and the emitter-to-chassis capacitance. The two transistors are in series for DC so that each receives approximately half battery voltage.

Band-pass Filters BP512 and BP513

Additional RF selectivity is obtained by inserting three band-pass filters between signal-frequency amplifier RA511 and mixer RC511. Two of these filters are individual modules and designated BP512 and BP513 whereas the third circuit is part of the following mixer module, RC511.

Mixer RC511

Mixer RC511 receives the incoming signal from the antenna and the local oscillator signal.

The signal from band-pass filter BP511 is coupled to a parallel-tuned circuit (L1-C1). From a tap on the coil, the signal is fed to the base of the mixer (Q1).

Low impedance to the IF and good stability are obtained by using a tap on the coil and relatively high value of coupling capacitance.

The local oscillator signal is taken out from the circuit L1 - C2 in filter module BP514 and fed to the input of mixer RC511 together with the signal from band-pass filter BP513.

The following crystal filter makes it necessary to introduce provision for varying the output impedance of the mixer. This can be done by means of a strap.

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Technical Specifications

Band-pass Filter BP511

Frequency Ranges

BP511L: 146 - 160 MHz

BP511H: 156 - 174 MHz.

Input Impedance

Nominal: 50 ohms.

RF Amplifier RA511

Frequency Range

RA511L: 146 - 160 MHz

RA511H: 156 - 174 MHz.

Gain

Voltage gain is approx. 35 dB.

Band-pass Filters BP512 and BP513

Frequency Ranges

BP512L and BP513L: 146 - 160 MHz.

BP512H and BP513H: 156 - 174 MHz.

Mixer RC511

Frequency Range

146 - 174 MHz.

Voltage Gain

50 kHz channel spacing: approx. 19 dB.

20/25/12.5 kHz channel spacing: approx. 22 dB.

IF

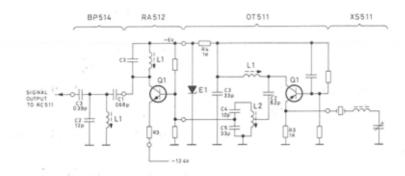
10.7 MHz.

Current Drain

With oscillator signal; approx, 1.5 mA.

Without oscillator signal; approx. 1.2 mA.

Oscillator and Frequency Multiplier OT511, RA512 and BP514



The oscillator and multiplier section generates the injection signal for the receiver mixer. It is composed of the following modules:

OT511 Oscillator and frequency tripler

RA512 RF amplifier

BP514 Band-pass filter.

Oscillator and Frequency Tripler OT511

The oscillator/tripler unit contains a thirdovertone crystal oscillator the output frequency
of which is three times the oscillator frequency.
Basically, the oscillator is a Colpitts oscillator
with the crystal in series with the emitter of the
oscillator transistor. The oscillator will therefore operate at the frequency of minimum crystal impedance - the series resonance of the crystal - provided the collector circuit is tuned to
approximately that frequency.

The receiver crystals (maximum three crystals) are placed in sockets in a separate crystal shift unit, XS511, in which the transmitter crystals too are placed.

The pi-section of the collector circuit (L1 - C2 - C3) has been made so wide that frequency pulling will have no appreciable influence on its impedance. The third harmonic of the oscillator frequency is selected in the parallel-resonant circuit, from whose capacitive tap the local oscillator signal is fed to the following RF amplifier, RA512.

The oscillator/tripler module is in a DC series

connection with the following amplifier stage and either stage therefore operates at only approximately half battery voltage.

RF Amplifier RA512

Amplifier module RA512 amplifies the local oscillator signal to a power level that is adequate for mixer module RC511.

Under normal operating conditions the amplifier stage is driven so hard that limiting of the output signal occurs. This limiting has been introduced intentionally in order to compensate for variations in the output of the oscillator module. The collector circuit (L1 - C3) is tuned to three times the local oscillator frequency (like C2 - C4 - C5 in oscillator/tripler OT511).

Band-pass Filter BP514

A band-pass filter between the RF amplifier module and the mixer module reduces spurious signals.

Technical Specifications

Oscillator/Tripler OT511

Crystal Frequency Ranges

OT511H: 48.4 - 54.4 MHz

OT511L: 52.2 - 56.9 MHz.

Output Frequency Ranges

OT511H: 145.2 - 163.2 MHz

OT511L: 156.6 - 170.7 MHz.

Crystal Frequency Calculation

Low sub-band, 146 - 160 MHz:

$$fx = \frac{fs + 10.7}{3}$$
 MHz.

High sub-band, 156 - 174 MHz:

$$fx = \frac{fs - 10.7}{3}$$
 MHz

where fx is the crystal frequency in MHz fs is the receiver signal frequency in MHz.

Crystal Specification

Storno type 98-9, spec. s-98-9.

Crystal Power Rating

Approx. 0.1 mW.

 $\frac{\text{Frequency Stability}}{\text{Better than } \pm 2 \text{ x } 10^{-6}}$ at 23°C and a voltage variation of $\pm 20\%$.

Frequency Pulling

Crystal trimmer permits pulling the crystal frequency not less than $\pm 25 \times 10^{-6}$.

Power Output

Approx. 200 µW.

Amplifier RA512

Frequency Ranges

RA512H: 145 - 163 MHz

RA512L: 156 - 171 MHz.

Power Gain

Approx. 8 dB (during limiting).

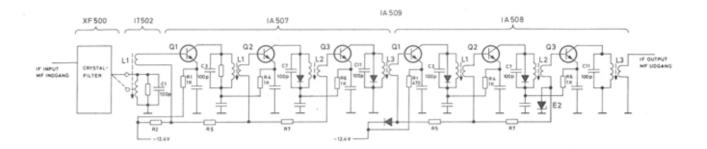
Band-pass Filter BP514

Frequency Ranges

BP514H: 145 - 163 MHz.

BP514L: 156 - 171 MHz

IF Amplifier XF500, IT502, IA506 or IA509



Description

The IF chain of the receiver consists of the following modules:

XF500 10.7 MHz crystal filter unit. Different types with different bandwidths are used, depending on the channel spacing employed in the particular radiotelephone.

> XF501 is used for 50 kHz channel spacing.

XF502 is used for 20/25 kHz channel spacing.

XF504 is used for 12.5 kHz channel spacing.

IT502 Impedance transformer.

IA509 10.7 MHz IF amplifier consisting of:

IA507 1st 3-stage IF amplifier IA508 2nd 3-stage IF amplifier

Crystal Filter Unit and Impedance Transformer, XF500 and IT502

The 10.7 MHz IF signal from the mixer is fed to the crystal filter input. After the required degree of selectivity has been obtained in the filter, the signal is fed to impedance transformer IT502, which operates as a matching network between the crystal filter and the following IF amplifier. Because the input and output impedances of the various crystal filter units are not identical it is necessary to provide some means of altering the impedance transformation in module IT502. This has been accomplished by means of taps on the transformer primary.

For example, crystal filter type XF501 connects to the top of the coil whereas crystal filters XF502, and XF504 connect to the tap on the coil.

IF Amplifier IA509

The IF amplifier employed consists of two 3stage amplifier units, IA507 and IA508, which are enclosed in a common screen can. The screen can is divided into six compartments which provide mutual screening between the individual amplifier stages.

The two IF amplifier units, IA507 and IA508, are practically identical grounded-emitter amplifiers whose collector circuits are tuned to 10.7 MHz. The three stages of both amplifiers are connected in a DC series chain across the battery voltage so that each stage receives one-third of the battery voltage.

The only difference between the two units is that two diodes are included in the biasing network of the IA508 unit. One of these, E1, secures constant current through the transistors and, consequently, stable gain. The other one, zener diode E2, secures a constant output level for the following discriminator at battery voltages between 10 and 15 V.

The IF amplifier operates both as amplifier and amplitude limiter, the two last stages of the IA508 unit operating solely as noise-limiter stages.

Technical Specifications

XF500

Frequency

10.7 MHz.

Insertion Loss

Max. 5 dB.

Bandwidth

XF501: max. 6 dB drop at ±15 kHz.

XF502: max. 6 dB drop at ±7.5 kHz.

XF504: max. 3 dB drop at ± 2.75 kHz.

Input Impedance

XF501: 2 kΩ//25 pF

XF502: 820 Ω//25 pF

XF504: 910 Ω//25 pF.

Output Impedance

XF501: $2 k\Omega//25 pF$.

XF502: 820 Ω//25 pF.

XF504: 910 Ω//25 pF.

IT502

Frequency

10.7 MHz.

Input Impedance

With XF501: 2 $k\Omega//25$ pF.

With XF502: 820 $\Omega//25$ pF.

With XF504: 910 $\Omega//25$ pF.

IA509

Frequency Range

10.7 MHz.

Supply Voltage

Nominal: 12.4 V

Maximum: 15.0 V

Minimum: 10.0 V

Must be capable of operation at: 9V.

3 dB Bandwidth

IA507: 150 kHz

IA508: 150 kHz.

Gain (typical)

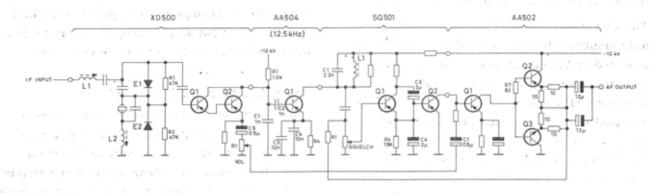
IA507: 65 dB

IA508: 75 dB.

Current Drain (at 12.4 V)

3 mA.

Discriminator, Squelch Circuit and AF Amplifier XD500, AA504, SQ501 and AA502



Description

The AF section of the receiver consists of the following modules:

XD500 Crystal discriminator. Depending on the channel spacing employed in the particular receiver, the following discriminator types are used:

> For 50 kHz channel spacing: XD501 For 25 kHz channel spacing: XD502 For 20 kHz channel spacing: XD502 For 12.5 kHz channel spacing: XD503.

SQ501 Squelch circuit.

AA502 AF amplifier.

For 12.5 kHz channel spacing only: AA504 Noise amplifier for SQ501.

Discriminator XD500

The discriminator employs a crystal whose points of parallel and series resonance are determined by coil L2 in conjunction with capacitors C3 and C4.

The 30 pF frequency of the crystal is approx. 10.715 MHz. The symmetry of the demodulation characteristic is adjusted with coil L1.

Because the discriminators require a high value of load impedance whereas the following amplifier AA505 requires a low value of generator impedance, the discriminator module incorporates an impedance converter in the form of a Darlington amplifier, which is characterized by having high input impedance and low output impedance. Its gain at the centre frequency is ap-

prox. -0.2 dB. The collector circuit of the Darlington amplifier is described in detail under Squelch Circuit SQ501 below.

AF Amplifier AA502

In order to be able to understand the operation of the squelch circuit it is necessary to study the AF amplifier AA502 first. This module consists of the following stages:

Driver stage

Push-pull output stage.

The driver stage, which uses transistor Q1, is a grounded-emitter amplifier with frequencydependent negative feedback. The input signal from the crystal discriminator is applied to the base via the volume-control potentiometer (R1) which is mounted on the cabinet proper.

The push-pull stage (Q2 and Q3) contains two complementary transistors (NPN and PNP). The transistors are matched and should not normally be replaced individually. They operate in Class B in a common collector configuration. The output is transformerless and matched for a 40-ohm speaker.

Squelch Circuit SQ501

The squelch circuit serves to suppress noise (hiss) and reduce current drain during nonsignal periods (stand-by). The squelch circuit is operated by noise voltages in the output signal of discriminator XD500.

The squelch circuit incorporates a squelch filter (L1 - C1) and a detector (Q1) followed by

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a DC amplifier (Q2) which performs a relay function.

The parallel-tuned circuit L1 - C1 is the collector circuit of the Darlington amplifier.

The circuit is tuned to 12 kHz, and noise signals amplified by the Darlington amplifier are selected by the circuit and fed to the squelch potentiometer together with a feedback DC voltage from AF amplifier AA502, whereafter the composite signal is applied to the base of Q1, which operates as a detector. This will cause a DC voltage, roughly equal to the peak value of the base signal, to build up across RC circuit R4 - C4. This DC voltage is fed directly to the base of transistor Q2, which operates as relay transistor. When the DC voltage reaches a certain level (approx. 0.5V), the internal resistance of the transistor will drop to a very low value and its collector potential approaches OV (chassis potential).

Because the collector of the relay transistor connects directly to the base of the driver transistor Q1 of the AF amplifier, the bias of the latter transistor will be very nearly shortcircuited.

The voltage at the junction of R8, R9, R10, and R11 in AF amplifier AA502 will approach the full battery voltage owing to the fact that the base bias of the control transistor is nearly short-circuited. This negative potential is fed back to the base of detector transistor Q1 in squelch circuit SQ501 via resistor R1 in SQ501 and the squelch potentiometer. This produces an increasing amount of feedback which shuts off AF amplifier AA502 even more effectively.

When a signal is being received, the noise components will be partly suppressed, causing the noise signal which is fed from the squelch filter to the base of the detector stage (Q1) to drop to below 0.5 V and the relay transistor (Q2) to begin to cut off. The result of this is that the control transistor in AF amplifier AA502 will again receive base bias, and the voltage at the junction of R8, R9, R10, and R11 begins to decrease towards one-half the battery voltage.

This voltage, as described above, is fed back to the detector stage in squelch circuit SQ501, causing it to become less conductive. This will in turn cause the collector voltage of the relay transistor to become more negative - in other words: the output stage changes rapidly from the non-conductive to the conductive condition.

Noise Amplifier AA504

The lower noise output level of discriminator XD503 in radiotelephones with 12.5 kHz channel spacing makes it necessary to insert an amplifier between the discriminator and squelch circuit SQ501. The load on the Darlington amplifier in this case is a resistor, and the load on the noise amplifier is the parallel-tuned circuit L1 - C1 in the SQ501 module.

The amplifier proper is a single transistor in a grounded-emitter circuit. A capacitor, C1, short-circuits the IF signal from discriminator XD503, and modulating frequencies are cut off by capacitors C2, C3, and C4. This arrangement results in maximum gain at 12 kHz.

Technical Specifications

XD500

Supply Voltage

Nominal: 12.4 V

Maximum: 15.0 V

Minimum: 10.0 V

Must be capable of operation at: 9.0 V.

Current Drain

At -12 V: 1.2 mA.

Bandwidth

XD501 (50 kHz channel spacing): ± 25 kHz XD502 (25/20 kHz channel spacing): ± 12 kHz.

XD503 (12.5 kHz channel spacing): ±6 kHz.

Output Voltage

XD501; at 1000 Hz and $\Delta f = \pm 10 \text{ kHz}$: 500 mV. XD502; at 1000 Hz and $\Delta f = \pm 3.3 \text{ kHz}$: 350 mV. XD503; at 1000 Hz and $\Delta f = \pm 1.7 \text{ kHz}$: 350 mV.

Harmonic Distortion

XD501: at $\Delta f = \pm 10 \text{ kHz}$: 3.5% XD502: at $\Delta f = \pm 3.3 \text{ kHz}$: 3.5%

XD503: at $\Delta f = \pm 1.7 \text{ kHz}$: 3.5%.

Noise Amplifier AA504

Supply Voltage

Nominal: 12.4 V

Maximum: 15 V

Minimum: 10 V.

Current Drain

At 12.4 V: 0.45 mA.

Gain

At 12 kHz and 12.4 V: 18 dB +4 dB/-2 dB.

SQ501

Supply Voltage

12.4 V nominal.

Current Drain

In squelched condition: Max. 0.5 mA.
In unsquelched condition: Approx. 0.03 mA.

Squelch Sensitivity (EIA measuring method)

After 40 dB suppression of the output noise, the squelch circuit must be capable of opening at a signal-to-noise ratio of 8 dB.

(At $\Delta f = 2/3 \Delta f_{max}$ and $F_{mod} = 1000 Hz$).

Maximum Output-noise Attenuation

Output noise must be capable of not less than $60~\mathrm{dB}$ attenuation.

AF Amplifier AA502

Supply Voltage

Nominal: 12.4 V

Maximum: 15.0 V

Minimum: 10.0 V

Must be capable of operation at: 9.0 V.

Current Drain

At nominal voltage without signal, with squelch: 0.6 mA. With signal: 3.0 - 34 mA.

Power Output

At nominal voltage and nominal input level: $200 \ \mathrm{mW}$.

Input Level

Nominal input level at 1000 Hz and full power output: 200 mV.

Frequency Response

With reference to 1000 Hz and -6 dB/octave, the limits are +2 dB and -8 dB.

Harmonic Distortion

At 1000 Hz and 200 mW output: 5%.

AF Noise Attenuation in Squelched Condition

At nominal input voltage: 40 dB.

D. Common Modules

Those functions of the radiotelephone which are common to both transmitter and receiver are handled by the following modules:

JP531	Junction panel containing voltage stabi-
	lizer circuit, and circuits for the speak-
	er-microphone.

$_{ m JP532}$	Junction panel containing circuits for
	adjustment of transmitter AF level as
	well as filters for operating voltage for
	individual receiver modules

XS511	Crystal shift unit for transmitter and
or	receiver containing switch, sockets,
XS531	and circuits for three transmitter and
	three receiver crystals. XS511 is used
	in type CQP510 radiotelephones and
	XS531 in type CQP530 radiotelephones.

Junction Panel JP 531

Junction panel JP531 contains the ADC circuit which protects the RF transistors in the transmitter output stage. This circuit is described in the text covering the transmitter section. A built-in zener regulator provides a stabilized 7.6 V supply. Junction panel JP531 also contains some resistors and capacitors which are employed in conjunction with the microphone circuit, and some of the connections to the multi-wire connector pass through the panel.

Junction Panel JP 532

Junction panel JP532 contains potentiometers for setting the maximum frequency swing of the transmitter (R1) and the tone level from a builtin tone transmitter (R2).

The panel also contains filters for operating voltages for a number of receiver modules.

Crystal Shift Unit XS531or XS511

The crystal shift unit contains sockets for three receiver crystals and three transmitter crystals. The maximum number of channels with which the radiotelephone can be equipped is therefore three

The receiver crystals are overtone crystals oscillating on their series resonant frequency (near the third harmonic). In series with each crystal is a series-resonant circuit consisting of a coil and a trimmer capacitor. By means of the variable capacitance, the frequency may be pulled to exactly the nominal frequency of the crystal.

In parallel with each transmitter crystal is a trimmer capacitor by means of which the frequency can be pulled to the nominal frequency of the crystal.

The channel selector has four positions three of which are used for switching between the three channels. In the fourth position, the radiotelephone is switched off. The switch sections are so designed that unused receiver crystals are disconnected whilst unused transmitter crystals are short-circuited to chassis potential.

The crystal shift unit moreover contains a main fuse through which flows the entire amount of current consumed by the radiotelephone, and a protective diode. Should voltage of the wrong polarity be applied, the diode will conduct and so short-circuit the battery voltage, with the result that the fuse blows and thus removes voltage from the radiotelephone.

Battery BU 501

The replaceable nickel-cadmium battery BU501 supplies the operating voltage required by the radiotelephone (nominal voltage is 12.4 V).

In normal operation the battery may be used for approx. ten hours before charging is necessary (see also Chapter I, section Operation).

The condition of the battery is checked by means of a filament lamp at the bottom of the radiotelephone cabinet as explained in Section A, Control Functions).

Speaker-Microphone Circuit

The speaker-microphone is integral with the cabinet and operates as a speaker during re-

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ception and as a microphone during transmission. Switching between the two functions is performed by two contact pairs which are actuated when the transmit button is operated (see also Section A, Control Functions).

Multi-Wire Connector J1

The multi-wire connector J1 on the top of the cabinet is used for making a few important

check measurements on the equipment and for connecting various extra accessories such as lapel microphone, earphone, etc.

The multi-wire connector contains nine pins. The table below specifies the points in the radiotelephone to which the individual pins connect as well as the functions performed by them.

Pin	Purpose
1	Battery voltage, negative with respect to chassis (pin 6)
2	Connection for earphone etc.
3	Connection for external microphone (between pins 3 and 8)
4	Short-circuits the speaker-microphone to pin 3 when an external microphone is connected.
5	Audio for an external tone receiver (if provided), taken off after the discriminator but ahead of the volume control.
6	Chassis (connects directly to the positive battery terminal when the equipment is switched on).
7	Discriminator test point, connects to test point 6 through 1 $\ensuremath{\mathrm{M}\Omega}$ resistor.
8	Connection for external microphone (between pins 3 and 8)
9	Available for special-purpose accessories

60.037-E1

CHAPTER III. ACCESSORIES A. Charging Units

Additional nickel-cadmium batteries and three types of charging units are available as standard accessories.

BU501 10-cell nickel-cadmium battery, 225 mAh.

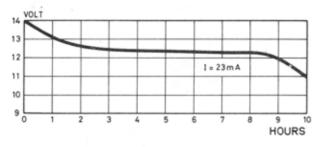
CU501 Charging unit with provision for connection of up to ten battery outlets.

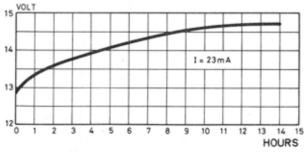
CU502 Charging unit with provision for connection of up to ten battery outlets and with built-in timer.

CU503 Charging unit with provision for connection of up to two battery outlets.

Battery BU501

As mentioned in Chapter I, the battery may be charged more than 500 times without appreciable reduction of its capacity. However, it should not be overcharged repeatedly as this will reduce its capacity.





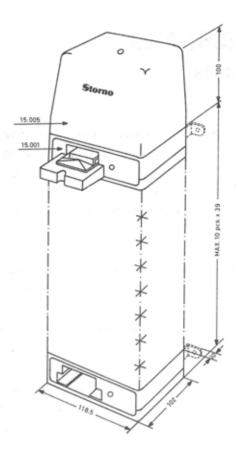
As shown in the illustration, the discharge curve is essentially straight-lined at a discharge current of 23 mA. When the voltage has dropped to approx. 11 volts, in practice

corresponding to approximately ten hours of operation, the voltage curve drops fairly sharply, and if the voltage across the battery goes below approx. 10 V there will be a risk of repolarization of one or more cells, which may then be ruined the next time the battery is charged. Strong polarity reversal of one or more cells will be evidenced by somewhat lower voltage for a normally charged (not overcharged) battery.

In cases where one radiotelephone is used by several persons or where other factors make it impossible to keep a check on the operating time so that the charging time cannot be predetermined with certainty, there are two methods of solving this problem. One consists in always operating the radiotelephone until the built-in pilot lamp shows that the battery is discharged, thereafter replacing the discharged battery with a fully charged spare battery. This can easily be carried in a pocket, thanks to its small size. The other method consists in discharging the battery before recharging it. However, the discharge current should not exceed 115 mA, which means that the shorting resistor employed should not be smaller than 110 Ω and be rated at not less than 3W. Discharge should not be allowed to continue past the point where the battery terminal voltage has dropped to approx. 11 V.

Charging Unit CU501

Charging unit CU501 consists of a power supply (15.005) to which a maximum of ten identical battery outlets (15.001) may be connected. A built-in switch permits switching the mains voltage input between 110 V AC and 220 V AC. The output from the secondary of the mains transformer (T1) is rectified in a bridge circuit (E1) and fed to the battery outlets. In each outlet, the charging current for the battery



flows through a resistor (R4) and a filament lamp (V1) which operates both as current regulator and pilot lamp. Normal charging current for each battery outlet is approx. 25 mA, and the time normally required for charging a discharged battery is 14 hours.

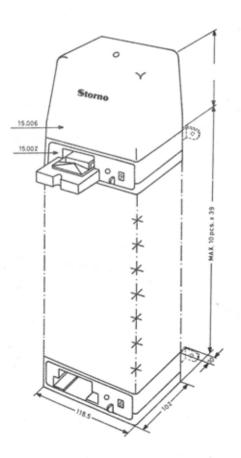
Charging Unit CU502

Charging unit CU502 consists of a power supply (15.006) to which a maximum of ten identical battery outlets (15.002) may be connected. Besides a bridge rectifier (E1), the power supply section contains a synchronous motor the driving shaft of which makes 1/12 revolution per hour, thanks to a gear reduction system. Each battery outlet moreover has a built-in counter which may be set to charge the battery for any desired number of periods between 1 and 9. The length of each period is one hour and a half, corresponding to approximately one hour's normal operation of the radiotelephone.

The cam wheel of the synchronous motor sees to it that contacts 01 make every one and onehalf hours, thereby causing electrolytic capacitor C1 to discharge through contacts 01, counter coil A, rectifier E2, and relay contacts A. This will cause counter relay A to move backwards one digit, and when digit 0 has been reached, the counter relay operates, causing contacts a to break the battery charging circuit. However, a very low value of charging current (approx. 0.6 mA) flows through a resistor (R3) to compensate for self-discharge.

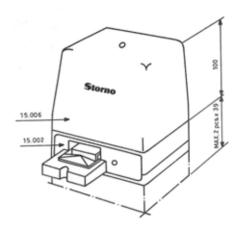
When contacts a of the counter relay are open, rectifier E2 will prevent charging current from flowing through the counter coil to the other battery outlets. Similarly, rectifier E3 will prevent the battery from discharging through the counter relay coil and the other battery outlets. Lamp V1 operates both as current regulator and pilot lamp.

Contacts a of the counter relay remain open until the outlet counter is once again set for charging.



Charging Unit CU 503

Charging Unit CU503 consists of a power supply (15.007) to which a maximum of two identical battery outlets (15.001) may be connected. The mains transformer (T1) has taps for both 110 V AC and 220 V AC. When the charging unit is



rewired for operation from another mains voltage, the fuse should be replaced with one of suitable rating. The output from the secondary of the mains transformer (T1) is rectified in a bridge circuit (E1) and fed to the battery outlets. In each outlet, charging current for each battery flows through a resistor (R4) and a filament lamp (V1) which operates both as current regulator and pilot lamp.

Common Specifications

Supply Voltage

110 V or 220 V AC, 50 Hz.

Charging Current

When battery is discharged: 22 - 27 mA. When battery is fully charged: 20 - 25 mA. (except as specified for CU502).

No-load Voltage 40 V DC.

B. Selective Tone Equipment

General

Space is provided in the cabinet for installation of a tone transmitter, and the cabinet is equipped with the cabling required for the purpose.

If the radiotelephone does not incorporate a tone transmitter, the space set aside for its installation will be covered by a plate to which the tone equipment cabling is soldered.

Either a TT501 single-frequency tone transmitter or a TT504 double-tone transmitter may be installed. In type CQP500R radiotelephones a TT503 tone transmitter may be installed in conjunction with control unit CB503. The TT503 permits switching between two tone frequencies. The tone frequency or frequencies desired should be stated when ordering the tone transmitter.

Single-tone Transmitter TT501

Tone transmitter TT501 is housed in an 18x18mm module can. The tone transmitter consists of a Hartley-type oscillator with feedback between the emitter and base.

The tuning coil L1 is wound on a miniature cup core with air gap and has a ferrite tuning slug for accurate adjustment of the oscillator frequency.

The total tuning capacitance is composed of three parallel-connected capacitors, C2, C3, and C4, of the type having a very small temperature coefficient.

In order to make the output voltage and frequency independent of any variations in operating voltage, the DC supply voltage for the oscillator is stabilized by a zener diode (E1).

Technical Specifications

Supply Voltage

Nominal 12.4 V Minimum 10.0 V

Maximum 14.0 V.

Current Drain

Nominal 20 mA at 12.4 V.

Frequencies

One of the following frequencies: 1435 Hz, 1520 Hz, 1530 Hz, 1670 Hz, 1750 Hz, 1830 Hz, 1860 Hz, 1980 Hz, 2000 Hz, 2135 Hz, 2200 Hz, 2280 Hz, 2400 Hz, 2450 Hz, 2600 Hz, 2812 Hz, 2900 Hz, 3047 Hz.

Frequency Stability

±1%

Harmonic Distortion

Max. 6%.

Output Level

 $3V \pm 1$ dB loaded by 1 M Ω .

Single-tone Transmitter TT503

Tone transmitter TT503 can be installed only in type CQP500R radiotelephones in conjunction with control unit CB503, which has a switch for selecting between high and low tone. The module is housed in an 18 x 18 mm can and consists of a Hartley-type oscillator with feedback between emitter and base. Tuning coil L1 is wound on a miniature cup core with air gap and has a ferrite tuning slug for accurate adjustment of oscillator frequency.

The total tuning capacitance is composed of two capacitors, C1 and C2, which have a very small temperature coefficient.

When a low tone is to be transmitted, an additional capacitor is added across the tuning capacitance. This capacitor is located on junction panel JP504 owing to space considerations. To transmit tone I (lower frequency), the switch on control box CB503 feeds -12V to terminal 3, and diode E2 is biased in the forward direction, diode E3 is blocked, and voltage is fed to the oscillator while limiter LI502 is disabled via terminal 2. The external tuning capacitor is connected to terminal 1 and the -12V battery terminal and will thus affect the oscillator frequency.

Chapter III. Accessories

To transmit tone II, -12V is fed to terminal 4, and diode E3 is biased in the forward direction, diode E2 is blocked, and voltage is fed to the oscillator. Limiter LI502 is disabled via terminal 2, and in AF amplifier module AA501/AA503 negative voltage is applied to the emitter of Q1 via a resistor, R5. This will reduce the gain so much that the two tones will produce the same frequency swing on the transmitter.

Technical Specifications

Supply Voltage

Nominal 12.4 V

Minimum 10.0 V

Maximum 14.0 V.

Current Drain at 12.4V

20 mA.

Frequency Stability

±1%.

Harmonic Distortion

Maximum 6%.

Output Voltage

 $7V \pm 1$ dB (load 1 M Ω).

Frequencies

1750 and 2135 Hz.

Frequency Deviation

Max. ±5 Hz.

Difference Between Tone Levels

Maximum 0.5 dB.

Double-tone Transmitter TT504

Double-tone transmitter TT504 delivers two tones simultaneously. It is housed in an 18 x 18 mm module can except for the tuning capacitors which are mounted outside the module can owing to space considerations.

The tone transmitter consists of two Hartleytype oscillators with feedback between emitter and base. The tuning coils, L1 and L2, are wound on miniature cup cores with air gap and have ferrite tuning slugs for accurate adjustment of the oscillator frequencies. The tuning capacitors are polystyrene capacitors of the type having a small temperature coefficient.

The two oscillators are connected together via two 1 M\Omega resistors so that feedback between the oscillators is avoided. In order to make the output voltage and the frequencies independent of any variations in operating voltage, the DC supply voltage for the module is stabilized by zener diode E1.

Technical Specifications

Supply Voltage

Nominal 12.4 V.

Current Drain

Nominal 3.8 mA at 12.4 V.

Frequencies

1400 Hz, 1530 Hz, 1670 Hz, 1830 Hz, 2000 Hz, 2200 Hz, 2400 Hz, 2600 Hz, 2900 Hz,

Frequency Stability

±1%.

Harmonic Distortion

Max. 6%.

Output Voltage

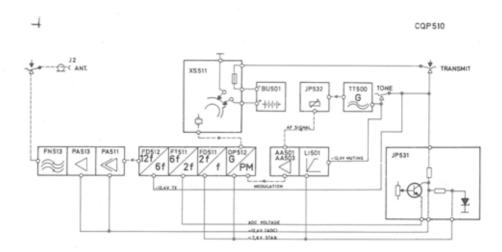
Loaded by 1 $M\Omega$ and with one oscillator switched off: 1.8 V.

Tone-button Function in Locally Controlled Radiotelephone

A tone call signal from a locally controlled radiotelephone is transmitted by pressing both the transmit button and the tone button at the same time.

The transmit button applies 12 V operating voltage to the transmitter and, via the tone button, to the tone transmitter. The tone signal from the operated tone transmitter is fed via the level control potentiometer in junction panel JP532 to the modulation input of the AF amplifier. Moreover, speech limiter module LI501 is disabled, thereby muting the signal from the microphone.

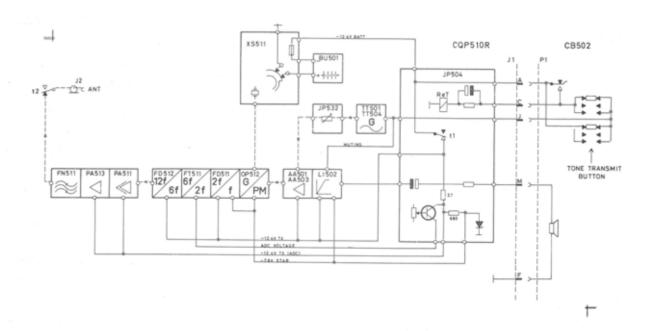
Chapter III. Accessories



Tone-button Function in Remotely Controlled Radiotelephone

Transmission of a tone call signal from a remotely controlled radiotelephone only requires operation of the tone button on the control box.

This will cause the transmitter to be switched on and operating voltage to be applied to the tone transmitter; also, speech limiter LI502 will be disabled. The tone signal from the tone transmitter is fed via the level control potentiometer in junction panel JP532 to the modulation input of the AF amplifier



CHAPTER IV. SERVICE A. General

As dispatched from Storno, the Stornophone 500 portable radiotelephone is completely tested and - unless otherwise agreed upon - tuned to the desired frequencies with an accuracy better than $\pm 2 \times 10^{-6}$ Hz/Hz.

In order to ensure optimum performance at any time, the Stornophone 500 radiotelephone should be subjected to preventive service inspections at regular intervals and tuned up if necessary. The frequency of such service inspections will depend both on the total number of operating hours and on operating conditions, but intervals between service inspections should not exceed six months.

Adjustments and repairs of mechanical or electrical defects outside module cans can be performed by any skilled radio technician who has the necessary tools and measuring equipment at his disposal and has acquainted himself with the operation of the Stornophone 500 radiotelephone by studying this manual.

Circuit repairs inside individual module cans should not be attempted as a rule, not only because of the miniaturization resulting from the use of small components as well as high component density but also because it will be cheaper in the great majority of cases to replace a module than to try to repair it.

Ordering of Spare Parts

When ordering components, modules, or mechanical parts for the Stornophone 500 radiotelephone please state their code numbers and designations. These are given in the electrical and mechanical parts lists of this manual.

Check Measurements

The Stornophone 500 radiotelephone is equipped with a number of test points for use when check-

ing its general condition and when performing adjustments to it.

Electrical locations of test points and a number of typical voltages and currents are stated in the circuit diagrams of Chapter V of this manual.

Physical locations of test points appear from drawing No. D401.242 at the end of the section "Adjustment Procedure".

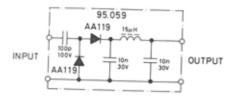
Measuring Instruments

The following measuring instruments are required for tracing faults in and making adjustments to the transmitter-receiver circuits:

Power supply, variable between 10 and 15V/300 mA/Ri < 2 Ω .

Multimeter, $Z_{\rm in} > 20~{\rm k}\Omega/{\rm V}$ (e.g. Unigor).

Probe, Storno type 95.059 (see diagram below).



Signal generator, 10,7 MHz, crystal controlled (e.g. Storno type G21, Code No. 95.163).

Signal generator, 146-174 MHz (e.g. Marconi type TF1066B).

AF valve voltmeter (e.g. Radiometer RV36).

DC oscilloscope (e.g. Telequipment S32A) or DC valve voltmeter ($R_i > 1 \text{ M}\Omega$).

Distortion meter (e.g. Radiometer type BKF6).

Tone generator, 300-5000 Hz (e.g. Philips model PM5100).

Deviation meter (e.g. Radiometer type AFM1).

RF wattmeter, 50 Ω 0-1W (e.g. Bird model 6254).

Modulation transformer with attenuator pad (Storno No. 60.5100).

If frequency adjustment is to be made, also: Frequency counter, 146-174 MHz (e.g. HP model 5245L with 5253B).

Opening the Cabinet

Remove the battery by sliding the locking pawl knob on the cabinet back plate upwards. This will release the battery, permitting it to be tipped out.

Thereafter remove the six screws holding the cabinet lid (identified in Fig.) and lift the lid off.

Installing Crystals

If your radiotelephone was dispatched to you with no crystals installed in it the cabling diagram in Chapter V will tell you where to place the crystals.

Tuning to frequency is performed as described in section D, "Adjustments".

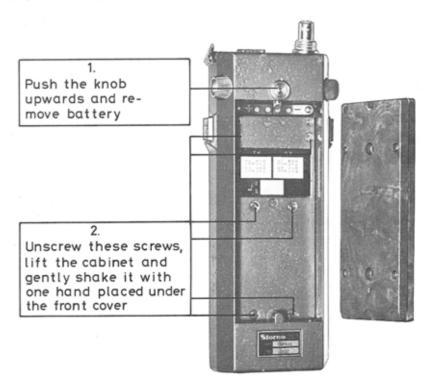
Crystal Ageing

The increasingly rigorous demands on frequency stability make the problem of crystal ageing grow in proportion. The problem is chiefly associated with mechanical vibrations in consequence of which all factors causing an increase or reduction in the effective mass of the quartz plate, either during or after its manufacture, will invariably result in a frequency change.

Some of the factors contributing to undesired ageing are infinitesimal changes in crystal mass due to inadequate cleanliness and to contamination of the crystal surface. Other causes are poor electrode materials checking and excessive humidity of the air or gas trapped in the crystal holder after it has been sealed.

Indirect causes of mass changes such as unnoticed surface tension and strain introduced by the crystal mountings will likewise produce frequency drift.

Undesired frequency ageing in metal-encased and hermetically sealed high-frequency crystal units is chiefly due to difficulties in regard to securing the necessary component purity and preventing the ingress of flux vapours and other volatile substances during the process of sealing the crystal holder. A contributory cause is the difficulty of securing an airtight enclosure that will last the life of the crystal unit - a result of weakness in



the solder used and of the glass-to-metal closure. It has been found that these ageing processing are intensified at high operating temperatures.

Reduction of Frequency Ageing Processes

Unfortunately, the frequency drift caused by longterm ageing cannot be countered by any kind of compensation technique because so many unpredictable factors enter the picture. However, it can be countered by adjusting the oscillator frequency at regular intervals, and in many cases this represents a satisfactory solution to the problem.

Undesired ageing occurring after production of the crystal has made it impossible for manufacturers to offer a guarantee against frequency changes caused by ageing. Instead a typical figure is stated, usually of the order of $\pm 10 \times 10^{-6}$ per year.

With AT cuts in metal holders, one year of ageing will cause frequency changes of the order of 5 to 10 $\,10^{-6}$. It should be noted that ageing processes vary with frequency, being more pro-

nounced for high-frequency crystals (thin plates) than for low-frequency crystals.

Readjustment of Frequencies

In consequence of the long-term ageing described above Storno recommend that radiotelephones which must meet stringent demands for frequency stability be subjected to readjustment of their oscillator crystals at intervals.

If the requirements for frequency stability exceed $\pm 5 \times 10^{-6}$ we wish to stress the need for such frequency adjustments. The times for making readjustments depend not only on individual crystals but on operating temperature as well. As a guide, however, it is suggested that the first adjustment be made after three or four months. The second readjustment should be made six or eight months later (these times are based on operation at normal ambient temperature).

Oven crystals will age somewhat more quickly. In this case, the first adjustment should be made after two or three months of operation, the second readjustment four or six months later.

B. Fault-finding

Visual Inspections

Any fault-finding operation should begin with careful visual inspection of the equipment. The technician should especially look for the following sources of trouble:

Defective cabling in the form of broken or loose wires.

Loose screws, these being frequent causes of poor chassis connections.

Foreign elements in the cabinet such as loose blobs of solder or cut-off wire ends from earlier jobs. Such particles can cause short-circuits in all parts of the circuits.

Measurements

Feed 12.4 V from an external power supply to the battery clips. Check that the receiver section receives operating voltage when in the stand by and receive conditions.

Turn the transmitter on and check the operating voltage for the transmitter section. If no operating voltage for the transmitter and receiver sections is present, check to see if the fuse in XS511 has blown.

Receiver Faults

If the loudspeaker is dead or only a hissing sound is heard, check for signal continuity in the AF section, IF chain, oscillator chain, and antenna change-over contacts.

The AF section may be checked by feeding an AF signal from a tone generator to terminal 5 of connector J1 and listening whether the signal

is coming through the speaker. The squelch and volume controls should be in their full clock-wise positions during this check.

The check on the IF chain should be made in two phases. First, apply a modulated 10.7 MHz signal to test point 3 of the input of the last IF amplifier unit, IA505/IA508.

AS DC voltage appears at test point 3 the signal should be applied through a capacitor.

If the signal is heard in the loudspeaker, the IF gain should be checked at test point 6. Typical gain in IA505/IA508: 75 dB (approx. 25 dB per stage).

Thereafter check the first half of the IF chain comprising IT502 and IA504/IA507 by applying a modulated 10.7 MHz signal to test point $\boxed{9}$ If there is signal continuity, check the gain of IF module IA504/IA507 by feeding a 10.7 MHz signal to the input of the module and measuring the gain at test point $\boxed{3}$.

Typical gain in IA504/IA507: 65 dB (approx. 22 dB per stage).

NOTE: In all gain measurements, the input signal level should be kept as low as possible in order to avoid limiting

Check the injection signal for mixer stage RC511 at test point $\boxed{2}$. A reading of 3 μA should be obtained.

Feed a modulated RF signal through the antenna connector. If desired, the antenna change-over contacts may be checked for voltage drops across the closed contacts.

Check the gain of the receiver RF section and mixer stage.

With an input signal of 4 mV EMF, 20 mV should be present at test point 9 (in IT502), measuring with an RF probe and multimeter.

The tracing of faults to one more modules should be followed up by DC measurements. For this purpose a number of typical voltages are given in the circuit diagrams in this manual. Check to see if these voltages are present.

The transistors should be checked by measuring their emitter and base voltages. The difference (the base bias) should be approx. 0.6V for silicon transistors and approx. 0.15V for germanium transistors.

NOTE: Both PNP and NPN transistors are used.

On PNP transistors, base and emitter voltages should be measured with respect to chassis potential and collector voltages with respect to -12.4V. On NPN transistors, the same voltages should be measured with respect to the opposite potential.

The transistors of defective stages may be checked by resistance measurements of their diode junctions (with no operating voltage applied to the stages in question).

Using the ohmmeter, the base-emitter and base-collector junctions should be measured in both the forward and back directions.

Low resistance should be measured in the forward direction (of the order of a few hundred ohms).

High resistance should be measured in the back direction (of the order of 1 k Ω to 100 k Ω), determined by the shunt resistors of the stages in question.

NOTE: At no time during resistance measurements on transistors may the ohmmeter current exceed 1 mA.

Transmitter Faults

Connect a wattmeter to the transmitter output (antenna connector J2). If output is low or entirely absent, check the output signals of the individual transmitter units, using a multimeter and RF probe.

Start making measurements at the transmitter output, working backwards towards the oscillator.

Outputs of individual units are designated as test points for which typical readings are given in the following test point chart.

The measurement of DC voltages on transistors in the power amplifier stages of the transmitter is difficult as these stages operate in Class C.

However, it is possible to measure the emitter voltage of a stage if it receives drive from the preceding stage.

Also in the case of the transmitter section it should be kept in mind that both PNP and NPN transistors are used. To facilitate checking of the transmitter circuits a number of typical DC voltages and currents are stated on the circuit diagrams.

The charts below list a number of test-point values which will be a useful aid in judging the performance of the radiotelephone in subsequent check measurements. In addition, they will provide an indication of whether readjustment is required.

Transmitter Section

Test Point	Module	Reading	Instruments
11	OP512	0.5 V	RF probe + multimeter
Collector Q1	FD511	1.0 V	RF probe + multimeter
12	FT511	1.6 V	RF probe + multimeter
Emitter Q1	FT511	0.5 V	RF probe + multimeter
ADC	FT511	4-6 V	DC-Voltmeter
13	FD512	1.6 V	RF probe + multimeter
Emitter Q1	FD512	0.5 V	RF probe + multimeter
14	PA511	3.5 V	RF probe + multimeter
Output	PA511	4.5 V	RF probe + multimeter
Output	PA513	17 V	RF probe + multimeter
Transmitter output	Ant. Connec.	500 mW	Wattmeter

Receiver Section

Input Signal (emf)	Test Point	Module	Reading	Instruments
None	1	OT511	ЗμА	
None	2	RC511	1 V	eter
10 mV ●	Signal Output	RA511	0.3 V	multimeter
4 mV ●	9	IT502	20 mV	+
3 mV ▲	3	IA505/508	30 mV	probe
3 mV ▲	4	IA505/508	70 mV	R
3 mV ▲	5	IA505/508	-1 V	
1 mV 🛦	6	IA505/508	0,2-0,3V	

- Signal generator set to the receiver frequency and connected to input of the receiver.
- ▲ Signal generator set to 10.7 MHz and connected to input of 1st IF Amplifier Module IA504/507.

Multimeter

The above table was compiled using a multimeter type Unigor S4. If other instruments are used, the instrument must have an input impedance of not less than 100 $k\Omega/V$ in order that the readings have some relevance.

C. Repairs

Replacing Modules

Replacements of module cans will not normally cause difficulties if reasonable care is taken. In particular, care should be taken to avoid damaging adjoining modules during the removal and insertion of modules.

If the module to be removed is located below one of the screen plates, the screen should be removed first. To do this, insert a tool having a wide contact face (the blade of a knife or a screwdriver having a broad blade) under the screen plate. Care should be taken to avoid inserting the tool between the screen plate and the modules below it in order to avoid damaging the module cabling. Unsolder the cabling of the module you wish to replace - it is a good plan to make a few notes about the wiring connections first so as to make it possible to have exactly the same cabling after the replacement job as before it.

Best possible chassis connection between the module cans is secured by solder tags on each can which are soldered to the tags of adjoining cans. One side should be unsoldered at a time. While applying the hot soldering iron, press the blade of a small knife down between the cans and free the can you wish to replace by wriggling it while the solder is still liquid.

When free, the module can should be pulled out carefully. Before inserting the new module can, the solder tags of adjoining modules should be cleaned of excess solder. Thereafter push the new module into place, carefully solder the tags together and solder the cabling to the new module

If the replaced module contains adjustable components, that module as well as adjacent modules should be adjusted in accordance with the directions given in this chapter.

Soldering

As mentioned above, soldering on the circuits boards used in the radiotelephone requires great care.

A low-voltage soldering iron of approx. 15W rating is required for soldering directly on

circuit boards while a 220V soldering iron of approx. 30W rating may be used for unsoldering tags in connection with replacements of module cans.

When soldering on, or in the immediate vicinity of, circuit boards, the soldering iron should not be applied for more than three seconds. The circuit boards are made of a glass fibre material which is perfectly capable of withstanding the heat for a short time, but there is a risk that the heat may cause the copper foil to work loose from the base material; there is also a risk that components may be damaged or detach themselves from the circuit board and fall down into the module can.

Correct soldering temperature is 270°C, and the use of a soldering iron having a tip not more than 3-4 mm in diameter is recommended. The tip should be shaped like a chisel or screwdriver.

Conventional 60/40 solder may be used, but solder having a flux content of approx. 0.5% is better suited. Conventional solder contains approx. 3.5% flux.

Excess solder should be removed with isopropyl alcohol, but this solvent should not be permitted to come into contact with components.

Repairing Modules

Repairs to circuits in module cans should be carried out only in very special cases, and the greatest care should be shown in order to avoid degrading the performance and specifications of the radiotelephone.

After having been taking out, the module can should be placed in a device which can hold it in a horizontal position but without gripping it so firmly that the can is damaged. Using a sharp knife (a scalpel is recommended), pry the circuit board loose while heating, with a soldering iron, the soldered joints between the module can and the copper foil of the circuit board. When all four sides have been pried loose, the circuit board may be taken out. A

pump should be used to suck away liquid solder while heat is being applied.

Replacements of components in the circuits require a high order of accuracy as the wiring and placement of components must not be altered New components should meet the same specifications as the ones which were removed. Liquid solder may be removed during replacement of components by means of a length of coaxial-cable braiding.

When the fault has been repaired, the circuit board should be put back in the screen can. Because of the miniature construction, the capacity of the can is fully utilized for which reason great care should be taken to prevent bare wires from getting into contact with the screen can, and to ensure that the internal insulating fail is properly placed in the can.

If the can was damaged during the repair job, it should be replaced with a new one.

When the circuit board is in place, a soldered joint should be made between the screen can and the chassis connection of the circuit board.

After having been repaired and put back in place, the module must be adjusted, as must also the adjoining circuits.

Replacement of Squelch and Volume Potentiometers

Access to the potentiometers is obtained by loosening the transmit and tone button contact pairs by removing the screws on the cabinet back plate (see sketch). The contact pairs may then be removed if care is taken. In order to avoid damaging the cabling and connections to the contact pairs, care should be taken to avoid pulling too hard.

Thereafter remove the potentiometer control knob, proceeding as follows:

- a) Remove the circlip holding the knob label in place.
- b) Take out label.
- c) Loosen screw.
- d) Release the grip of the collet on the potentiometer shaft by pulling the knob outwards while pressing the loosened screw inwards against the collet. Remove collet, sealing ring, screw, and knob.

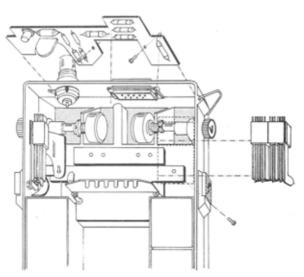
Unsolder the potentiometer cabling.

Release the potentiometer from the cabinet by loosening the potentiometer nut (a Storno No. 17.011 spanner may be used).

When installing a new potentiometer the control knob sealing ring should be lubricated with silicone grease before being put back.

While being clamped, the knob should be pressed so hard against the cabinet that a sufficiently high turning moment is obtained.

On completion of the job, any silicone grease that may have leaked from the sealing ring should be wiped off the cabinet and control knob.



Replacing Junction Panel JP531

To replace junction panel JP531, first loosen the contact pairs as described above. Then loosen the two screws holding the panel and multi-wire connector. The junction panel may now be lifted up carefully and the cabling unsoldered.

Replacing Connectors

To replace connectors, loosen junction panel JP531 as described in the preceding paragraph. Then unsolder the connector cabling and remove the connector. A Storno No. 17.012 spanner may be used for replacement of the antenna connector.

Replacement of Lamp in Charging Unit

Replacement of the indicator lamp in charging outlets type 15.001 and type 15.002 requires a sleeve, Storno Code No. 17.050, or a sleeve consisting of an 80 mm length of screened PVC tubing of 6.0 mm inside diameter and 0.5 mm wall thickness.

Remove the red indicator lamp glass from the front panel.

Press the sleeve down over the top of the lamp bulb. Press down and turn anti-clockwise. Then pull the sleeve and lamp out. Place a new lamp in the sleeve or tubing. Press the lamp down to grip the lamp holder. Press down and turn clockwise.

Pull out sleeve and insert the red indicator lamp glass.



LAMP NO. 92.5003

EXTRACTOR NO. 17.050

Adjustment of Charging Current

Replacement of the indicator lamp should always be followed by an adjustment of the charging current.

To do this connect a milliammeter in series with a zenerdiode (12.4V \pm 5%, code no. 99.5030) across the battery terminals.

Adjust potentiometer R6 for a meter reading of 22mA ±1mA. The potentiometer is accessible through a hole in the rear of the cassette.

D. Adjustment Procedure

General

If the radiotelephone has three channels, adjustment should be made on a basis of the middle frequency. Two-channel radiotelephones should be adjusted for equal performance on both channels. This can be accomplished by changing back and forth between channels during the process of adjustment and is important especially if the frequencies are widely separated. Because there is interaction between the circuits, the adjustments should be repeated several times until maximum performance and stability are obtained.

RECEIVER ADJUSTMENT

During adjustment, the radiotelephone must be powered from an external supply capable of being varied between 0 and 15V and delivering a minimum of 300 mA. The power supply should

be set to deliver 12.4V. During adjustment of the receiver, the power supply should be set for 25-30 mA current limiting.

Adjustment of Oscillator and Multiplier, OT511, RA512 and BP514

Instruments

RF probe, Storno type 95.059. Multimeter.

Procedure

Connect multimeter via RF probe to test point

Adjust coil L1 in OT511 for minimum multimeter reading.

Connect multimeter via RF probe to test point

Adjust coil L2 in OT511, coil L1 in RA512, and coil L1 in BP514 for maximum multimeter reading.

Adjustment of IF. and Discriminator, IT502, IA500, and XD500

Instruments

RF probe, Storno type 95.059.

Multimeter:

10.7 MHz signal generator, crystal controlled. DC valve voltmeter or DC oscilloscope.

Procedure

Terminate signal cable from signal generator in coupling coil (2 turns, 3 mm dia.). Couple coil to L1 in IT502 by pushing it in below the screen at IT502.

Connect multimeter via RF probe to test point $\boxed{3}$.

Tune coils L1, L2, and L3 in IA504/IA507 and coil L1 in IT502 for maximum multimeter reading at minimum signal generator output.

Connect multimeter via RF probe to test point 4.

Adjust coil L1 in IA505/IA508 for maximum multimeter reading at minimum signal generator output so that limiting does not occur.

Connect multimeter via RF probe to test point

Adjust coil L2 in IA505/IA508 for maximum reading.

Connect multimeter via RF probe to test point

Adjust coil L3 in IA505/IA508 for maximum reading.

Connect DC valve voltmeter or DC oscilloscope to test point $\boxed{7}$.

Adjust coil L2 in XD500 for 0V DC at test point 7.

Adjustment of VHF Circuits, BP511, RA511, BP512, BP513, and RC511

Instruments

Signal generator, 146-174 MHz. RF probe, Storno type 95.059. Multimeter.

DC valve voltmeter or DC oscilloscope

Procedure

Connect signal generator to antenna connector J2 and set it to the receiving frequency.

Connect DC valve voltmeter or DC oscilloscope to test point $\boxed{7}$.

Connect multimeter via RF probe to test point 3.

Increase signal generator output level until discriminator 0 can be read at test point 7

Adjust coil L2 in RA511 for maximum multimeter reading.

Adjust coil L1 in BP512, coil L1 in BP513, and coil L1 in RC511 for maximum multimeter reading.

While making the adjustments, the signal generator output should be reduced so that the multimeter reading is kept inside the most sensitive range.

Gain in the VHF circuits may be checked at test point 9.

For an RF input signal of 4 mV EMF, approx. 20 mV should be read on the multimeter.

Adjustment of Distortion and Sensitivity

Instruments

Signal generator, 146-174 MHz.

Distortion meter.

AF valve voltmeter (if not incorporated in the distortion meter).

DC valve voltmeter or DC oscilloscope.

Procedure

Connect DC oscilloscope or DC valve voltmeter to "Discriminator Zero", test point Connect distortion meter and (if used) AF valve voltmeter across loudspeaker terminals. Connect signal generator to antenna connector

J2 and adjust frequency to produce 0V DC at test point 7

Frequency-modulate signal generator with 1000Hz and frequency swing of $\Delta f = 70\% \Delta f$ max.

70% ∆f max. is:

for radiotelephones with 50 kHz channel spacing: 10.5 kHz.

for radiotelephones with 25 kHz channel spacing: 3.5 kHz.

for radiotelephones with 20 kHz channel spacing:

for radiotelephones with 12.5 kHz channel spacing: 1.75 kHz.

Set signal generator output level to 1 mV. Adjust coil L3 in IA505/IA508 for maximum AF voltage.

Adjust coil L1 in XD500 for minimum distortion. Adjust coil L1 in IT502 for minimum distortion. Adjust coil L1 in IA504/IA507 for minimum distortion.

Requirement: Distortion ≤5%.

As the adjustment of coil L1 in XD500 influence on the zero setting of the discriminator, all such adjustments should be followed by a checking of the discriminator zero with a 10.7 MHz signal applied as described in paragraph "Adjustment of IF and Discriminator".

The squelch should be open - that is, squelch potentiometer turned fully anti-clockwise.

Set volume control for 0.5V af voltage.

Calibrate the distortion meter so that the sum of signal, noise, and distortion corresponds to 100% when the filter is not inserted.

Insert the filter to remove the modulating frequency.

Reduce the output of the signal generator until the distortion meter reading increases to 25%,

corresponding to a 12-dB ratio between signal + noise + distortion and noise + distortion (12dB SINAD).

Adjust L1 in BP511 for best possible signal-tonoise ratio.

It should be possible to obtain a 12-dB signalto-noise ratio for 0.84V emf.

Checking the AF Output Amplifier

Instruments

Signal generator, 146-174 MHz. Distortion meter.

DC oscilloscope or DC valve voltmeter.

Procedure

Connect DC oscilloscope or DC valve voltmeter to test point

Connect signal generator to antenna connector J2 and set its frequency accurately to produce OV DC at test point | 7 | . Adjust signal generator output level to 1 mV EMF modulated by 1000 Hz at frequency swing of $\Delta f = 70\% \Delta f$ max. Output power should be not less than 200 mW with volume control turned full on.

Back off volume control until output power is 200 mW, corresponding to 2.8V across 40 Ω .

Check distortion. Requirement: ≤ 5%.

Checking the Squelch Circuit

Instruments

Signal generator, 146-174 MHz. Distortion meter with AF valve voltmeter. DC oscilloscope or DC valve voltmeter.

Procedure

Connect signal generator to antenna connector J2 and adjust to receiving frequency.

Connect DC oscilloscope or DC valve voltmeter to test point 7 .

Turn squelch potentiometer fully clockwise that is, squelch closed.

Increase supply voltage to 15 V.

Increase signal generator output level until squelch opens.

Squelch circuit should be capable of being opened by signal of 3 μV EMF.

Adjust supply voltage to 12.4V. Switch off signal generator (which should remain connected to the antenna connector).

Check that the squelch will close and open, both at nominal supply voltage of 12.4 V and at minimum supply voltage of 10 V.

Adjustment of Crystal Frequency XS511

Instruments

Frequency counter, 146-174 MHz.
Signal generator, 146-174 MHz.
DC oscilloscope or DC valve voltmeter.
T-network.

Procedure

Owing to considerable interaction in the multiplier chain the crystal frequency will be affected if a frequency counter is connected directly to it. It is therefore necessary to insert a T-network between the signal generator and the antenna connector and connect the frequency counter to the T-network.

Set the signal generator so that the counter indicates correct receiving frequency. Connect the DC oscilloscope or DC valve voltmeter to discriminator zero, pins 6 and 7 of connector J1. Instrument sensitivity should be sufficiently high to permit clear readings of frequency changes (approx. 1V).

Because the crystal frequency will change slightly when the lid is put on, adjustments should be made through holes in the back, with the lid screwed on. Adjust the trimmer capacitor for the channel selected to produce zero indication on the DC oscilloscope or DC valve voltmeter. On completion of the adjustment, the frequency should be accurate to better than $\pm 2 \times 10^{-6}$ - that is, $\pm 300~{\rm Hz}$ at 150 MHz.

TRANSMITTER ADJUSTMENT

The transmitter should be adjusted with the external power supply set to deliver 12.4V and produce approx. 300 mA current limiting.

Adjustment of Oscillator, Multiplier Chain, and Power Amplifier OP512, FD511, FT511, FD512, PA511, PA513, and FN511

Instruments

RF wattmeter, 50 Ω , 0-1W. RF probe, Storno type 95.059. Multimeter.

Procedure

Connect wattmeter to antenna connector J2. Turn ADC potentiometer fully anti-clockwise to produce maximum ADC voltage.

Turn transmitter on.

Connect multimeter via RF probe to test point

Adjust coil L1 in OP512 for maximum multimeter reading. ~~ 2 $~\sim$ $^{\vee}$

Connect multimeter via RF probe to test point 12 .

Adjust coils L1 and L2 in FD511 to produce maximum multimeter reading. $\forall\,\circ\,\smile\,\vee$

Connect multimeter via RF probe to test point

Adjust coils L1 and L2 in FT511 for maximum multimeter reading.

Connect multimeter via RF probe to test point 14.

Adjust coils L1 and L2 in FD512 for maximum multimeter reading.

If a wattmeter reading is obtained while making these adjustments, adjust for maximum output power while backing off the ADC potentiometer so that power output does not exceed 500 mW. Adjust the following coils for maximum output:

L1 and L2 in PA511. Sigur

L1 and L2 in PA513.

L1, L2, and L3 in FN511.

While making adjustments the ADC potentiometer should constantly be backed off so that output does not exceed 500 mW.

Reduce supply voltage until output is down to 200 mW.

Adjust coils L1 and L2 in FT511 and coils L1 and L2 in FD512 for maximum output. If circuits are flat-topped or saddle-shaped, middle of curve should be used.

Set supply voltage to 12.4V and ADC potentiometer to produce 500 mW output.

Check transmitter current drain.

Requirement: Current drain at 12.4V supply voltage and 500 mW output: 120 mA.

On completion of the adjustments set the supply voltage to 10V and check that output is 250 mW on all channels.

Adjustment of Modulation

Instruments

Tone generator.

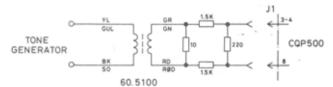
AF valve voltmeter.

Deviation meter.

Distortion meter.

Matching transformer, Storno type 60.5100. 750 μ sec de-emphasis network.

Procedure



Connect tone generator via matching transformer to pins 3/4 and 8 of connector J1.

Connect deviation meter to antenna connector J2 through suitable attenuator pad.

Turn transmitter on.

Set input voltage from tone generator to 10 mV and vary the frequency between 300 and 3000 Hz to obtain maximum possible frequency swing (the valve voltmeter must not be connected to the connector pins during the subsequent measurements in order to avoid ripple voltages). Adjust potentiometer R1 in JP532 for maximum permissible frequency swing on deviation meter. Check frequency swing at both positive and negative readings.

Maximum permissible frequency swing, Δf max., is as follows:

For radiotelephones with $50\,\mathrm{kHz}$ channel spacing: $15\,\mathrm{kHz}$.

For radiotelephones with 25 kHz channel spacing: 5 kHz.

For radiotelephones with 20 kHz channel spacing: 4 kHz.

For radiotelephones with 12.5 kHz channel spacing: 2.5 kHz.

Reduce input signal voltage to 70% Δf max. at modulating frequency of 1000 Hz.

Sensitivity should be better than 2 mV.

Connect distortion meter to AF output of deviation meter through 750 $\mu\,\mathrm{sec}$ de-emphasis network.

Adjust coil L1 in OP512 for minimum distortion.

Requirement: Distortion ≤ 7%.

Remove connector P1 from input (P1) and test the loudspeaker as a microphone.

Adjustment of Crystal Frequency XS511

Instruments

Frequency counter, 146-174 MHz. Attenuator pad.

Procedure

Connect frequency counter via suitable attenuator pad to antenna connector J2.

Screw lid on.

Turn transmitter on.

Adjust trimmer capacitor for the selected channel until the correct output frequency is indicated by the frequency counter. Because the lid affects the crystal frequency, adjustments should be made through holes in the back of the cabinet.

Requirement: Frequency accuracy on completion of the adjustments should be better than $\pm 2 \times 10^{-6}$, that is: ± 300 Hz at 150 MHz.

TONE TRANSMITTER ADJUSTMENT

Adjustment of Tone Transmitter TT501

Instruments

Frequency counter.

Deviation meter.

Distortion meter.

Procedure

Connect deviation meter to antenna connector J2.

Connect distortion meter and frequency counter to AF output of deviation meter.

Press transmit button and tone button.

Adjust frequency swing to 70% Δf max., using potentiometer R2 in JP532.

Adjust tone frequency to nominal value, using coil L1 in TT501.

Requirement: ≤ 0.5% (5 Hz per 1000 Hz).

Distortion measured with distortion meter and without de-emphasis in deviation meter: Distortion $\leq 3\%$.

Adjustment of Tone Transmitter TT504

Instruments

Frequency counter.

Deviation meter.

Distortion meter.

Procedure

One oscillator in TT504 should be switched off while the other one is being checked. To do this,

short-circuit to chassis the base of the transistor you wish to switch off.

Connect deviation meter to antenna connector J2.

Connect distortion meter and frequency counter to AF output of deviation meter.

Operate transmitter button and tone button.

Adjust frequency swing, using potentiometer R2 in JP532, to 35% Δf max. for one tone.

Then switch to other tone and check frequency swing.

Because of de-emphasis network R3-C4 in JP532 the two tones should produce identical readings ± 1 dB.

Alternatively, adjust potentiometer R2 in JP532 so that mean frequency swing for the two tones is $35\% \Delta Fmax$.

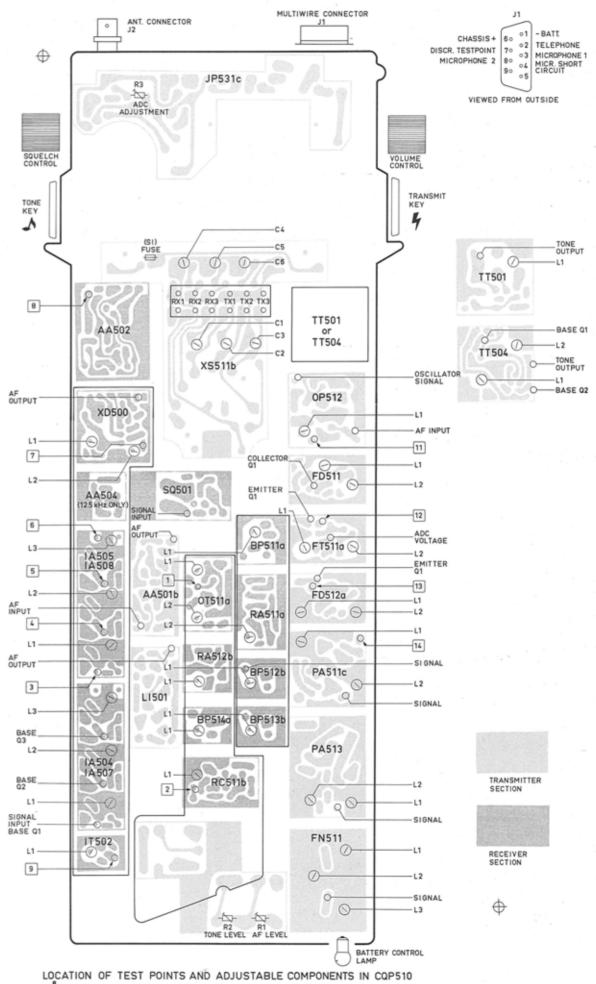
Requirement: $\Delta f_{\text{tone}} = 70\% \Delta f_{\text{max.}} \pm 1 \text{ dB.}$

Tone frequencies should be adjusted to nominal frequencies by the aid of coils L1 and L2 in TT504.

Requirement: Frequency accuracy should be better than 0.5% (5 Hz per 1000 Hz).

Distortion, measured with distortion meter and without de-emphasis in deviation meter; Distortion $\leq 3\%$.

{	



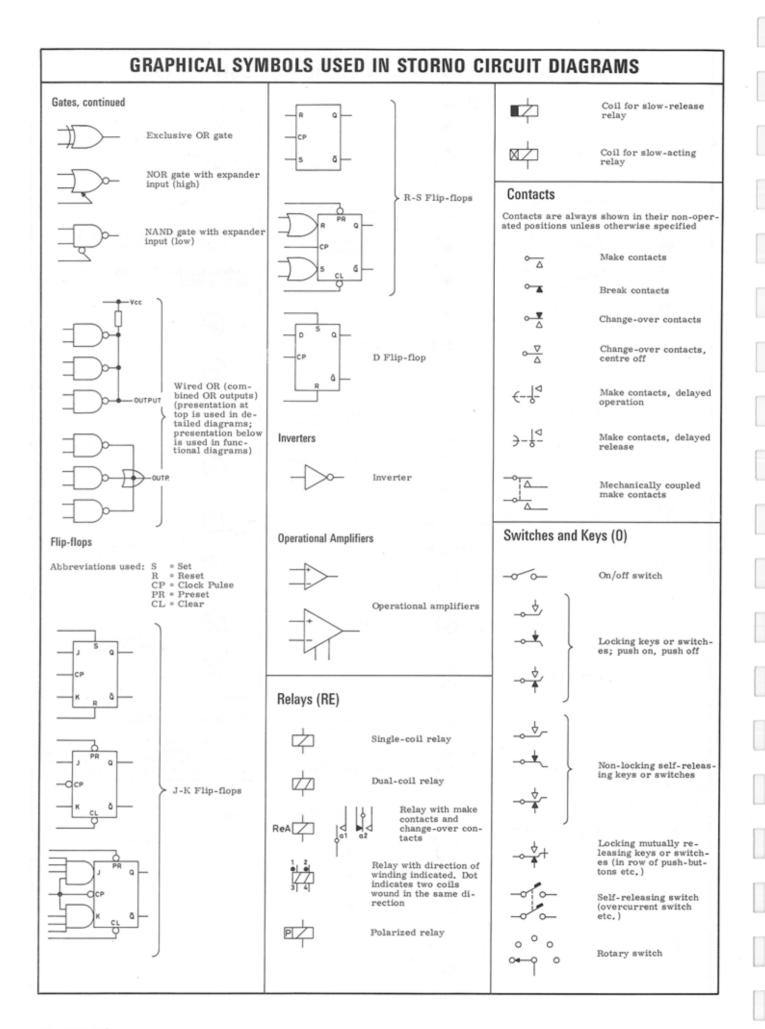
MÅLEPUNKTER OG JUSTERBARE KOMPONENTERS PLACERING I CQP510

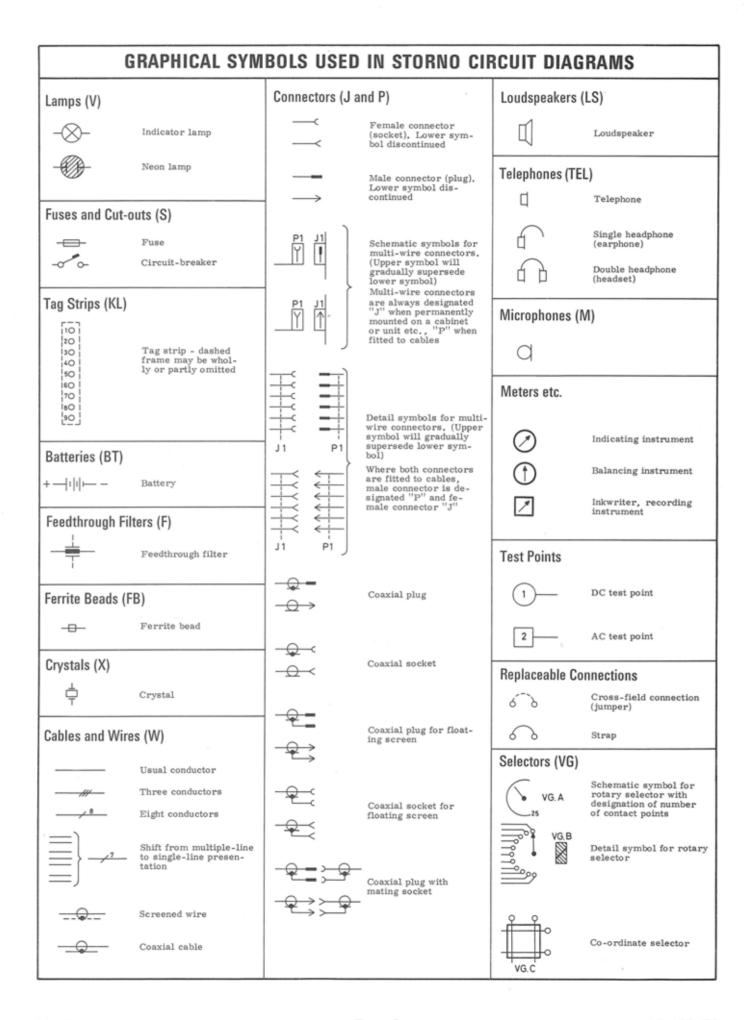
D401.242

CHAPTER V. DIAGRAMS AND ELECTRICAL PARTS LISTS

	3727 . I 15 0 .	

GRAPHICAL SYMBOLS USED IN STORNO CIRCUIT DIAGRAMS Resistors (R) Diodes (E) P-channel dual gate ₩ Diode Resistor Resistor with fixed tap GATE 2 Bridge rectifier N-channel JFET tetrode Variable resistor Resistor with movable Series-connected stabilizer diodes within one Varistor (voltage-dependent resistor) P-channel JFET Light-sensitive diode (Photosensitive diode) tetrode Temperature-dependent Insulated Gate Field Effect Transistors resistor with negative temperature coefficient Light-emitting diode (IGFET or MOS) Light-sensitive resistor (Photosensitive resistor) Zener diode (unidirectional) SUBSTR. Zener diode (bidirec-tional) N-channel IGFET (MOS) SOURCE Capacitors (C) Capacitor Tunnel diode Variable capacitor Varactor diode (capacitance diode) P-channel IGFET Trimmer capacitor Controlled rectifier, (MOS) PNPN (N-thyristor) Feedthrough capacitor Controlled rectifier, NPNP (P-thyristor) Electrolytic capacitor N-channel dual gate Transistors (Q) IGFET (MOS) Coils (L) Transistor, PNP RF coil, air core Transistor, NPN Coupled RF coils, air P-channel dual gate IGFET (MOS) RF coil with core Light-sensitive transis-tor Integrated Circuits (IC) RF coil with adjustable Unipolar transistor with N-type base Several integrated circuits contained within one case are designated by one common number followed by an identifying letter (a, b, c etc.). Thus, circuits ICla, IClb and IClc are contained within one case. Unipolar transistor with P-type base AF choke Transformers (T) Junction Field Effect Transistors (JFET) Gates Transformer with adjustable RF cores AND gate N-channel JFET Transformer with iron OR gate P-channel JFET NAND gate Transformer with screen connected to chassis N-channel dual gate JFET NOR gate SOURCE





Replacement of Contact Sets in COP510/COP530

The conversion parts listed below are required for the replacement of spring contact sets 47.0278 and 47.0277 with microswitches:

Microswitch complete with mounting hardware and operating lever (for tone button). Storno No. 47.0558.

Microswitch complete with mounting hardware, operating lever, and wiring board (for transmit button). Storno No. 47.0559.

Coaxial cabling. Storno No. 18.0649.

A 0.3 $\mu\mathrm{F}$ tantalum capacitor, Storno No. 73.5079, is required in some cases.

Procedure

Unsolder and remove the coaxial cabling going from the transmit button spring contact set to the antenna connector, receiver input, and transmitter output.

Loosen screw marked "A". The transmit button contact set may now be tipped up above the cabinet side.

- Unsolder two pink leads from pin 4 of connector J1. Solder them together and insulate them.
- 2 In equipments including Junction Panel JP531c (recent type) turn over capacitor C5 (0.3 μF) so that its minus terminal faces resistors R5 and R6.

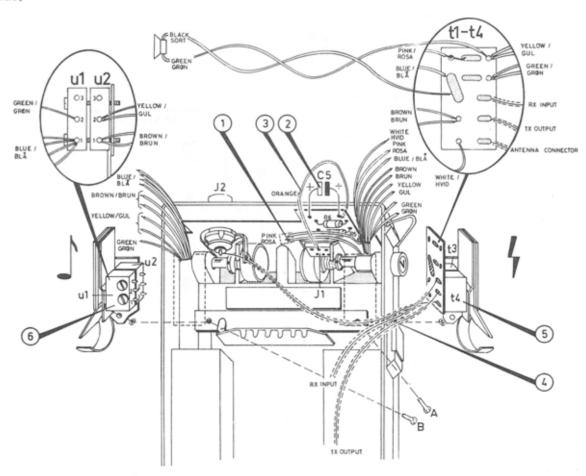
In equipments including Junction Panel JP531 (early type) replace resistor R7 (470 Ω) with a 0.3 μ F capacitor (C5), Storno No. 73.5079. Connect the capacitor with its minus terminal facing resistors R5 and R6.

Install an orange lead from the minus terminal of C5 on JP531 or JP531c to pin 4 of connector J1.

Remove the transmit button contact set after having previously unsoldered the connected cabling.

4 Connect the new coaxial cabling, No. 18.0649, to the wiring board on microswitch 47.0559 (as shown in the sketch).

Solder the coaxial cabling to the antenna connector.



Insert the microswitch in the cabinet and secure it with the screw marked "A".

The cabling of the contact set which was removed previously should next be soldered to the microswitch (as shown in the sketch).

Connect the coaxial cabling to the receiver input and transmitter output.

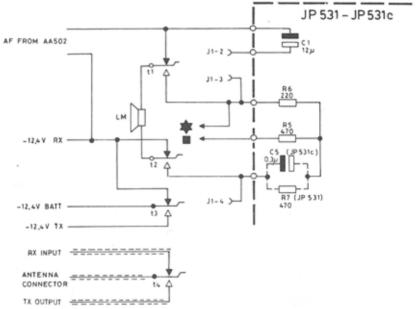
Remove the tone button spring contact set by loosening the screw marked "B" in the sketch and unsoldering the contact set cabling.

6 Solder the cabling to microswitch 47.0558 (see sketch for connections).

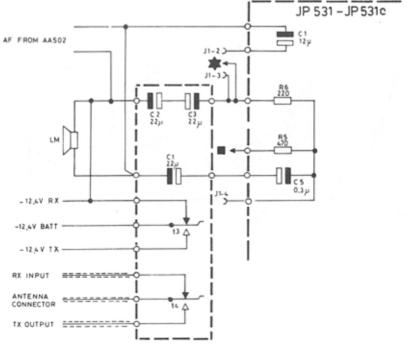
Insert microswitch in the cabinet and secure it with the screw marked "B".

Mode of Operations

Contact functions before replacement of contact set:



Contact functions after introduction of microswitches:



25

26

27

White

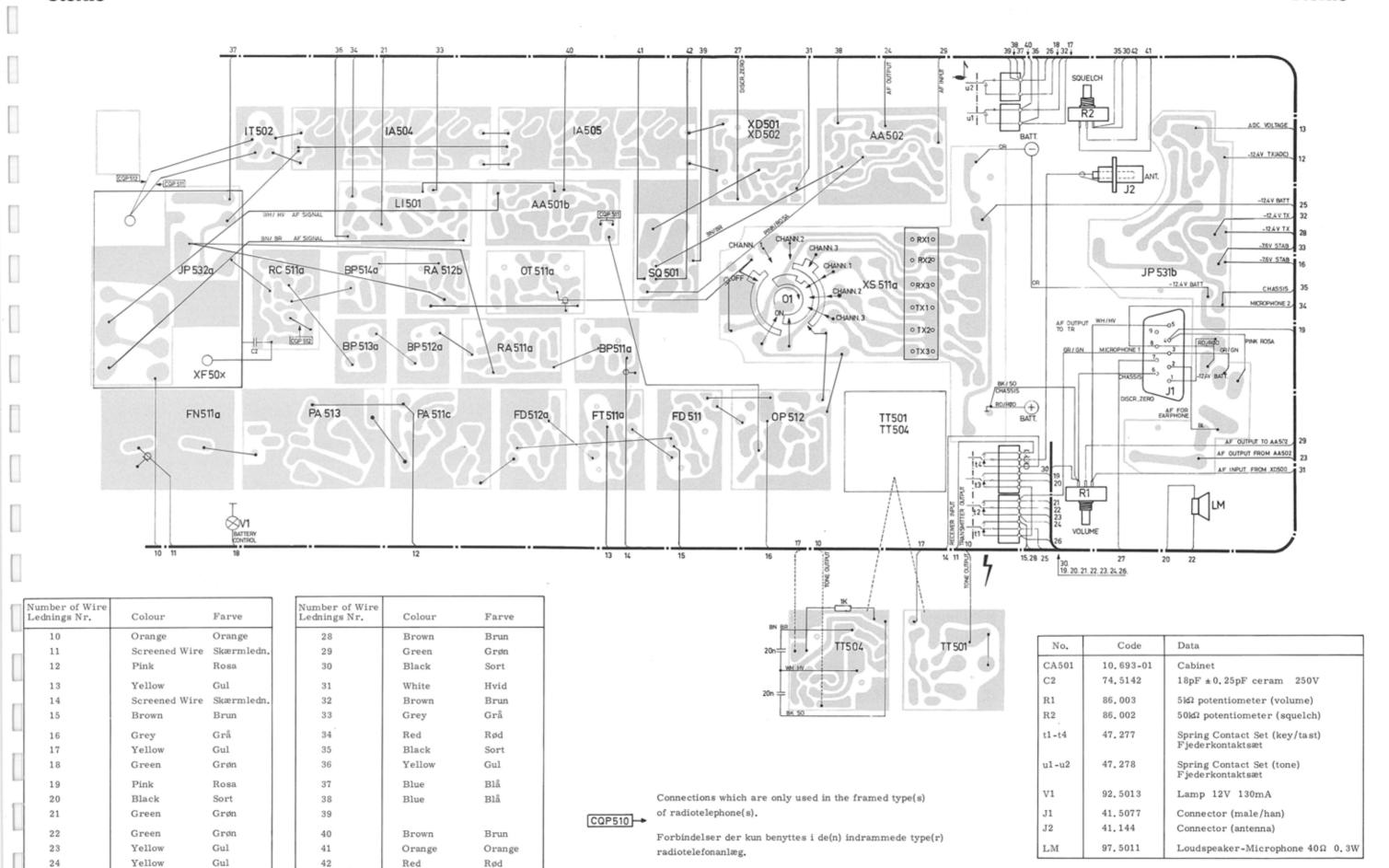
Blue

Yellow

Hvid

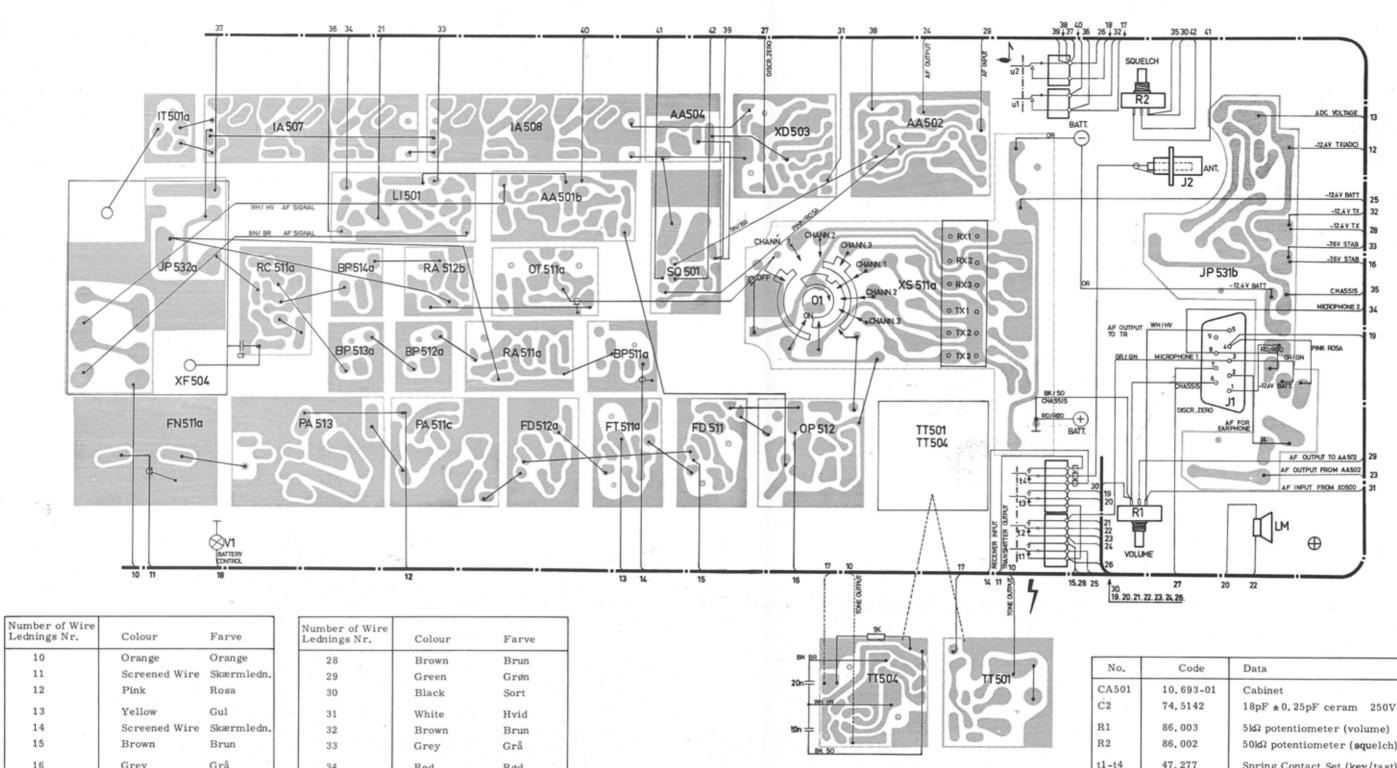
Blå

Gul



CABLE FORM KABLING

CQP511, CQP512



Lednings Nr.	Colour	Farve
10	Orange	Orange
11	Screened Wire	Skærmledn.
12	Pink	Rosa
13	Yellow	Gul
14	Screened Wire	Skærmledn.
15	Brown	Brun
16	Grey	Grå
17	Yellow	Gul
18	Green	Grøn
19	Pink	Rosa
20	Black	Sort
21	Green	Grøn
22	Green	Grøn
23	Yellow	Gul
24	Yellow	Gul
25	White	Hvid
26	Blue	Blå
27	Yellow	Gul

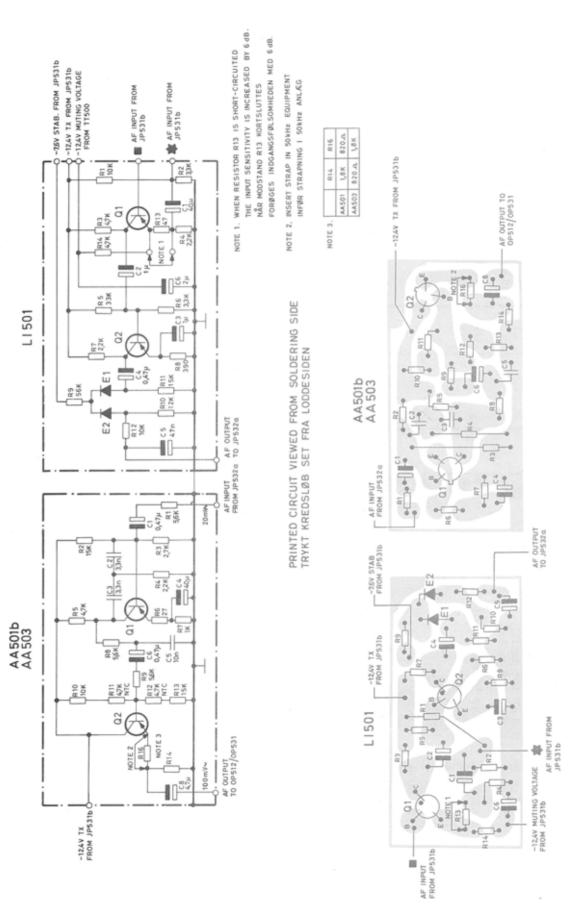
Number of Wire Lednings Nr.	Colour	Farve
28	Brown	Brun
29	Green	Grøn
30	Black	Sort
31	White	Hvid
32	Brown	Brun
33	Grey	Grå
34	Red	Rød
35	Black	Sort
36	Yellow	Gul
37	Blue	Blå
38	Blue	Blå
39		
40	Brown	Brun
41	Orange	Orange
42	Red	Rød

No.	Code	Data
CA501	10,693-01	Cabinet
C2	74.5142	18pF ± 0.25pF ceram 250V
R1	86.003	5kΩ potentiometer (volume)
R2	86,002	50kΩ potentiometer (squelch)
t1-t4	47.277	Spring Contact Set (key/tast) Fjederkontaktsæt
u1-u2	47.278	Spring Contact Set (tone) Fjederkontaktsæt
V1	92.5013	Lamp 12V 130mA
J1	41.5077	Connector (male/han)
J2	41,144	Connector (antenna)
LM	97.5011	Loudspeaker-Microphone 40Ω 0.3W

CABLE FORM KABLING

CQP514

D401.250



TRANSMITTER SECTION SENDERSEKTION

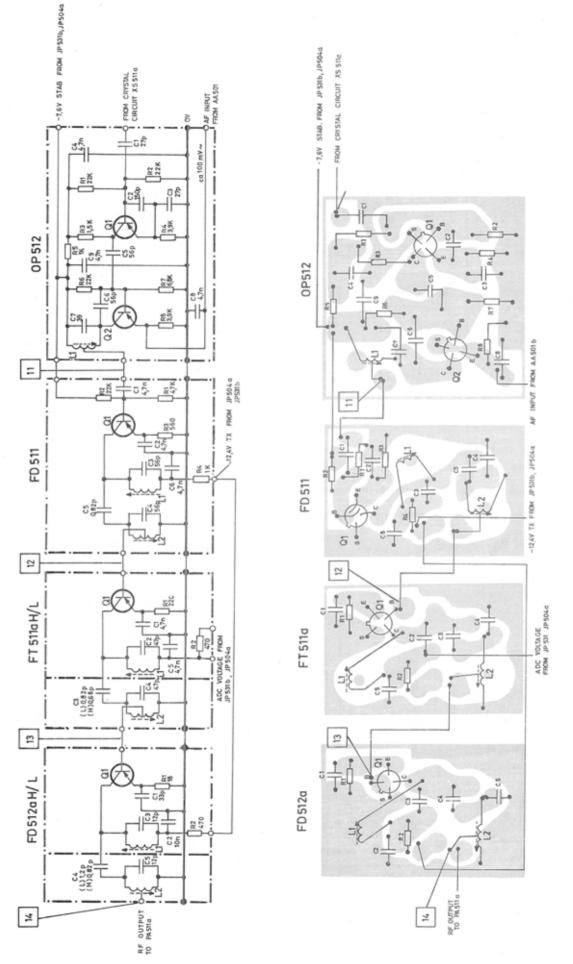
CQP510, CQP530

Storno

TYPE	NO.	CODE	DATA	
AA501b		114		
AASO3		10,2019	Audio Amplifier	
	C3	73,5073	0.5 µF 10% tantal 3.3 nF 10% polyest. FL	107
	C 24	73,5075	40 μ F -20 +75% tantal 10 nF 10% polvest. FL	30 200 200
	95 Ce	73,5073	5 µF 10% tantal	101
	C8	73,5080	7 µF	100
	R1	80,5058	.6 kg	0,1W
	R2	80,5063	15 kg 5%	0,1W
	H3	80,5054	2%	0.1W
	77 72 72	80.5053		0.1W
	R6	80,5030	200	0.1W
	R7	80,5049	10	
	R8	80,5058	5.6 kg 5%	0,1W
	K3	80, 5058	0,0	0.1W
	R11	89, 5009	4.7 kg 20% NTC	***
	R12	89,5009	209	
	R13	80,5063	5% carbon fi	0,1W
AA501	R14		2%	0.1W
AA503	R14	80, 5048	820055%	0.1W
AA503	R16		3 E	0.1W
	1			
	201	99,5115	Transistor BC179	
	2	0.00	3	
1501		10 996	Timiton Amnifian	
·)			TARREST CAMPACATO	
	55	200	-20 +7	38
	3 0	000	1,17 -20 +50% tantal	167
	0.4 7	3,51	i Eu	16V
	CS	es.	7 nF -2	20V
	Ce	3, 50	2 μF -20 +50% tantal	15V
	R1	80,5061	10	0.1W
	KZ	80,5055	KG 5%	0.1W
	R3	80,5057	2 2 3 3	0.1W
	K4	80,5053	2%	0.1W
	K3	80,5067	11 100	0.1W
	R.0	80 5053	50%	0. 1 W
	R8	504	390 02 5% "	0.1W
				٠l

	0.1W 0.1W 0.1W 0.1W 0.1W			CQP510,
DATA	56 kΩ 5% carbon film 12 kΩ 5% " " " 15 kΩ 5% " " " 10 kΩ 5% " " " 47 Ω 5% " " "	Diode OA200 Diode OA200	Transistor OC306/2 Transistor OC306/2	SECTION N
CODE	80,5070 80,5062 80,5063 80,5061 80,5033 80,5033	99,5028	99,5019	MITTER RSEKTIO X401.146/2
NO.	R9 R10 R11 R12 R13 R13	E1	Q2 Q2	SMIT ERSE x401.
TYPE				TRANSMITT SENDERSEK





Storno

PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

TYPE	NO.	CODE	DATA	
FD512aH FD512aL		10,1316	Frequency Doubler	
FD512H FD512L	CC	511 510 514 512 512 512	33 pF 2% ceram NO75 TB 10 nF -20 +80% ceram II PL 12 pF ± 0, 5 pF ceram NO75 TB 0, 82 pF ± 0, 1 pF ceram P100 BD 1, 2 pF ± 0, 25 pF ceram N150 BD 12 pF ± 0, 5 pF ceram NO75 TB	250V 20V 250V 250V 250V 250V 250V
	R1 R2	80,5028 80,5045	18Ω 5% carbon film 470Ω 5%	0, 1W 0, 1W
FD512H FD512L FD512H FD512L	1122	61.907 61.905 61.993 61.904	RF coil/HF spole 156-176 MHz RF coil/HF spole 146-156 MHz RF coil/HF spole 156-176 MHz RF coil/HF spole 146-156 MHz	
	Q1	99,5169	Transistor AF202S	
FT511aH FT511aL		10,1318	Frequency Tripler Frequency Tripler	
FT511H FT511L	222225	74.5108 76.5090 74.5121 74.5122 76.5090	4,7 nF -20 +80% ceram II PL 47 pF 5% polystyr TB 0,68 pF ±0,1 pF P100 BD 0,82 pF ±0,1 pF P100 BD 47 pF 5% polystyr TB 4,7 nF -20 +80% ceram II PL	20V 63V 250V 250V 63V 20V
	R1 R2	80,5041 80,5045	220 Ω 5% carbon film 470 Ω 5% "	0,1W 0,1W
FT511H FT511L	L1 L2 L2	61, 905 61, 903 61, 908	RF coil/HF spole 73-89 MHz RF coil/HF spole 78-89 MHz RF coil/HF spole 73-78 MHz	
	ଦୀ	99,5067	Transistor AF106	
FD511		10,1086	Frequency Doubler	
	CC	74.5108 74.5101 74.5111 74.5111 74.5122	4,7 nF -20 +80% ceram II PL 4,7 nF -20 +80% ceram II PL 56 pF 2% ceram NO75 TB 56 pF 2% ceram NO75 TB 0,82 pF ±0,1 pF ceram P100 BD 4,7 nF -20 +80% ceram II PL	20V 20V 250V 250V 500V 500V
			Transport of the state of the s	

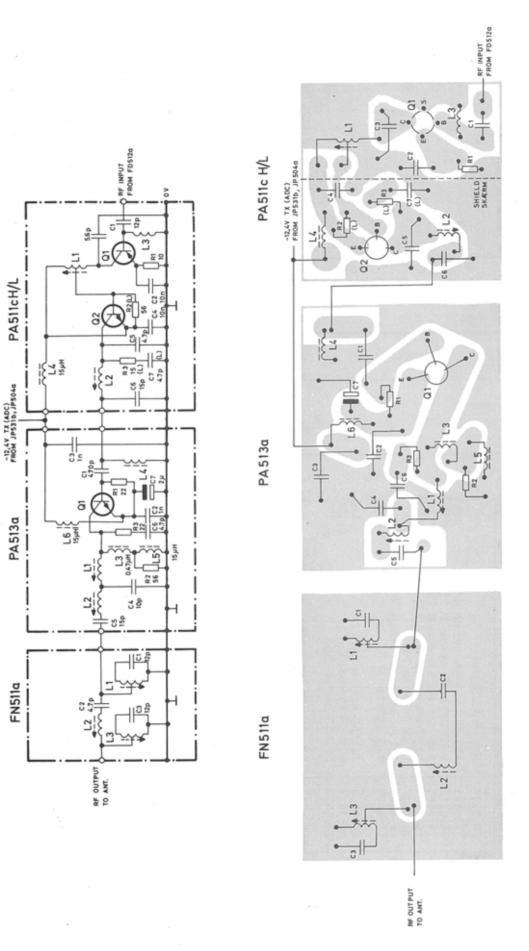
R1 80. 5057 4, 7 kD 5% carbon film 80. 5046 560 25 kD 5% " " " " " " " " " " " " " " " " " "	TYPE	NO.	CODE	DATA	
L1 61,744 RF coil/HF spole 24,3 - 29 MHz L2 61,745 RF coil/HF spole 24,3 - 29 MHz L2 99,5067 Transistor AF106 10,1120 Phase Modulator C1 74,5107 27 pF 2% ceram NO75 TB C2 76,5103 150 pF 2,5% polystyr C3 74,5110 56 pF 2% ceram NO75 TB C4 74,5111 56 pF 2% ceram NO75 TB C5 74,5111 56 pF 2% ceram NO75 TB C6 74,5111 56 pF 2% ceram NO75 TB C7 74,5111 56 pF 2% ceram NO75 TB C8 76,5061 4,7 nF 10% polyest FL C9 76,5061 4,7 nF 10% polyest FL C9 76,5061 4,7 nF 10% polyest FL R1 80,5065 22 k3 5% " " " R2 80,5065 22 k3 5% " " " R3 80,5065 3,9 k3 5% " " " R6 80,5066 6,8 k3 5% " " " R7 80,5069 6,8 k3 5% " " " R8 80,5066 7 Transistor AF124 Q1 99,5073 Transistor AF124		R1 R2 R3 R4	80, 5057 80, 5065 80, 5046 80, 5049	carbon film	0,1W 0,1W 0,1W 0,1W
Q1 99.5067 Transistor AF106 10.1120 Phase Modulator 74.5107 27 pF 2% ceram NO75 TB 75.5061 4,7 nF 10% polystyr 75.5061 4,7 nF 10% polysest FL C5 74.5111 56 pF 2% ceram NO75 TB 74.5111 56 pF 2% ceram NO75 TB 74.5111 56 pF 2% ceram NO75 TB C6 74.5111 56 pF 2% ceram NO75 TB C7 74.5111 56 pF 2% ceram NO75 TB C8 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL R1 80.5065 22 k2 5% carbon film R2 80.5065 1,5 k2 5% ii ii R3 80.5065 1,5 k2 5% ii ii R6 80.5065 22 k2 5% ii ii R7 80.5066 22 k2 5% ii ii R8 80.5066 3,9 k2 5% ii ii C1 783 C01/spole 11,3 - 14,6 MHz Q1 99.5066 Transistor AF121 Q2 Transistor AF124		L1 L2		coil/HF spole 24, 3 - 29 coil/HF spole 24, 3 - 29	
10.1120 Phase Modulator 74.5107 27 pF 2% ceram NO75 TB 76.5103 150 pF 2,5% polystyr 74.5156 4,7 nF 10% polyest FL 74.5111 56 pF 2% ceram NO75 TB 74.5111 56 pF 2% ceram NO75 TB 74.5111 56 pF 2% ceram NO75 TB 74.5111 39 pF 2% ceram NO75 TB 74.5117 39 pF 2% ceram NO75 TB 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 76.5061 1,5 kΩ 5% "" " 80.5065 22 kΩ 5% "" " 80.5066 3,9 kΩ 5% "" " 80.5069 6,8 kΩ 5% "" " 80.5059 6,8 kΩ 5% "" " 80.5059 6,8 kΩ 5% "" " 80.5056 3,9 kΩ 5% "" " 80.5056 Transistor AF121 Transistor AF124		Q1	99,5067		
74.5107 76.5103 76.5103 76.5103 76.5103 76.5104 76.5061 74.5111 56 pF 2% ceram NO75 TB 74.5111 56 pF 2% ceram NO75 TB 74.5117 39 pF 2% ceram NO75 TB 74.5117 39 pF 2% ceram NO75 TB 74.5117 74.5117 39 pF 2% ceram NO75 TB 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 76.5061 76.5061 78.5065 22 kΩ 5% carbon film 80.5065 22 kΩ 5% ii ii 80.5065 80.5066 80.5066 80.5066 80.5066 80.5066 80.5066 80.5066 80.5066 80.5066 80.5066 80.5066 80.5067 80.5069 80.5069 80.5069 Transistor AF121 Transistor AF121	512		0.1120	Phase Modulator	
76.5103 150 pF 2, 5% polystyr 74.5156 27 pF 2% ceram N750 TB 74.511 56 pF 2% ceram N075 TB 74.511 56 pF 2% ceram N075 TB 74.511 39 pF 2% ceram N075 TB 74.511 39 pF 2% ceram N075 TB 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 80.5065 22 kG 5% arbon film 80.5065 22 kG 5% "" " 80.5065 3,9 kG 5% "" " 80.5066 6,8 kG 5% "" " 80.5066 7 Transistor AF121 7 Transistor AF121		Cl	5107	27 pF 2% ceram NO75 TB	250V
76.5061 74.5111 74.5111 75.5061 74.5111 75.5061 74.5111 75.5061 74.5117 75.5061 74.5117 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5061 76.5063 76.5063 76.5064 76.5064 76.5064 76.5064 76.5065 76.5065 76.5066 76.506		0 C	5103		30V
74.5111 56 pF 2% ceram NO75 TB 74.5111 56 pF 2% ceram NO75 TB 74.5117 39 pF 2% ceram NO75 TB 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 80.5065 22 kΩ 5% "" " 80.5056 1,5 kΩ 5% "" " " 80.5056 1,5 kΩ 5% "" " " 80.5056 22 kΩ 5% "" " " 80.5056 5,8 kΩ 5% "" " " 80.5059 6,8 kΩ 5% "" " " 80.5056 6,8 kΩ 5% "" " " 80.5056 73.9 kΩ 5% " " " " 80.5056 73.9 kΩ 5% " " " " 80.5056 99.5066 Transistor AF121		C4	5061		50V
74.5111 39 pF 2% ceram NO75 TB 74.5117 76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 76.5061 1,5 kΩ 5% "" " " 80.5055 1,5 kΩ 5% "" " " 80.5056 1, kΩ 5% "" " " 80.5069 6,8 kΩ 5% "" " " 80.5056 3,9 kΩ 5% " " " " 80.5056 6,8 kΩ 5% " " " " 80.5056 1,8 kΩ 5% " " " " 80.5056 1,8 kΩ 5% " " " " 80.5056 1,8 kΩ 5% " " " " 80.5056 1,9 kΩ 5% " " " " 80.5056 1,783 Coil/spole 11,3 - 14,6 MHz 99.5073 Transistor AF121		C2	5111		250V
76.5061 4,7 nF 10% polyest FL 76.5061 4,7 nF 10% polyest FL 80.5065 22 kΩ 5% carbon film 80.5065 22 kΩ 5% "" " 80.5056 3,9 kΩ 5% "" " 80.5059 1, kΩ 5% " " " 80.5059 6,8 kΩ 5% " " " 80.5059 6,8 kΩ 5% " " " 80.5059 6,8 kΩ 5% " " 80.5059 Transistor AF121 Transistor AF124		C2	5117		250V 250V
80.5065 22 kΩ 5% carbon film 80.5065 1,5 kΩ 5% " " " 80.5056 3,9 kΩ 5% " " " 80.5069 1 kΩ 5% " " " 80.5069 6,8 kΩ 5% " " " 80.5059 6,8 kΩ 5% " " " 80.5056 3,9 kΩ 5% " " " 80.5056 Transistor AF121 99.5073 Transistor AF124		00 CO	5061		50V
80.5065 22 kū 5% carbon film 0, 80.5065 22 kū 5% iii 0, 80.5051 1,5 kū 5% ii ii 0, 80.5056 3,9 kū 5% ii ii 0, 80.5059 6,8 kū 5% ii ii 0, 80.5059 6,8 kū 5% ii ii 0, 80.5056 3,9 kū 5% ii ii 0, 80.5056 3,9 kū 5% ii ii 0, 6,8 kū 5% ii ii 0,8 kū 5% ii 1,8 kū 5					2
80.5051 1,5 kd 5% " " " 0,8 k0.5056 3,9 kd 5% " " " 0,9 kd 5% " " " 0,0 kd 5065 6,8 kd 5% " " " 0,0 kd 5056 80.5056 3,9 kd 5% " " " 0,0 kd 5056 80.5056 3,9 kd 5% " " 0,0 kd 5056 80.5056 Transistor AF121 99.5073 Transistor AF124		R1	5065		0, 1W
80.5056 3,9 kg 5% "" "" 0,8 80.5049 1 kg 5% "" "" 0,8 80.5065 22 kg 5% "" " " 0,9 80.5059 6,8 kg 5% "" " " 0,9 80.5056 3,9 kg 5% " " " 0,9 80.5056 3,9 kg 5% " " " 0,9 80.5056 Transistor AF121 99.5073 Transistor AF124		R3	80,5051	= =	0, 1 W
80.5049 1 k2 5% " " 0, 80.5065 22 k2 5% " " 0, 80.5059 6, 8 k2 5% " " 0, 80.5056 3, 9 k2 5% " " 0, 0, 80.5056 3, 9 k2 5% " Transistor AF121 99, 5073 Transistor AF124		R4	80,5056	= :	0, 1W
61.783 Coil/spole 11, 3 - 14, 6 MHz 99.5066 Transistor AF121 99.5073 Transistor AF124		R5	80,5049	= =	0, 1W
61.783 Coil/spole 11, 3 - 99.5066 Transistor AF121 99.5073 Transistor AF124		R7 R8	80,5059	= =	0, 1W 0, 1W 0, 1W
99,5073 Transistor		L1	61,783	11,3 -	
		Q1 Q2	99,5066	Transistor AF121 Transistor AF124	

TRANSMITTER SECTION CQP510(R) SENDERSEKTION

X401,156

CQP510(R) TRANSMITTER SECTION

SENDERSEKTION



PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

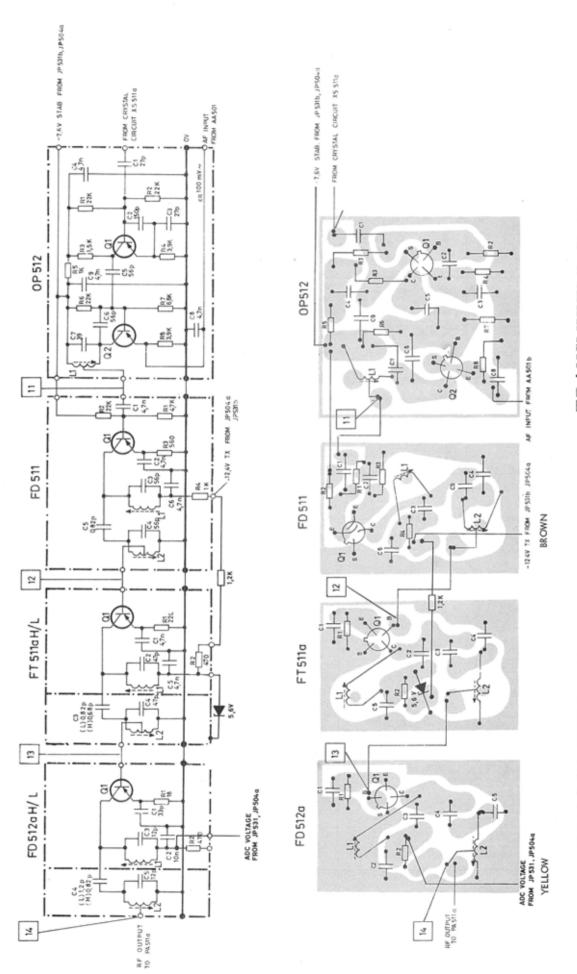
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TYPE	NO.	CODE	DATA	
FN511a		10,1548	Antenna Filter	
	C3 C2	74.5136 74.5131 74.5136	12 pF 5% ceram N150 DI 4,7 pF ±0,25 pF ceram N150 DI 12 pF 5% ceram N150 DI	125V 125V 125V
	L1 L3	61.976 61.975 61.974	RF coil/HF spole 146-174 MHz RF coil/HF spole 146-174 MHz RF coil/HF spole 146-174 MHz	
PA513a		10,2324	Power Amplifier	
	CC	74.5161 74.5155 74.5135 74.5137 74.5131	470 pF -20 +80% ceram II PL 1 nF -20 +80% ceram II PL 1 nF -20 +80% ceram II PL 10 pF 5% ceram N150 TB 15 pF 5% N150 TB 4, 7 pF \pm 0, 25 pF ceram N150 TB 2 μ F 20% tantal	63V 63V 63V 125V 125V 125V 35V
	R1 R2 R3	80,5029 80,5034 80,5029	22 Ω 5% carbon film 56 Ω 5% carbon film 22 Ω 5% carbon film	0, 1W 0, 1W 0, 1W
	1122 123 124 125 126	61, 1084 61, 1084 63, 5008 63, 5007 63, 5007	RF coil/HF spole 146-176 MHz RF coil/HF spole 146-176 MHz 0, 47 μ H 20% RF choke/HF drossel 0, 47 μ H 20% RF choke/HF drossel 15 μ H 10% RF choke/HF drossel 15 μ H 10% RF choke/HF drossel	0,5A 0,5A
	Q1	99,5229	Transistor 2N4427	
PA511cH PA511cL		10.1314	Power Amplifier Power Amplifier	
	2222222	74.5136 74.5109 74.5132 74.5109 74.5131 74.5131	12 pF 5% ceram N150 DI 10 nF -20 +80% ceram II PL 5, 6 pF ± 0, 25 pF ceram N150 DI 10 nF -20 +80% ceram II PL 4, 7 pF ± 0, 25 pF ceram N150 DI 15 pF 5% ceram N150 DI 4 7 pF +0 25 pF ceram N150 DI	125V 20V 250V 20V 250V 125V
PA511L PA511L	R1 R2 R3		Ω 5% carbon film Ω 5% carbon film Ω 5% carbon film	0,1W 0,1W 0,1W

	76 MHz 56 MHz 76 MHz 56 MHz 1 500 mA							
DATA	spole 156-176 spole 146-156 spole 146-156 spole 156-176 sselspole choke/drossel 5	AF2025 BSX 19						
	RF coil/HF spole 156-17 RF coil/HF spole 146-15 RF coil/HF spole 146-15 Choke/drosselspole 15 μ H 10% choke/drossel	Transistor AF Transistor BS						
	RF c RF c RF c RF c Chok	Tran						
CODE	61,0906 61,0901 61,0902 61,0900 62,0651 63,5007	99,5169 99,5139						
NO.	L22 L23 L23 L43	Q1 Q2						
TYPE	PA511H PA511L PA511H PA511L							

TRANSMITTER SECTION CQP510(R)

X401.206



TRANSMITTER SECTION CQP510(R)-1W SENDERSEKTION

D 401.724

PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

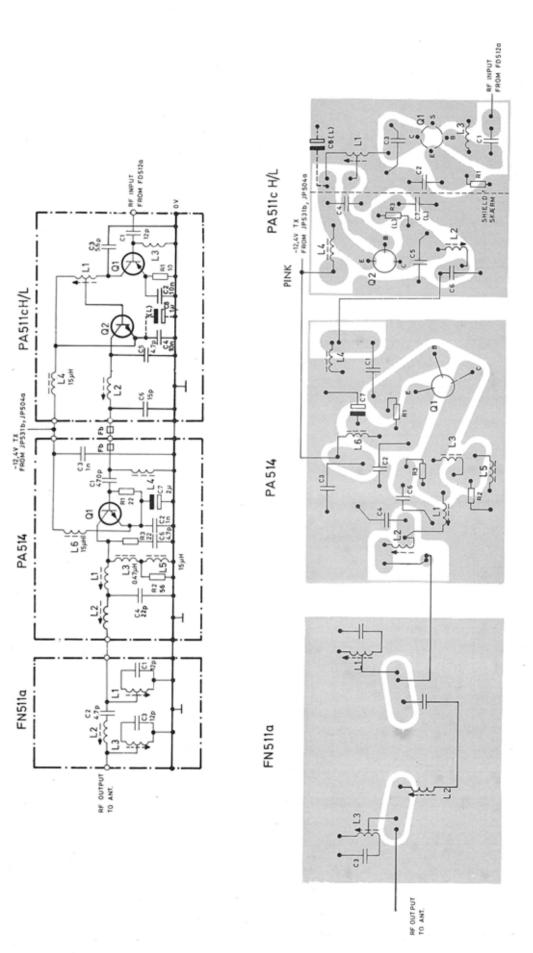
		250V 20V 250V 250V 250V 250V 250V	0,1W 0,1W			20V 63V 250V 250V 250V 63V 250V	0,1W 0,1W			20V 20V 250V 500V 500V
DATA	Frequency Doubler Frequency Doubler	33 pF 2% ceram NO75 TB 10 nF -20 +80% ceram II PL 12 pF ± 0, 5 pF ceram NO75 TB 0, 82 pF ± 0, 1 pF ceram P100 BD 1, 2 pF ± 0, 25 pF ceram N150 BD 12 pF ± 0, 5 pF ceram NO75 TB	$18\ \Omega\ 5\%$ carbon film $470\ \Omega\ 5\%$	RF coil/HF spole 156-176 MHz RF coil/HF spole 146-156 MHz RF coil/HF spole 156-176 MHz RF coil/HF spole 146-156 MHz	Transistor AF202S	Frequency Tripler Frequency Tripler 4, 7 nF -20 +80% ceram II PL 47 pF 5% polystyr TB 0, 68 pF ± 0, 1 pF P100 BD 0, 82 pF ± 0, 1 pF P100 BD 47 pF 5% polystyr TB 4, 7 nF -20 +80% ceram II PL	220 \(\Omega\) 5\% carbon film 470 \(\Omega\) 5\%	RF coil/HF spole 73-89 MHz RF coil/HF spole 78-89 MHz RF coil/HF spole 73-78 MHz Transistor AF106		4, 7 nF -20 +80% ceram II PL 4, 7 nF -20 +80% ceram II PL 56 pF 2% ceram NO75 TB 56 pF 2% ceram NO75 TB 0, 82 pF ± 0, 1 pF ceram P100 BD 4, 7 nF -20 +80% ceram II PL
CODE	10,1316	74.5116 74.5109 74.5141 74.5122 74.5124	80,5028 80,5045	61, 907 61, 905 61, 993 61, 904	99,5169	10.1318 10.1319 74.5108 76.5090 74.5121 76.5090 77.5108	80,5041 80,5045	61, 905 61, 903 61, 908	10,1086	74.5108 74.5111 74.5111 74.5122 74.5108
NO.		222222	R1 R2	1222	Q1	2222245	R1 R2	L2 L2 01		CC
TYPE	FD512aH FD512aL	FD512H FD512L		FD512H FD512L FD512H FD512L		FT511aH FT511aL FT511H FT511L		FT511H FT511L	FD511	

R1 80,5055 22 47 ka 5% carbon film 0,5046 80,5049 1 ka 5% 1 1 1 1 1 1 1 1 1	TYPE	NO.	CODE	DATA	
L1 61.744 RF coil/HF spole 24, 3 - 29 MHz L2 61.745 RF coil/HF spole 24, 3 - 29 MHz C1 99.5067 Transistor AF106 C2 76.5103 150 pF 2% ceram NO75 TB 25 C3 74.5116 27 pF 2% ceram NO75 TB 25 C4 74.5111 56 pF 2% ceram NO75 TB 25 C5 74.5111 56 pF 2% ceram NO75 TB 25 C6 74.5111 56 pF 2% ceram NO75 TB 25 C6 74.5111 56 pF 2% ceram NO75 TB 25 C7 74.5111 56 pF 2% ceram NO75 TB 25 C8 74.5111 56 pF 2% ceram NO75 TB 25 C9 76.5061 4,7 nF 10% polyest FL 5 C9 76.5061 4,7 nF 10% polyest FL 5 C9 76.5061 1,5 k3 5% " " " C9 80.5065 22 k3 5% " " " C9 80.5065 1,5 k3 5% " " " C9 80.5065 22 k3 5% " " " C9 80.5065 22 k3 5% " " " C1 61.783 Coil/spole 11,3 - 14,6 MHz C2 C1/spole 11,3 - 14,6 MHz C3 99.5073 Transistor AF124	*	R1 R2 R3 R4	80,5057 80,5065 80,5046 80,5049	_	0, 1W 0, 1W 0, 1W 0, 1W
C1 74.5107 Phase Modulator C2 76.5103 150 pF 2% ceram NO75 TB 25 C3 76.5061 4,7 nF 10% polyest FL C4 5111 56 pF 2% ceram NO75 TB 25 C4 74.5111 56 pF 2% ceram NO75 TB 25 C5 74.5111 39 pF 2% ceram NO75 TB 25 C6 74.5111 39 pF 2% ceram NO75 TB 25 C7 74.5111 39 pF 2% ceram NO75 TB 25 C8 76.5061 4,7 nF 10% polyest FL C9 76.5061 4,7 nF 10% polyest FL C9 76.5061 4,7 nF 10% polyest FL C9 76.5061 1,5 k2 5% " " " C9 76.5061 22 k2 5% carbon film C9 80.5065 22 k2 5% " " C9 80.5065 22 k2 5% " " C9 80.5065 22 k2 5% " " C9 80.5066 22 k2 5% " " C9 80.5066 22 k2 5% " " C9 76.5061 1,5 k2 5% " " C9 76.5061 1,5 k2 5% " " C9 76.5061 1,5 k2 5% " " C9 76.5063 22 k2 5% " " C9 76.5069 22 k2 5% " " C9 76.5069 22 k2 5% " C		L1 L2	47	coil/HF spole 24, 3 - 29 coil/HF spole 24, 3 - 29	
C1 74.5107 27 pF 2% ceram NO75 TB 25 C2 76.5103 150 pF 2, 5% polystyr 3 74.5156 27 pF 2% ceram N750 TB 25 C4 76.5061 4,7 nF 10% polyset FL 56 pF 2% ceram NO75 TB 25 C4 74.5111 56 pF 2% ceram NO75 TB 25 C7 74.5117 39 pF 2% ceram NO75 TB 25 76.5061 4,7 nF 10% polyest FL 55 76.5061 4,7 nF 10% polyest FL 55 NG 5065 22 kG 5% "" " " " 0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,		Q1	9,506		
74.5107 27 pF 2% ceram NO75 TB 35 76.5103 150 pF 2,5% polystyr 3 74.5156 4,7 nF 10% polyest FL 56.5061 4,7 nF 10% polyest FL 574.5111 56 pF 2% ceram NO75 TB 25 74.5111 56 pF 2% ceram NO75 TB 25 74.5117 39 pF 2% ceram NO75 TB 25 76.5061 4,7 nF 10% polyest FL 5 76.5061 4,7 nF 10% polyest FL 5 76.5061 4,7 nF 10% polyest FL 5 80.5065 22 kΩ 5% " " " 0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0	OP512		0.112	Phase Modulator	
74.5107 76.5103 76.5103 76.5103 76.5103 76.5103 774.5156 77.0F 2% ceram NO75 TB 76.5061 74.5111 56 pF 2% ceram NO75 TB 75.5061 74.5111 56 pF 2% ceram NO75 TB 75.5061 74.71F 10% polyest FL 76.5061 76.5061 77.0F 10% polyest FL 76.5061 76.5061 77.0F 10% polyest FL 76.5061 76.5061 77.0F 10% polyest FL 76.5061 77.0F 10% polyest FL 76.5061 78.5065 78.5065 78.5065 78.5065 78.5066 78.506		ξ	1 4 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0		
74.5156 27 pF 2% ceram N750 TB 75.5061 4,7 nF 10% polyest FL 5 74.5111 56 pF 2% ceram NO75 TB 25 74.5111 56 pF 2% ceram NO75 TB 25 74.5117 39 pF 2% ceram NO75 TB 25 76.5061 4,7 nF 10% polyest FL 5 76.5061 4,7 nF 10% polyest FL 5 80.5065 22 kG 5% "" " " " 0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,		35	74,5107	27 pF 2% ceram NO75 TB 150 pF 2, 5% polystyr	250V 30V
76.5061 76.5061 74.7 ar 10% polyest FL 74.5111 56 pF 2% ceram NO75 TB 74.5117 39 pF 2% ceram NO75 TB 76.5061 4,7 nF 10% polyest FL 56.5065 80.5065 22 k2 5% carbon film 80.5065 22 k2 5% ii ii 80.5066 80.5066 3,9 k2 5% ii ii 80.5069 80.5069 6,8 k2 5% ii ii 80.5069 6,8 k2 5% ii ii 80.5069 80.5069 1 k2 5% ii ii 0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,		CS	74,5156	27 pF 2% ceram N750 TB	250
74.5111 56 pF 2% ceram NO75 TB 25 74.5111 56 pF 2% ceram NO75 TB 25 74.5117 39 pF 2% ceram NO75 TB 25 76.5061 4,7 nF 10% polyest FL 5 80.5065 22 k2 5% carbon film 0,80.5065 1,5 k2 5% " " " 0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0		O C	76,5061	4, 7 nF 10% polyest FL	50
74.5117 39 pF 2% ceram NO75 TB 25 76.5061 4,7 nF 10% polyest FL 5 76.5061 4,7 nF 10% polyest FL 5 76.5061 22 kΩ 5% carbon film 0,80.5065 22 kΩ 5% " " " 0,80.5056 3,9 kΩ 5% " " " 0,80.5069 6,8 kΩ 5% " " " 0,80.5069 6,8 kΩ 5% " " " 0,80.5059 6,8 kΩ 5% " " " 0,90,80.5056 3,9 kΩ 5% " " " 0,90,80.5056 3,9 kΩ 5% " " " 0,90,80.5056 Transistor AF121 99.5073 Transistor AF124		3 5	74.5111	56 pF 2% ceram NO75 TB	250
76.5061 4, 7 nF 10% polyest FL 76.5061 4, 7 nF 10% polyest FL 80.5065 22 kΩ 5% "" " 80.5056 3, 9 kΩ 5% "" " 80.5056 3, 9 kΩ 5% "" " 80.5059 6, 8 kΩ 5% "" " 80.5059 6, 8 kΩ 5% "" " 80.5056 3, 9 kΩ 5% "" " 80.5056 3, 9 kΩ 5% "" " 80.5056 Transistor AF121 99.5073 Transistor AF121		C2	74,5117	39 pF 2% ceram NO75 LB	250
80.5065 22 k3 5% carbon film 80.5065 22 k3 5% carbon film 80.5065 3,9 k3 5% " " " 80.5069 80.5069 80.5069 6,8 k3 5% " " 80.5059 80.5059 6,8 k3 5% " " 90.5056 Transistor AF121 99.5073 Transistor AF121		0°0	76,5061	4,7 nF 10% polyest FL	501
80.5065 22 k2 k2 5% carbon film 80.5065 22 k2 5% " " " 80.5051 1,5 k2 5% " " " 80.5056 3,9 k2 5% " " " 80.5069 22 k2 5% " " " 80.5069 6,8 k2 5% " " " 80.5059 6,8 k2 5% " " 80.5059 6,8 k2 5% " " 90.5056 Transistor AF121 99.5073 Transistor AF124		3	TOOC *01	4, I nF 10% polyest FL	200
80.5065 22 kn 5% " " 0, 80.5051 1,5 kn 5% " " 0, 80.5056 3,9 kn 5% " " 0, 80.5049 1 kn 5% " " 0, 80.5065 22 kn 5% " " 0, 80.5059 6,8 kn 5% " " 0, 80.5056 3,9 kn 5% " " 0, 80.5056 3,9 kn 5% " 0, 80.5056 Transistor AF121 99.5073 Transistor AF124		R1	80,5065	22 k2 5% carbon film	0,11
80.5051 1,5 k2 5% 11 11 0,5 k2 5% 11 11 11 0,5 k2 5% 11 11 11 0,5 k3 5% 11 11 11 11 0,5 k3 5% 11 11 11 11 11 11 11 11 11 11 11 11 11		R2	80,5065	22 kΩ 5% " "	0,1
60.5055 3, 9 kd. 5% 00, 80.5049 1 kd. 5% 00, 80.5055 6, 8 kd. 5% 00, 80.5056 3, 9 kd. 5% 00, 80.5056 3, 9 kd. 5% 00, 80.5056 Transistor AF121 99.5073 Transistor AF124		22	80,5051	1, 5 kg 5%	0,1
80.5065 22 kg 5% " " 0, 80.5065 8, 8 kg 5% " " 0, 80.5056 3, 9 kg 5% " " 0, 0, 0, 0, 0, 0, 0, 0, 0, 0, 0, 0, 0,		R4	80, 5056	3, 9 kd 5%	0,1
80.5059 6,8 kg 5% " " 0,8 80.5056 3,9 kg 5% " " 0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0,0		R6	80.5065	29 LO 50% 11 11	0,0
61.783 Coil/spole 11, 3 - 14, 6 MHz 99.5073 Transistor AF121 99.5073 Transistor AF124		R3	80,5059	6,8 kg 5% " " "	
99, 5066 Transistor AF121 99, 5073 Transistor AF124		=	2000		
99,5073 Transistor AF12		1		- 2 "11	
		Q1 Q2	99,5066 99,5073	AF12 AF12	

TRANSMITTER SECTION CQP510(R) SENDERSEKTION

X401,156

CQP510(R)-1W



PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

TRANSMITTER SECTION SENDERSEKTION

D 401.345

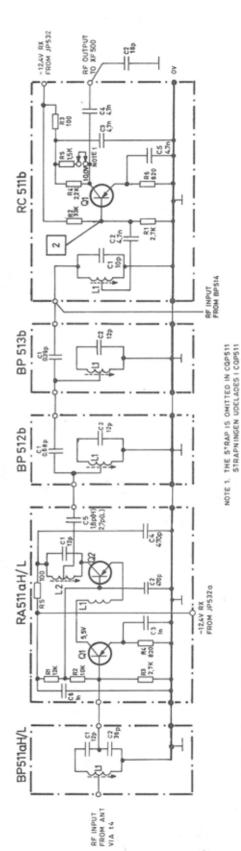
TYPE	NO.	CODE	DATA	
FN511a		10,1548	Antenna Filter	
	C22 C2	74.5136 74.5131 74.5136	12 pF 5% ceram N150 DI 4.7 pF ± 0.25 pF ceram N150 DI 12 pF 5% ceram N150 DI	125 V 125 V 125 V
	L1 L2 L3	61.976 61.975 61.974	RF coil/HF spole 146-174 MHz RF coil/HF spole 146-174 MHz RF coil/HF spole 146-174 MHz	
PA514	C1 C2 C3	10.2579. 74.5161 74.5155 74.5155	am II PL 1 PL 1 II PL	63 V 63 V 63 V
-	C4 C6 C7	74.5106 74.5131 73.5102	22 pF 5% ceram TB 4.7 pF ± 0.25 pF ceram N150 TB 1 2 μF 20% tantal	160.V 160 V 35 V
	R1 R2 R3	80.5029 80.5034 80.5029	22 \(\text{R} \) 5% carbon film 56 \(\text{R} \) 5% carbon film 0 22 \(\text{R} \) 5% carbon film 0	0.1 W 0.1 W 0.1 W
	L3 L3 L5 L6	61, 1084 61, 1084 63, 5008 62, 0651 63, 5007 63, 5007	RF coil/HF spole 146-174 MHz RF coil/HF spole 146-174 MHz 0.47 µH 20% RF choke/HF drossel 0.08 µH RF choke/HF drossel 15 µH 10% RF choke/HF drossel 15 µH 10% RF choke/HF drossel	0.5 A
	Q1	99,5256	Transistor BLX65	
РА511сН		10,1314-02	Power Amplifier 156-174 MHz	
PA511dL		10,1315-03	Power Amplifier 146-156 MHz	
W .	222222	74, 5136 74, 5109 74, 5132 74, 5131 74, 5131	12 pF 5% ceram N150 DI 10 nF -20+80% ceram II PL 5.6 pF ± 0.25 pF ceram N150 DI 2 10 nF -20+80%ceram II PL 4.7 pF ± 0.25 pF ceram N150 DI 2 15 pF 5% ceram N150 DI 2	125 V 20 V 250 V 20 V 250 V 125 V
	R1	80,5025	10 \Omega \cdot 5\% carbon film (0.1 W
PA511H PA511L PA511H PA511L	2222	61.0906 61.0901 61.0902 61.0900	RF coil/HF spole 156-174 MHz RF coil/HF spole 146-156 MHz RF coil/HF spole 156-174 MHz RF coil/HF spole 146-156 MHz	

Storno

Choke/drosselspole L4 63,5007 15 μH 10% choke/drossel 500 mA Q1 99,5139 Transistor AF202S Q2 Transistor BSX19 Transistor BSX19	
99.5169	selspole hoke/drossel 500 mA
	AF202S BSX19
_	

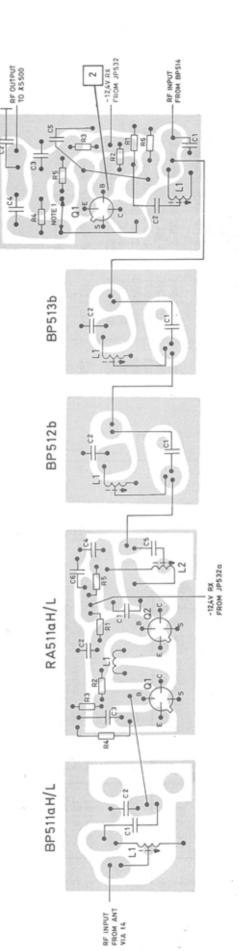
TRANSMITTER SECTION CQP510(R)-1W SENDERSEKTION

X401,335



PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

RC511b



CQP510(R) RECEIVER SECTION MODTAGERSEKTION

Storno

Storno

BP511aH BP511aL				
0110L		10,1355		
		10,1350	Bandpass Filter	
	C2	74.5141 74.5117	12 pF ± 0, 5 pF ceram NO75 TB 39 pF 2% ceram NO75 TB	250V 250V
BP511H BP511L	11	61.922 61.917	RF coil/HF spole 156-174 MHz RF coil/HF spole 146-160 MHz	
RA511aH RA511aL		10,1356	RF-Amplifier RF-Amplifier	
RASIIH	22222	74.5141 74.5161 74.5112 74.5161	775 TB PL N150 BD	250V 125V 20V 125V 250V
KASIIL	C.C.	74.5112	II.	250V 20V
	R1 R2 R3 R4	80, 5062 80, 5061 80, 5054 80, 5048 80, 5037	12 kg 5% carbon film 10 kg 5% carbon film 2.7 kg 5% carbon film 820 \(\text{ is 5} \) carbon film 100 \(\text{ is 5} \) carbon film	0.1W 0.1W 0.1W 0.1W
RA511H RA511L	L22	62.614 61.923 61.916	Coil/spole 68-88 MHz, 146-174 MHz RF coil/HF spole 156-174 MHz RF coil/HF spole 146-160 MHz	Z
	ଦ୍ଧୀ ଦୃ2	99,5067 99,5067	Transistor AF106 Transistor AF106	
BP512b		10,1357	Bandpass Filter	
	C2	74.5121 74.5141	0.68 pF ± 0.1 pF ceram P100 BD 12 pF ± 0.5 pF ceram NO75 TB	500V 250V
	L1	61,1060	RF coil/HF spole $156-174~\mathrm{MHz}$	٠.
BP513b		10,1358	Bandpass Filter	
	C2	74.5120 74.5141	0.39 pF ± 0.1pF ceram P100 BD 12 pF ± 0.5 pF ceram NO75 TB	500V 250V
	L1	61,1060	RF coil/HF spole 156-174 MHz	

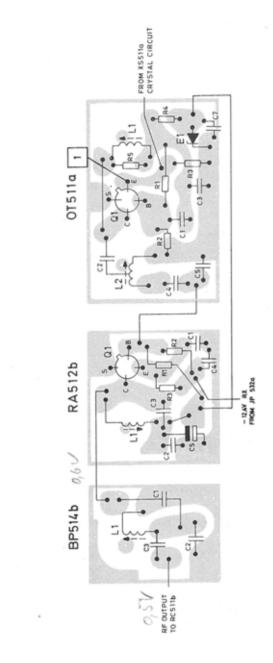
Storno			250V 20V 50V 50V	0.1W 0.1W 0.1W 0.1W 0.1W				
	DATA	Receiver Converter	12 pF ± 0.5 pF ceram NO75 TB 4.7 nF -20 +80% ceram II PL 4.7 nF 10% polyest, FL 4.7 nF 10% polyest, FL	2.7 kg 5% carbon film 33 kg 5% carbon film 100 \(\Omega \) 5% carbon film 2.2 kg 5% carbon film 1.5 kg 5% carbon film 820 \(\Omega \) 5% carbon film	RF coil/HF spole	Transistor AF106		
	CODE	10,1325	74,5141 74,5108 76,5061 76,5061	80,5054 80,5067 80,5037 80,5053 80,5051 80,5048	61,912	99,5067		
	NO.		CC2 CC3 CC4	R1 R2 R3 R4 R5	L1	ଦ୍ୟ		
	TYPE	RC511a	,					

RECEIVER SECTION CQP510(R)

X401,145

CQP510(R)

RECEIVER SECTION MODTAGERSEKTION



FROM XS511a CRYSTAL CIRCUIT

-12,4V RX FROM JP 532a

Pare Mare

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TO RCS11b

PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

Stormo

Storno

07511a H/L

RA512bH/L

BP514bH/L

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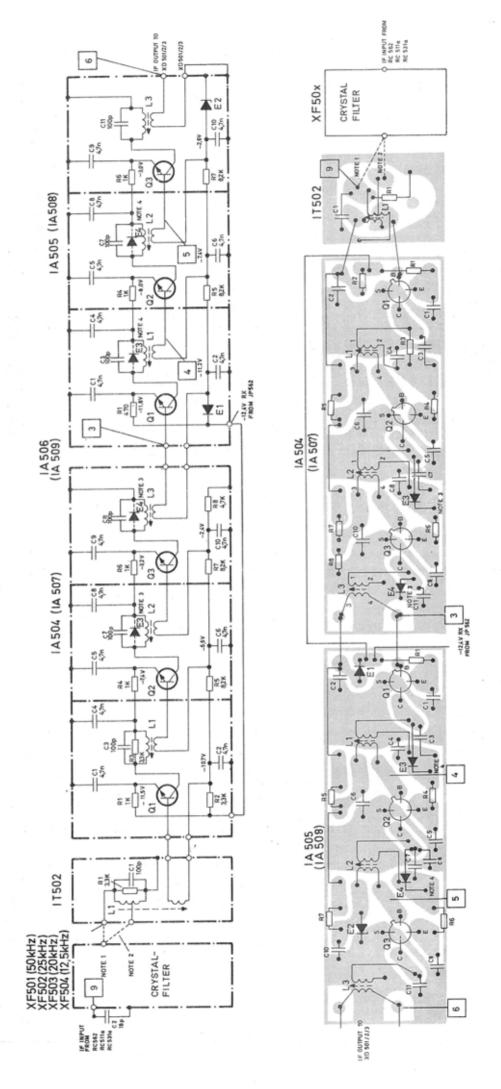
		250V 250V 20V	z_		20V 20V 125V 250V 250V 10V	0.1W 0.1W 0.1W				50V 250V 250V 250V 250V 20V	0.1W 0.1W 0.1W 0.1W
DATA	Bandpass Filter Bandpass Filter	0.68 pF ± 0.1 pF ceram P100 BD 12 pF ± 0.5 pF ceram NO75 TB 0.39 pF -20 +80% ceram II PL	RF coil/HF spole 145-168 MHz RF coil/HF spole 156, 7-170, 7 MHz	RF Amplifier RF Amplifier	1 nF -20 +80% ceram II PL 1 nF -20 +80% ceram II PL 8, 2 pF 5% ceram N150 TB 6 d pF ± 0.5 pF ceram NO75 TB 1 nF -20 +80% ceram II PL 2, 2 µF -20 +50% tantal	15 kg 5% carbon film 3.9 kg 5% carbon film 470 ß 5% carbon film	RF coil/HF spole 130-170 MHz	Transistor BF173	Oscillator Tripler Oscillator Tripler	1 nF 10% polyest, FL 8.2 pF ± 0.5 pF ceram N750 DI 33 pF 2% ceram NO75 TB 12 pF ± 0.5 pF ceram NO75 TB 33 pF 2% ceram NO75 TB 1 nF -20 +80% ceram II PL	6.8 kD 5% carbon film 3.9 kD 5% carbon film 1 kD 5% carbon film 1 kD 5% carbon film 2.7 kD 5% carbon film
CODE	10,1359	74,5121 74,5141 74,5120	61,925 61,919	10,1360	74.5112 74.5134 74.5133 74.5133 74.5112	80,5063 80,5056 80,5045	61,1083	99,5168	10,1361	76.5069 74.5160 74.5116 74.5141 74.5112	80,5059 80,5056 80,5049 80,5049
NO.		322	33		222222	R1 R3	Ľ	Q1		CCCCCC	R1 R2 R3 R4
TYPE	3P514bH 3P514bL		BP514H BP514L	RA512bH RA512bL	RA512H RA512L				OT511aH OT511aL		

Storno

TYPE	NO	CODE	DATA
OT511H OT511L	L1 L2 L2	61,915 61,927 61,914	RF coil/HF spole 52, 23-56, 9 MHz RF coil/HF spole 145-168 MHz RF coil/HF spole 156, 7-170 MHz
	E1	99,5114	Zenerdiode BZY 57
	Q1	99,5067	Transistor AF106
RECEIVER	IVE	SE	CTION COP510(R)

MODTAGERSEKTION X401.220

こるどり10(尺)



PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN

NOTE 2: STRAP FOR 25, 20 AND 12, SHHZ CHANNEL SEPARATION

NOTE 1: STRAP FOR SORME CHANNEL SEPARATION STRAPHING FOR SORNE KANALAFSTAND STRAPNING FOR 25, 20 OG 12, SKHE KANALAFSTAND DIODES E3 AND E4 ARE INSERTED IN 14507 CHIZ. DIODER E3 OG E4 INDSATTES KUN 1 14507.

NOTE 3:

NOTE 4: DIDGES E3 OG E4 ARE INSERTED IN IA 508 ONLY.
DIDGER E3 OG E4 INDSATTES KUN I IA 508.

RECEIVER SECTION MODTAGERSEKTION

CQP500

D401.105/4

Storno

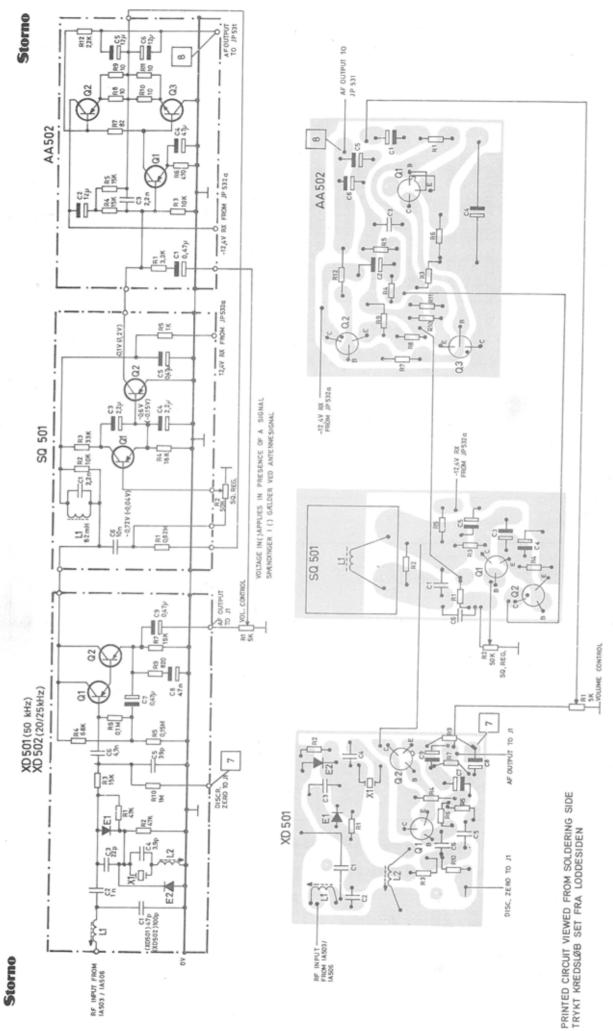
	DATA	Filter 50 kHz	Filter 25/20 kHz	Filter 12, 5 kHz	ce Transformer Unit 2.5% polystyr. TB 25V	% carbon film 0.1W	ole 10,7 MHz	IA505	IA508	iffer Unit	0% polyest. FL 50V 0% FL 50V	r TB		111	yr TB	J -	1.1	rB	000		: :		spole 10.7 MHz	spole	V4148 V4148	
5002 5002 5001 5012 1991 1991 1047 1047 1047 1047 1048 5061 5062 5061 5062 5062 5064 5065 5065 5066 5067	DATA	Filter	Filter	Filter 12.	Impedance Transformer Unit 100 pF 2.5% polystyr. TB	.3 kg 5% carbon film	P-1	A504 + IA505	+	Amplifier Unit	7 nF 10% polyest.) pF	7 nF	7 nF 10% "	pF.	nF 10% polyest.	nF 10% "	pF 2.5% polystyr	carbon fi	3 KL 5%	2 kg 5% " kg 5% "	2 kg 5% "	coil/HF spole 10.	coil/HF spole 10. coil/HF spole 10.	iode 1N4148 iode 1N4148	
	CODE	2005	5001	9.5012	0.1991	5055	.1047	0,1918	0,2493	0,1893	5061	5102	5061	5061	5102	5061	5061 4	5102 1	5049 1	5049 1	5060	5060 8 5057 4	1045	1045	9, 5237	_
	TYPE	XF501	XF502	XF504	IT502			IA506	IA509	IA504 IA507															IA507 IA507	

			50V 50V 25V 50V 50V	50V 50V 50V 50V 25V	0.1W 0.1W 0.1W 0.1W 0.1W		400mW		
DATA	Transistor BF167 Transistor BF167 Transistor BF167	IF Amplifier Unit IF Amplifier Unit	4.7 nF 10% polyest. FL 4.7 nF 10% polyest. FL 100 pF 2.5% polystyr. TB 4.7 nF 10% polyest FL 4.7 nF 10%	HHHHH H	470 \(\alpha \) 5% carbon film 1 k\(\alpha \) 5% " " " 8.2 k\(\alpha \) 5% " " " 1 k\(\alpha \) 5% " " " 8.2 k\(\alpha \) 5% " " " "	RF coil/HF spole 10.7 MHz RF coil/HF spole 10.7 MHz RF coil/HF spole 10.7 MHz	Diode Stab. ZE 1.5 Zenerdiode 3.3V 5% Diode 1N4148 Diode 1N4148	Transistor BF167 Transistor BF167 Transistor BF167	
CODE	99.5166 99.5166 99.5166	10,1894	76.5061 76.5061 76.5102 76.5061 76.5061	76. 5061 76. 5061 76. 5061 76. 5061 76. 5061	80, 5045 80, 5049 80, 5060 80, 5060	61.1045 61.1045 61.1045	99.5209 99.5210 99.5237 99.5237	99.5166 99.5166 99.5166	
NO.	&2 &3 &3		22222	11 11 11 11 11 11 11 11 11 11 11 11 11	R1 R4 R6 R7	1322	를 들고 123 124 137 137 137 137 137 137 137 137 137 137	885	
TYPE		IA505 IA508					IA508 IA508		

RECEIVER SECTION MODTAGERDEL

CQP500

X401.251



RECEIVER SECTION CQP510(R) MODTAGERSEKTION CQP530(R)

		250V 20V 250V 250V 250V 250V 20V 16V 16V	0,000 11W 0,000 11W 0,000 11W 0,000 10W 0,000						50V 10V 10V 16V	0, 1W 0, 1W 0, 1W 0, 1W
DATA	Crystal Discriminator Crystal Discriminator	47 pF 2% ceram NO75 TB 100 pF 2,5% polystyr N150 TB 1 nF -20 +80% ceram PL 22 pF ± 0,5pF ceram NO75 TB 3,9 pF ± 0,25pF ceram N150 DI 39 pF 2% ceram NO75 TB 4,7 nF -20 +80% ceram PL 0,47 μF -20 +50% tantal 47 nF -20 +50% tantal 0,47 μF -20 +50% tantal	47 kg 5% carbon film 47 kg 5% carbon film 15 kg 5% carbon film 68 kg 5% carbon film 0,15 Mg 5% carbon film 15 kg 5% carbon film 15 kg 5% carbon film 820 g 5% carbon film 1 Mg 10% carbon film	Coil/spole 10,7 MHz Coil/spole 10,7 MHz Coil/spole 10,7 MHz	Diode AA119 Diode AA119	Transistor BCZ13 Transistor BCZ13	Crystal type 98-7	Squelch Unit	2, 2 nF 10% polyest, FL 2, 2 μ F -20 +50% tantal 2, 2 μ F -20 +50% tantal 0, 47 μ F -20 +50% tantal 10 nF 10% polyest FL50	0,82 MM 5% carbon film 10 kM 5% carbon film 33 kM 5% carbon film 18 kM 5% carbon film
CODE	10,984	74,5118 76,5102 74,5112 74,5106 74,5130 74,5117 74,5108 73,5134 73,5134	80, 5069 80, 5069 80, 5063 80, 5071 80, 5075 80, 5073 80, 5085	61,594 61,614 61,595	99,5074 99,5074	99,5043 99,5043	98,5003	10,967	76.5059 73.5129 73.5129 73.5134 76.5070	80,5084 80,5061 80,5067 80,5064
NO.		22222222	R1 R2 R3 R4 R5 R6 R7 R9	1112	E1 E2	Q1 Q2	X1	,	22223	R1 R3 R4
TYPE	XD501 XD502	XD501 XD502		XD501 XD502				SQ501		

Storno

	R5	80,5049	1 k2 5% carbon film	0, 1W
	Ľ	61,577	Coil/spole 82 mH	
	୍ଦ୍ର ବ୍ୟ	99,5043	Transistor BCZ13 Transistor BCZ13	
AA502		10,991	AF amplifier	
	Cl	73,5134	0, 47 µF -20 +50% tantal	16V
	C25	73,5074	12 µF -20 +75% tantal	15V
	25.0	78.5029	2, 2 nF 10% polyest. FL 47F -20 +50% tantal	200
	C2	73,5074	12 µF -20 +75% tantal	15V
	90	73,5074	12 µF -20 +75% tantal	15V
	R1	80,5055	3, 3 kg 5% carbon film	
	R3	80,5061	10 kg 5% carbon film	
	R4	80, 5063	15 kg 5% carbon film	
	Re	80 5045	15 Kat 5% carbon illin 470 O 5% carbon film	0,1W
	R7	80, 5036	82 2 5% carbon film	
	R.8	80,5025	5% carbon	0, 1W
	K9 R10	80, 5025	10 2 5% carbon film	0, 1W
	R11	502	5% carbon	0,10
	R12	80,5053	2, 2 kg 5% carbon film	0, 1W
		99,5115	Transistor BC179	
	228	99,5068	Transistor pair (Q2-AC132, Q3-AC127)	3-AC127)
	}			

RECEIVER SECTION CQP510(R) MODTAGERSEKTION CQP530(R)

X401,153

RECEIVER SECTION MODTAGERSEKTION

CQP514(R), CQP534(R)

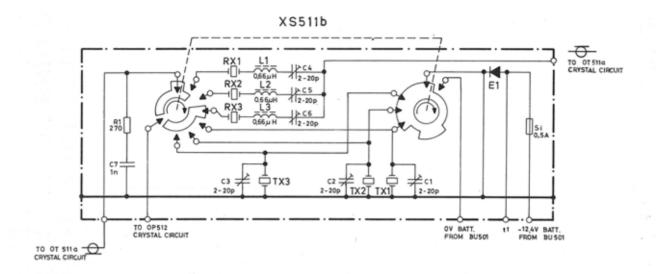
D401.252

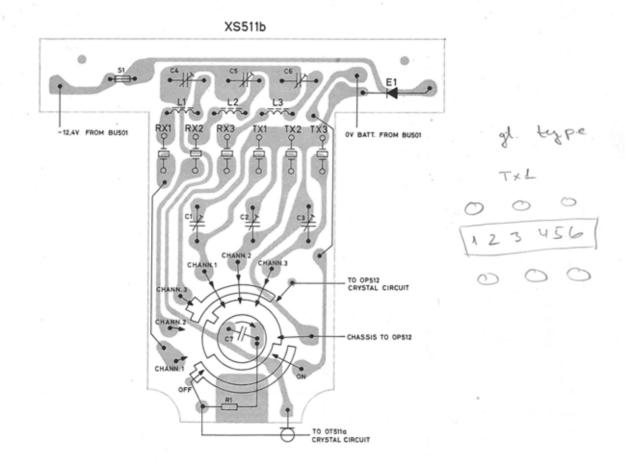
_				
	16V 15V 50V 6V 15V 15V	0,1W 0,1W 0,1W 0,1W 0,1W 0,1W 0,1W 0,1W	50V 50V 50V 50V 0,1W 0,1W 0,1W	50V 10V 10V 16V 50V 0,1W
DATA	AF amplifier 0,47 µF -20 +50% tantal 12 µF -20 +75% 2.2 nF 10% polyest FL 47 µF -20 +50% tantal 12 µF -20 +75% 12 µF -20 +75% 12 µF -20 +75%	3.3 kΩ 5% carbon film 10 kΩ 5% 15 kΩ 5% 15 kΩ 5% 10 0 5% 10 0 5% 10 0 5% 10 0 5% 10 0 5% 10 0 5% 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	Noise Amplifier 1 nF 10% polyest FL 1 nF 10% polyest FL 10 nF 10% " FL 1.2 k\(\text{T}\) 5% carbon film 0.1 \(\text{M}\) 5% " " " 2.2 k\(\text{T}\) 5% " " " Transistor BC214L	Squelch Unit 2.2 nF 10% polyest FL 2.2 μ F -20 +50% tantal 2.2 μ F -20 +50% " 0, 47 μ F -20 +50% " 10 nF 10% polyest FL 0.82 M Ω 5% carbon film 10 k Ω 5%
CODE	10,991 73.5134 73.5074 76.5059 73.5029 73.5074	80, 5055 80, 5061 80, 5063 80, 5045 80, 5035 80, 5025 80, 5025 80, 5025 80, 5025 80, 5025 80, 5025	10.2062 76.5069 76.5070 76.5070 76.5070 80.5053 80.5063	10,967 76,5059 73,5129 73,5129 73,5134 76,5070 80,5061
NO.	555555	R1 R3 R4 R6 R7 R10 R11 R12 Q1 Q2 Q2	C1 C2 C3 C4 C4 R1 R2 R3 R3 R4	C1 C3 C5 C6 C6 R1 R2
TYPE	AA.502		AA504	SQ501

Storno		0,1W 0,1W 0,1W				300	200	500V	250V	20V	7000	167		1/10W				1/10W 1/10W					
	DATA	33 k2 5% carbon film 18 k2 5% " " " " 1 k2 5% " " "	Coil/spole 82 mH	Transistor BCZ13 Transistor BCZ13	Crystal Discriminator	2.5% polystyr	1 nr -20 +80% ceram PL 22 pF ± 0. 5 pF ceram TR	3.9 pF ± 0, 25pF " DI	39 pF 2%	0.47 nF -20 +50% PL	47 nF -20 +50% tantal	0.47 nF -20 +50% tantal		47 kg 5% :: :: :: :: :: :: :: :: :: :: :: :: ::	ka 5% "	0, 15 Mg 5% "	5% "	820 2 5% '' '' 1	Coil/spole 10,7 MHz Coil/spole 10,7 MHz	Diode AA119 Diode AA119	Transistor BCZ13 Transistor BCZ13	Crystal Type 98-25	
	CODE	80, 5067 80, 5064 80, 5049	61,577	99, 5043 99, 5043	0	76.5102	· 4	4	4.	73, 5134	00	es.	80, 5069	80, 5069	80,5071	80, 5075	80, 5063	80, 5048 80, 5085	61.614	99, 5074	99, 5043 99, 5043	98, 5009	
	NO.	R3 R4 R5	L1	Q1 Q2		55	38	C4	500	C2	C8	C3	R1	R3	R4	R5	R7	R10	L2	E1 E2	Q1 Q2	X1	_
	TYPE				XD503																		

RECEIVER SECTION CQP534 CQP514 MODTAGERSEKTION

X401,257





PRINTED CIRCUIT VIEWED FROM COMPONENT SIDE TRYKT KREDSLØB SET FRA KOMPONENTSIDEN

CRYSTAL SHIFT UNIT KRYSTALSKIFTEENHED

XS511b

D401.174

Storno

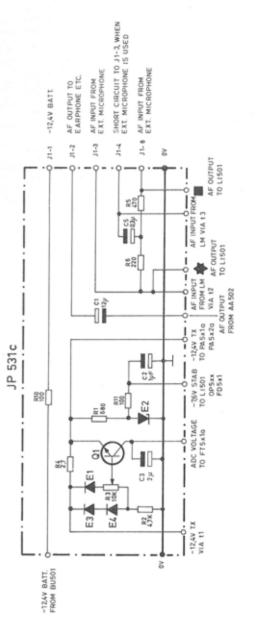
		500V 500V 500V 500V 500V 500V	0,1W					
DATA	Crystal shift Panel	2/20 pF teflon N250 2/20 pF teflon N250 1 nF -20 +50% ceram II PL	270 Ω 5% carbon film coil/spole 0, 66 μ H coil/spole 0, 66 μ H coil/spole 0, 66 μ H	Channel selector/kanalomskifter	Diode OA200			
CODE	10,1507	78.5046 78.5046 78.5046 78.5046 78.5046 78.5046	80,5042 62,720 62,720 62,720	47,257	99,5028			
NO.		CC	R1 L2 L3	01	E1			
TYPE	XS511b					100000 1100000 1100000		

DATA	
q	
CODE	
NO.	
TYPE	@18.3V

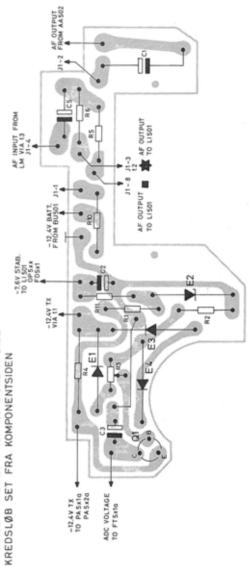
KRYSTALSKIFTEENHED XS511 CRYSTAL SHIFT UNIT

X401,163

JUNCTION PANEL SAMLEPANEL



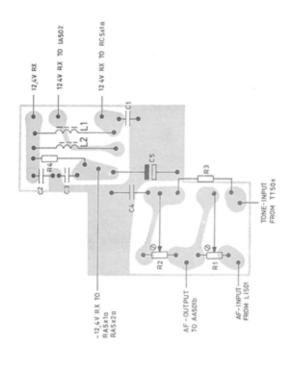
PRINTED CIRCUIT VIEWED FROM COMPONENT SIDE TRYKT KREDSLØB SET FRA KOMPONENTSIDEN



	15V 30V 35V 10V	0,1W 0,05W 1/16W 0,1W 0,1W 1/4W 0,1W								
DATA	Junction Panel 12 μF -20 +75% tantal 1 μF 20% tantal 2, 2 μF 20% tantal 0.3 μF 10% tantal	680 \$\Omega\$ 5\% carbon film 4. 7 k\$\Omega\$ 5\% carbon film 10 k\$\Omega\$ potm. Lin. carb. film 2, 7 \$\Omega\$ 5\% metall. 470 \$\Omega\$ 5\% carbon film 220 \$\Omega\$ 5\% carbon film 100 \$\Omega\$ 20\% metaloxyd 100 \$\Omega\$ 5\% carbon film	Diode OA200 Zenerdiode BZY61 Diode OA200 Diode OA200	Transistor BSY39						
CODE	10,1117 73,5074 73,5135 73,5102 73,5079	80.5047 80.5057 86.5037 89.5021 80.5045 89.5041 89.5022	99,5028 99,5075 99,5028	99,5076						
NO.	CG CG C	R1 R2 R3 R4 R5 R6 R10	E E E E E E E E E E E E E E E E E E E	Q1						
TYPE	JP531c						,			

	JP531c
DATA	JUNCTION PANEL SAMLEPANEL
CODE	UNCTI
NO.	SAN
TYPE	

D401.171



AF-OUTPUT TO

JP532a

- AF-INPUT FROM

PRINTED CIRCUIT VIEWED FROM COMPONENT SIDE TRYKT KREDSLØB SET FRA KOMPONENTSIDEN

-124V RX TONE-INPUT FROM RA5xla TT50X RA5x2a

-12,4V RX -12,4V RX TO TO 1A 502 RC 5x1a

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55

35 |-

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-12,4 V O

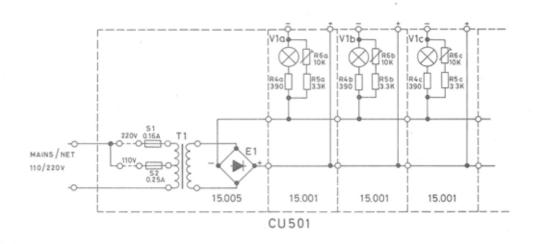
	20V 20V 20V 30V 15V	0,05W 0,05W 0,1W 0,1W	pole					
DATA	Junction Panel 4, 7 nF -20 +80% ceram II PL 4, 7 nF -20 +80% ceram II PL 4, 7 nF -20 +80% ceram II PL 1 nF 2, 5% polystyr 12 μ F -20 +75% tantal	50 kV potm. Lin carbon film 0, 5 MV potm. Lin carbon film 1 MV 10% carbon film 47 I 5% carbon film	15 μH 10% Filter Coil/drosselspole 15 μH 10% Filter Coil/drosselspole					
CODE	10,1021 74,5108 74,5108 74,5108 76,5109 73,5074	86,5036 86,5038 80,5033 80,5033	63,5007				il.	
NO.	CC CC CC CC CC	R1 R2 R3	L1 L2					
TYPE	JP532a							

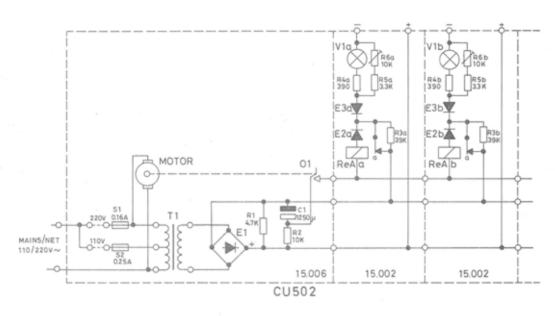
DATA					
CODE					
NO.				1	
TYPE			,		

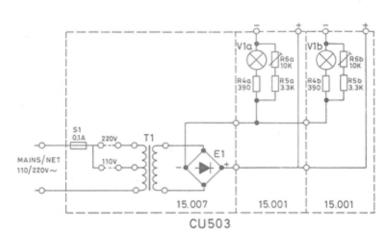
JUNCTION PANEL SAMLEPANEL

X401,158

JP532a







CHARGING UNIT CU501, CU502, CU503 LADEENHED

TYPE	NO.	CODE	DATA	
CU501		15,0005 15,0001	Charging Unit Battery Outlets/Ladekassetter	
	R4 R5 R6	81.5044 80.5055 86.5007	390 Ω 5% carbon film 3, 3 k Ω 5% carbon film 10 k Ω 20% potm. carbon film	1/2W 1/4W 0.2W
	T1	60,5125	Transformer	
	E1	94,5016	Rectifier/Ensretter B60 C500	
	V1	92,5071	Lamp/Lampe 30V 30 mA	
	S1 S2	92,5027 92,5029	Fuse/sikring 160 mA T Fuse/sikring 250 mA T	
CU 502		15,0006 15,0002	Charging Unit Battery Outlets/Ladekassetter	
	CI	73,50099	$1250\mu\mathrm{F}$ -10 +50% elco	40 V
	R1 R2 R3 R4 R5	82,5057 81,5061 80,5468 81,5044 80,5455 86,5007	4, 7 kΩ 5% carbon film 10 kΩ 5% carbon film 39 kΩ 5% carbon film 390 Ω 5% carbon film 3, 3 kΩ 5% carbon film 10 kΩ 20% potm. carbon film	2 W 1/2W 1/4W 1/2W 1/4W 0,2W
	T1	60,5125	Transformer	
	E2 E3	94,5016 94,5020 94,5020	Rectifier/Ensretter B60 C500 Diode 1N4004 Diode 1N4004	
	01	47.0301	Contact set/Kontaktsæt	
	V1	92,5003	Lamp/Lampe 30V 30 mA	
	ReA	58,5048	Counter/Tæller	
	SI	92,5027 92,5029	Fuse/Sikring 160 mA T Fuse/Sikring 250 mA T	
	Motor	93,5007	Synchronous motor with gear Synkronmotor med gear	

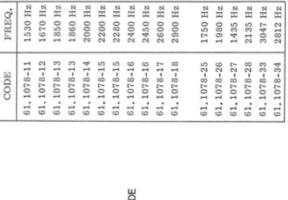
15,0007 Battery Outlets/Ladekassetter 15,0001 Battery Outlets/Ladekassetter 15,0001 Battery Outlets/Ladekassetter 15,0001 Battery Outlets/Ladekassetter 1/2w 86,5007 10 ka 20% potm. carbon film 1/4w 1/4w 10 ka 20% potm. carbon film 1/4w 1/4w 1/2w 10 ka 20% potm. carbon film 1/2w 1/	TYPE	NO.	CODE	DATA	
81. 5044 390 \(\alpha\) 5% carbon film 86. 5007 10 \(\alpha\) 20% potm. carbon film 60. 5126 Transformer 94. 5006 Rectifier/Ensretter B60 C160 92. 5025 Fuse/Sikring 100 mA T	CU503		15,0007	Charging Unit Battery Outlets/Ladekassetter	
60.5126 94.5006 92.5071 31 92.5025		R4 R5 R6	81,5044 80,5055 86,5007		/2W /4W .2W
94. 5006 92. 5071 92. 5025		$_{\rm T1}$	60,5126	Transformer	
		E1 V1 S1	94,5006 92,5071 92,5025	Rectifier/Ensretter B60 C160 Lamp/Lampe 30V 30 mA Fuse/Sikring 100 mA T	
		5			

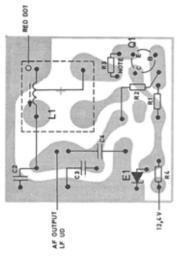
CHARGING UNIT CUS

CU501, CU502, CU503

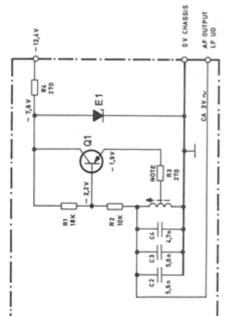
X401.234

TONE TRANSMITTER TONESENDER





PRINTED CIRCUIT VIEWED FROM SOLDERING SIDE TRYKT KREDSLØB SET FRA LODDESIDEN



NOTE: NOM 270-A-DJUSTED/JUST.

Storno

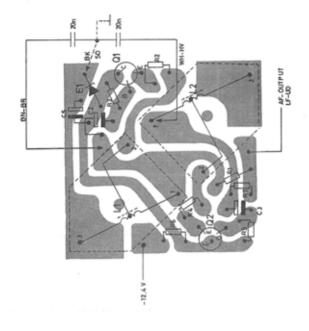
`												
	-											_
	25V 25V 25V	0.1W 0.1W 0.1W 0.1W										
DATA	5.6 nF 2.5% polystyr TB 5.6 nF 2.5% TB 4.7 nF 2.5% "TB	18 k2 5% carbon film 10 k2 5% " " 270 \(\text{2} \) % " " "	coil/spole	BZY61 zenerdiode	BCZ 13 transistor					N.		
CODE	76,5051 76,5051 76,5051	80,5064 80,5061 80,5042 80,5042	61,1078	99,5075	99,5043							
NO.	C23 C4	R1 R2 R3 R4	11	E1	ଦୀ							
TYPE												

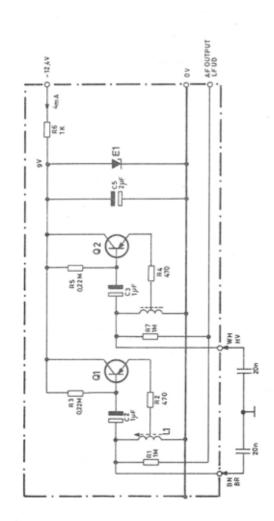
DATA			
CODE			
NO.			
TYPE			

TT501TONE TRANSMITTER
TONESENDER

x400.077/2

TONE TRANSMITTER TONESENDER





		,								
	15V 15V 15V	0,0,0,11W 0,0,0,11W 0,0,0,1W 0,0,1W								
DATA	2 μF -20% +50% 2 μF -20% +50% 2 μF -20% +50%	1 MM 5% carbon film 470 \(\text{A} 5\) \(\text{A} \) \(\text{B} \) \(\text{A}	coil/spole coil/spole	zenerdiode 9V	NS6063 Transistor NS6063 Transistor					
CODE	73.5098 73.5098 73.5098	80, 5085 80, 5045 80, 5077 80, 5077 80, 5045 80, 5049 80, 5085	61,1052 61,1052	99,5042	99, 5043			-		
NO.	C2 C3	R1 R2 R3 R4 R5 R6	L2 L2	E1	82					
TYPE										7

Storno			
	DATA		
	CODE		
	NO.		
	TYPE		

TONE TRANSMITTER
TONESENDER

[X401,079]

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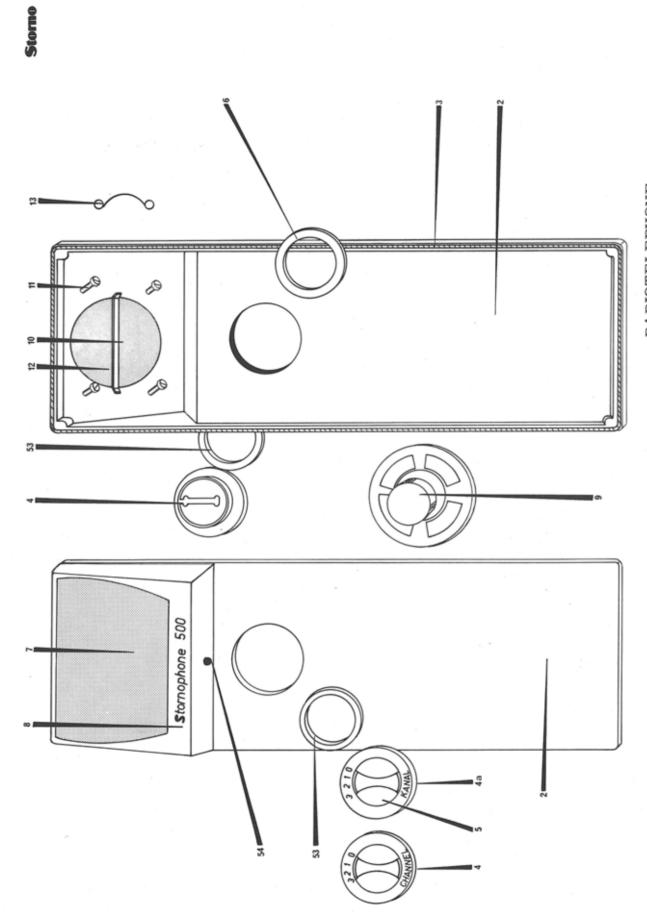
TT504

CHAPTER VI. MECHANICAL PARTS LISTS

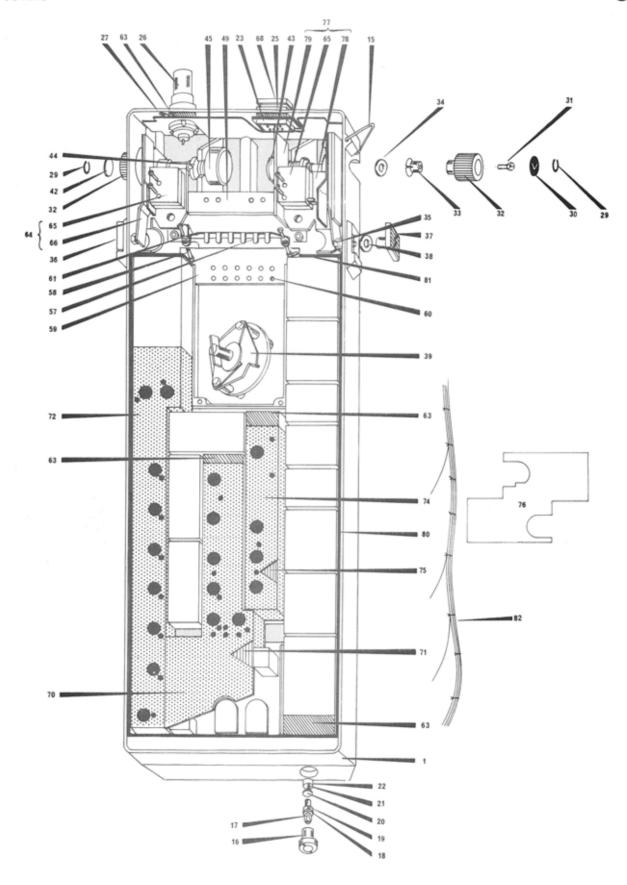
When ordering mechanical parts from Storno please state the code numbers and descriptions given in the parts lists.

경기 있다는 경기 전 보기를 들어야 하면 하는 것이 없는 것이 말하게 되었다.

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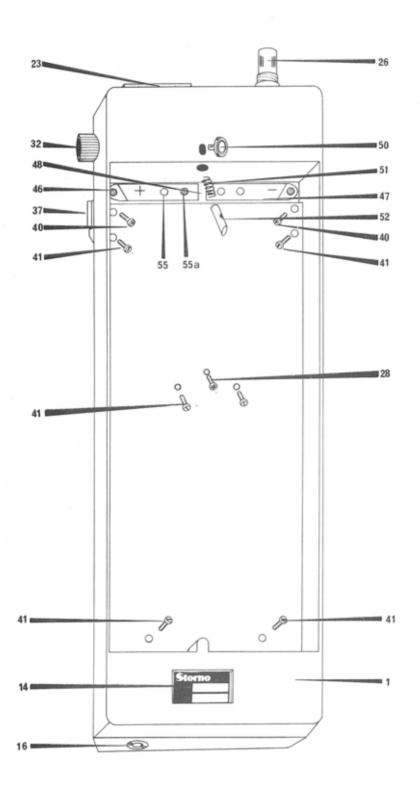


CQP510, CQP530 RADIOTELEPHONE TASCHENFUNKGERÄT



RADIOTELEPHONE TASCHENFUNKGERÄT

CQP510, CQP530



RADIOTELEPHONE TASCHENFUNKGERÄT

CQP510, CQP530

ITEM	CODE	DESCRIPTION
1	12.0039	Cabinet Kabinet
2	15.0012	Cover assembly Låg komplet
	12.0040	Cover without loudspeaker and channel selector Låg uden højttaler og kanalvælger
3	32.0110	Gasket for item 2 Pakning for position 2
4	49.0097	Channel knob assy (Channel) Omskifterknap komplet (Channel)
4a	49.0106	Channel knob assy (Kanal) Omskifterknap kompl. (Kanal)
5	51.0309	Semi-circular cover plate for items 4 and 4a Halvcirkelformet dækplade for pos. 4 og 4a
6	32, 0255	Washer Skive
. 7	52.0018	Speaker grille Højttalergitter
8	52,0017	Speaker frame with text Højttalerramme med tekst
9	97.5011	Speaker Højttaler
10	36.0154	Spring strip Fjeder, lang
11	20011-02605	Screw M2.6 x 5 Skrue M2,6 x 5
12	32.0136	Dust cover Støvdæksel
13	36.0209	Spring retainer Fjeder for højttaler
14	51.0306	Label 'STORNOPHONE 500' Firmaskilt
15	36.0105	Lanyard clip Øsken
16	29.0154	Lamp retainer Lampeholder
17	92.5013	Lamp 12V 130 mA Lampe 12V 130 mA
18	32.5015	'O' ring O-ring
19	29.0157	Washer Skive
20	30,0008	Contact dish Kontaktstift
21	36.0113	Spring Fjeder
22	32.0125	Insulating bush Isolationsbøsning
23	41.5077	Multiconnector, male Multikonnektor, han
24	20011-02604	Screw M2.6 x 4 Skrue M2,6 x 4
25	32.0117	Gasket for item 23 Pakning for pos. 23
26	41.0144	Antenna connector assy Antennekonnektor komplet

RADIOTELEPHONE RADIOTELEFONANLÆG

CQP510, CQP530

M405.011-2

ITEM	CODE	DESCRIPTION
27	34.0038	Solder tag Loddeflig
28	20052-02606	Screw M2.6 x 6 with recessed head Skrue M2,6 x 6 med krydskærv
29	36.0122	Circlip Låsering
30	51.0280	Label, volume knob Skilt til volumen kontrolknap
31	20011-02604	Screw M2 x 8 Skrue M2 x 8
32	49.0091-01	Knob Knap
33	31.0246	Bøsning Collect
34	32.0112	Sealing ring Pakning
35	28.0059	Screw Skrue
36	49.0090	Push button 'TONE' Trykknap ''TONE''
37	49.0185	Push button 'KEY' Trykknap "TAST"
38	32.0113	Sealing ring Pakning
39	47.0257	ON/Off-Channel selector assy Omskifter komplet
40	20052-02606	Screw M2.6 x 6 with recessed head Skrue med krydskærv
41	20041-03012	Screw M3 x 12 Skrue M3 x 12
42	51.0281	Label, squelch knob Skilt til squelch knap
43	86.0003	Potentiometer, volume Potentiometer, volumen
44	29.0152	Potentiometer, nut Potentiometer møtrik
45	86.0002	Potentiometer, squelch Potentiometer, squelch
46	36.0109	Battery contact, positive Batterifjeder, positiv
47	36.0110	Battery contact, negative Batterifjeder, negativ
48	32.0115-01	Insulating plate Isolationsplade
49	32.0116-01	Insulating plate Isolationsplade
50	49.0093	Knob, battery catch Låseknap
51	36,0114	Spring, battery catch Låsefjeder
52	37.0053	Lock bar, battery catch Låsepal
53	32.0111	Switch sealing ring Pakning for omskifter
54	30.5004	Channel indicating pip, red 2 ^ø x 5 Kærvnitte, rød, 2 ^ø x 5

RADIOTELEPHONE RADIOTELEFONANLÆG

CQP510, CQP530

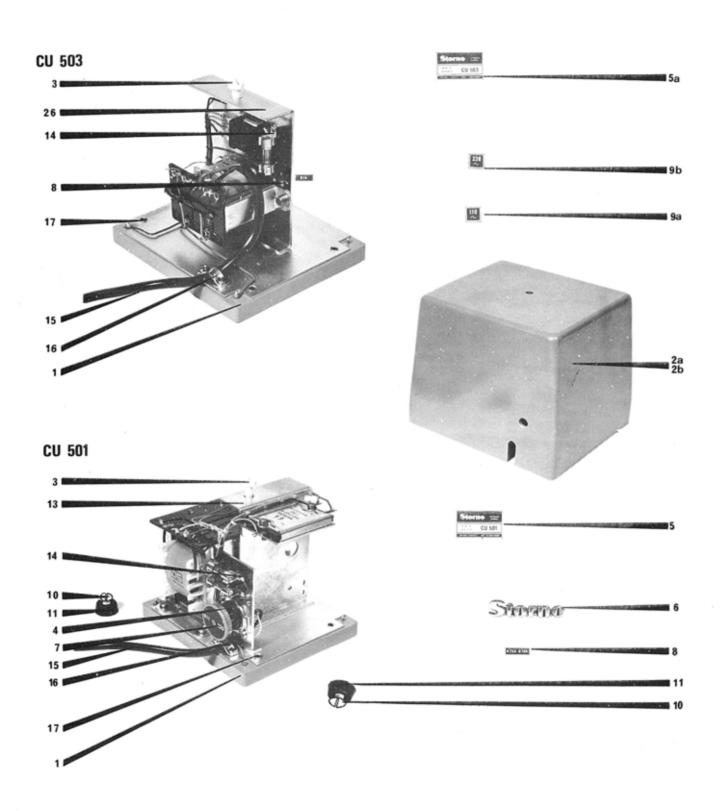
M405.011-2

ITEM	CODE	DESCRIPTION
55	30,0007-01	Rivet Nitte
55a	32,0109	Bush Bøsning
56	21081-02004	Screw Skrue
57	36.0103-01	Crystal retainer Krystalholder
58	31.0228	Spacing bush Afstandsbøsning
59	32.0114	Crystal mounting board Monteringsplade for krystaller
60	34.0019	Sockets for item 59 Bøsninger for pos. 59
61	36.0130	Fuse retainer Bøjle for sikring
62	29.0151	Washer Skive
63	32.0139	Packing blocks (4 ea.) Gummiklodser
64	47.5058	Microswitch Assembly (incl. Item 65,66) Mikroswitch komplet (inkl. pos. 65,66)
65	47.5055	Microswitch (excl. Item 66) Mikroswitch (ekskl. pos. 66)
66	33.0375	Activation Spring for Microswitch Aktiveringsarm for Mikroswitch
67	46,5005	Fuse holder Sikringsholder
68	32.0128-01	Protection cap for item 23 Beskyttelseshætte for pos. 23
69	33.0186-01	Clamp Bøjle
70	13,002-01	Screen plate Skærmplade
71	32.0344	Insulating plate Isolationsplade
72	13,0071	Screen plate for CQP with IA501 and IA502 Skærmplade for CQP med IA501 og IA502
	13.0072	Screen plate for CQP with IA506 or IA509 Skærmplade for CQP med IA506 og IA509
74	13.0021-01	Screen plate Skærmplade
75	32.0346	Insulating plate Isolationsplade
76	32,0138	Insulating plate Isolationsplade
77	47.0559	Microswitch assembly (incl. pos. 65,78,79) Mikroswitch, kompl. (inkl. pos. 65,78,79)
78	33.0374	Activation Spring for item 65 Aktiveringsarm for pos. 65
79	15.0042	Printed Circuit Board for item 77 Lederplade for pos. 77
80	13.0057-01	Mounting Box for Module Units Monteringskasse til modulenheder
81	34.	Solder Tag FRP 4052D Loddeflig FRP 4052D
82	18.0389	Cabling Kabling

RADIOTELEPHONE RADIOTELEFONANLÆG

CQP510, CQP530

M405.011/2-3 Page 3 of 3



CHARGING UNIT LADEGERÄTE

CU501, CU503

ITEM	CODE	DESCRIPTION
		CU503
	15,0007	Charging unit for 2 batteries Ladeensretter for 2 kassetter
1	12.0046	Base plate Bundstykke
2a	12.0049	Top cover less hole for voltage switch Dæksel uden hul for spændingsomsk.
3	21101-15001	Nylon screw M5 x 10 Nylonskrue M5 x 10
5a	51.0317	Type label Typeskilt
6	51.0171	'Storno' motif Firmaskilt
8	51.0328	Fuse holder label Skilt for sikringsholder
9a	51.0329	Label 110 V AC Skilt 110 V
9b	51.0327	Label 220V AC Skilt 220V~
14	46.5002	Fuse holder Sikringsholder
15	173-5012	Cable Ledning
16	38.5011	Cable clamp Kabelbøjle
17	30.5022	Tubular rivet Rørnitte
26	11.0326-02	Chassis plate complete Chassisplade komplet
		CU501
	15.0005	Charging unit for 10 batteries Ladeensretter for 10 kassetter
1	12.0046	Base plate Bundstykke
2 b	12.0045-01	Top cover with hole for voltage switch Dæksel med hul for spændingsomskifter
3	21101-05010	Nylon screw M5 x 10 Nylonskrue M5 x 10
4	47.0502	Voltage selector 110-220V Spændingsomskifter 110-220V
5	51.0315	Type label Typeskilt
6	51.0171	'Storno' motif Firmaskilt
7	51.0339	Voltage selector label Skilt for spændingsomskifter
8	51.0326	Fuse label Skilt for sikringsholder
10	28.5001	Insulating screw Isoleringsskrue
11	56.0007	Rubber feet Gummiben

CHARGING UNIT LADEENSRETTER

CU501, CU503

ITEM	CODE		DESCRIPTION
14	46.5002	Fuse holder Sikringsholder	
15	173-5012	Cable Ledning	
16	38.5011	Cable clamp Kabelbøjle	
17	30.5022	Tubular rivet Rørnitte	
	50		
		-	
			*

CHARGING UNIT LADEENSRETTER

CU501, CU503

M405.019-1